

# 2021 Index

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This index covers all technical items—papers, correspondence, reviews, etc.—that appeared in this periodical during 2021, and items from previous years that were commented upon or corrected in 2021. Departments and other items may also be covered if they have been judged to have archival value.

The Author Index contains the primary entry for each item, listed under the first author's name. The primary entry includes the coauthors' names, the title of the paper or other item, and its location, specified by the publication abbreviation, year, month, and inclusive pagination. The Subject Index contains entries describing the item under all appropriate subject headings, plus the first author's name, the publication abbreviation, month, and year, and inclusive pages. Note that the item title is found only under the primary entry in the Author Index.

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- Implementation of RTCVD-SiN<sub>x</sub> Gate Dielectric Into Enhancement-Mode GaN MIS-HEMTs Fabricated on Ultrathin-Barrier AlGaIn/GaN-on-Si Platform. *Shi, W.*, +, *TED Sept. 2021 4274-4277*
- Improved RF Power Performance of AlGaIn/GaN HEMT Using by Ti/Au/Al/Ni/Au Shallow Trench Etching Ohmic Contact. *Lu, H.*, +, *TED Oct. 2021 4842-4846*
- Improvement of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> MIS-SBD Interface Using Al-Reacted Interfacial Layer. *He, M.*, +, *TED July 2021 3314-3319*
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- InAlN/GaN HEMT on Si With  $f_{max} = 270$  GHz. *Cui, P.*, +, *TED March 2021 994-999*
- Influence of Carbon on pBTI Degradation in GaN-on-Si E-Mode MOSHEMT. *Viey, A.G.*, +, *TED April 2021 2017-2024*
- Influence of Fin-Like Configuration Parameters on the Linearity of AlGaIn/GaN HEMTs. *Wang, P.*, +, *TED April 2021 1563-1569*
- Interface Charge Effects on 2-D Electron Gas in Vertical-Scaled Ultrathin-Barrier AlGaIn/GaN Heterostructure. *Huang, S.*, +, *TED Jan. 2021 36-41*
- Interfacial Properties of nMOSFETs With Different Al<sub>2</sub>O<sub>3</sub> Capping Layer Thickness and TiN Gate Stacks. *Wang, D.*, +, *TED March 2021 948-953*
- Interplay Between Surface and Buffer Traps in Governing Breakdown Characteristics of AlGaIn/GaN HEMTs—Part II. *Joshi, V.*, +, *TED Jan. 2021 80-87*
- Interplay of Various Charge Sources in AlGaIn/GaN Epi-Stack Governing HEMT Breakdown. *Soni, A.*, +, *TED May 2021 2378-2386*
- Investigation of Electrical and Optical Properties of AlGaInP Red Vertical Micro-Light-Emitting Diodes With Cu/Invar/Cu Metal Substrates. *Sinha, S.*, +, *TED June 2021 2818-2822*
- Investigations of the Effects of the Orientation of AlN-Based Complementary Resistive Switches. *Hung, P.*, +, *TED Aug. 2021 3826-3831*
- Low ON-State Resistance Normally-OFF AlGaIn/GaN MIS-HEMTs With Partially Recessed Gate and ZrO<sub>x</sub> Charge Trapping Layer. *Cai, Y.*, +, *TED Sept. 2021 4310-4316*
- Low-Voltage Thyristor Heterostructure for High-Current Pulse Generation at High Repetition Rate. *Slipchenko, S.O.*, +, *TED June 2021 2855-2860*
- Mechanisms Underlying the Bidirectional  $V_T$  Shift After Negative-Bias Temperature Instability Stress in Carbon-Doped Fully Recessed AlGaIn/GaN MIS-HEMTs. *Zagni, N.*, +, *TED May 2021 2564-2567*
- Millimeter-Wave Donor-Acceptor-Doped DpHEMT. *Pashkovskii, A.B.*, +, *TED Jan. 2021 53-56*
- Modeling of Bias-Dependent Effective Velocity and Its Impact on Saturation Transconductance in AlGaIn/GaN HEMTs. *Pampori, A.U.H.*, +, *TED July 2021 3302-3307*
- Monolithic Comparator and Sawtooth Generator of AlGaIn/GaN MIS-HEMTs With Threshold Voltage Modulation for High-Temperature Applications. *Li, A.*, +, *TED June 2021 2673-2679*
- Monolithic Integrated Normally OFF GaN Power Device With Antiparallel Lateral Schottky Barrier Controlled Schottky Rectifier. *Bi, L.*, +, *TED April 2021 1778-1783*
- Noise Analysis of the Leakage Current in Time-Dependent Dielectric Breakdown in a GaN SLCFET. *Dalcanale, S.*, +, *TED May 2021 2220-2225*
- Nonalloyed Ohmic Contacts in AlGaIn/GaN HEMTs With MOCVD Regrowth of InGaIn for Ka-Band Applications. *Cakmak, H.*, +, *TED March 2021 1006-1010*
- Nonlinear Thermal Analysis of AlGaIn/GaN HEMTs With Temperature-Dependent Parameters. *Tang, M.*, +, *TED Sept. 2021 4565-4570*
- On the Channel Hot-Electron's Interaction With C-Doped GaN Buffer and Resultant Gate Degradation in AlGaIn/GaN HEMTs. *Chaudhuri, R.R.*, +, *TED Oct. 2021 4869-4876*
- Partial Recovery of Dynamic  $R_{ON}$  Versus OFF-State Stress Voltage in p-GaN Gate AlGaIn/GaN Power HEMTs. *Cioni, M.*, +, *TED Oct. 2021 4862-4868*
- Performance and Reliability Optimization of Supercritical-Nitridation-Treated AlGaIn/GaN High-Electron-Mobility Transistors. *Wu, P.*, +, *TED Sept. 2021 4317-4321*
- Physical Insights Into the Impact of Surface Traps on Breakdown Characteristics of AlGaIn/GaN HEMTs—Part I. *Joshi, V.*, +, *TED Jan. 2021 72-79*
- Physics-Based Stochastic Three-Dimensional Modeling for Metal-Oxide Resistive Random Access Memory. *Chen, S.*, *TED July 2021 3353-3358*
- Polycrystalline/Amorphous HfO<sub>2</sub> Bilayer Structure as a Gate Dielectric for  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> MOS Capacitors. *Yang, J.Y.*, +, *TED March 2021 1011-1015*
- Pt-Decorated Graphene Gate AlGaIn/GaN MIS-HEMT for Ultrahigh Sensitive Hydrogen Gas Detection. *Ahn, J.*, +, *TED March 2021 1255-1261*
- Quadruple Gate-Recessed AlGaIn/GaN Fin-Nanochannel Array Metal-Oxide-Semiconductor High-Electron Mobility Transistors. *Lee, H.*, +, *TED Jan. 2021 42-48*
- Recessed AlGaIn/GaN Schottky Barrier Diodes With TiN and NiN Dual Anodes. *Wang, T.*, +, *TED June 2021 2867-2871*
- Recessed Anode AlGaIn/GaN Schottky Barrier Diode for Temperature Sensor Application. *Pu, T.*, +, *TED Oct. 2021 5162-5166*
- Simulation Study of an Ultralow Switching Loss p-GaN Gate HEMT With Dynamic Charge Storage Mechanism. *Wang, F.*, +, *TED Jan. 2021 175-183*
- Single-Event Damage-Induced Gate-Leakage Mechanisms in AlGaIn/GaN High-Electron-Mobility Transistors. *Yue, S.*, +, *TED June 2021 2667-2672*
- Steep-Switching Fully Depleted Silicon-on-Insulator (FDSOI) Phase-Transition Field-Effect Transistor With Optimized HfO<sub>2</sub>/Al<sub>2</sub>O<sub>3</sub>-Multilayer-Based Threshold Switching Device. *Han, S.*, +, *TED March 2021 1358-1363*
- Suppression of Gate Leakage Current in Ka-Band AlGaIn/GaN HEMT With 5-nm SiN Gate Dielectric Grown by Plasma-Enhanced ALD. *Zhang, S.*, +, *TED Jan. 2021 49-52*
- Switching Performance Analysis of 3.5 kV Ga<sub>2</sub>O<sub>3</sub> Power FinFETs. *Jian, Z.A.*, +, *TED Feb. 2021 672-678*
- Temporal Electron-Spin Splitter Based on a Semiconductor Microstructure Constructed on Surface of InAs/Al<sub>x</sub>In<sub>1-x</sub>As Heterostructure by Patterning a Ferromagnetic Stripe and a Schottky-Metal Stripe. *Lu, M.*, +, *TED Feb. 2021 860-864*
- Thermal Design Rules of AlGaIn/GaN-Based Microwave Transistors on Diamond. *Gerrer, T.*, +, *TED April 2021 1530-1536*
- Time-Dependent Threshold Voltage Instability Mechanisms of p-GaN Gate AlGaIn/GaN HEMTs Under High Reverse Bias Conditions. *Li, S.*, +, *TED Jan. 2021 443-446*

- Tunable Electronic Trap Energy in Sol-Gel Processed Dielectrics. *Mondal, S.*, +, *TED March 2021 1190-1195*
- Understanding High-Energy 75-MeV Sulfur-Ion Irradiation-Induced Degradation in GaN-Based Heterostructures: The Role of the GaN Channel Layer. *Challa, S.R.*, +, *TED Jan. 2021 24-28*
- Unipolar Quantum Well InGaAs/AlGaAs Heterostructures With Impact Ionization for Efficient Low-Voltage Light-Emitting Devices. *Slipchenko, S.O.*, +, *TED June 2021 2823-2828*
- Aluminum gallium nitride**
- A High RF-Performance AlGaN/GaN HEMT With Ultrathin Barrier and Stressor *In Situ* SiN. *Wu, S.*, +, *TED Nov. 2021 5553-5558*
- Analytical Modeling of Sheet Carrier Density and on-Resistance in Polarization Super-Junction HFETs. *Yan, H.*, +, *TED Nov. 2021 5714-5719*
- Enhancing the Sensitivity of GaN High Electron-Mobility Transistors-Based pH Sensor by Dual Function of Monolithic Integrated Planar Multi-Channel and Ultraviolet Light. *Yang, X.*, +, *TED Dec. 2021 6437-6443*
- High-Temperature Sensitivity of a Depletion-Mode AlGaN/GaN MIS-HEMT. *Mutsafi, Z.*, +, *TED Nov. 2021 5695-5700*
- Lateral AlGaN/GaN Schottky Barrier Diode With Arrayed p-GaN Islands Termination. *Wang, H.*, +, *TED Dec. 2021 6046-6051*
- Modified Small Signal Circuit of AlGaN/GaN MOS-HEMTs Using Rational Functions. *Jadhav, A.*, +, *TED Dec. 2021 6059-6064*
- Part I: Physical Insights Into Dynamic  $R_{ON}$  Behavior and a Unique Time-Dependent Critical Stress Voltage in AlGaN/GaN HEMTs. *Gupta, S.D.*, +, *TED Nov. 2021 5720-5727*
- Polarization-Engineered Quaternary Barrier InAlGaN/AlGaN Heterostructure Field-Effect Transistors Toward Robust High-Frequency Power Performance in AlGaN Channel Electronics. *Li, L.*, +, *TED Nov. 2021 5535-5540*
- Rational Superlattice Electron Blocking Layer Design for Boosting the Quantum Efficiency of 371 nm Ultraviolet Light-Emitting Diodes. *Du, P.*, +, *TED Dec. 2021 6255-6261*
- Small-Signal Analysis of Channel Resistance  $R_L$  at Low Gate Bias Voltages in AlGaN/GaN HEMTs. *Kaushik, P.K.*, +, *TED Dec. 2021 6033-6038*
- Surface State Spectrum of AlGaN/AlN/GaN Extracted From Static Equilibrium Electrostatics. *Yu, H.*, +, *TED Nov. 2021 5559-5564*
- Aluminum nitride**
- Surface State Spectrum of AlGaN/AlN/GaN Extracted From Static Equilibrium Electrostatics. *Yu, H.*, +, *TED Nov. 2021 5559-5564*
- Ammonia**
- Flexible Room Temperature Ammonia Gas Sensor Based on Low-Temperature Tuning of Functional Groups in Grapheme. *Sett, A.*, +, *TED July 2021 3181-3188*
- Room-Temperature Hydrogen- and Ammonia Gas-Sensing Characteristics of a GaN-Based Schottky Diode Synthesized With a Hybrid Surface Structure. *Chen, W.*, +, *TED Feb. 2021 761-768*
- Ammonium compounds**
- Enhanced pH Sensitivity of AlGaN/GaN Ion-Sensitive Field-Effect Transistor by Recess Process and Ammonium Hydroxide Treatment. *He, Y.*, +, *TED March 2021 1250-1254*
- Amorphous semiconductors**
- A Physically Based Compact Model for IGZO Transistors. *Rios, R.*, +, *TED April 2021 1664-1669*
- Amorphous InGaZnO Thin-Film Transistors With Sub-10-nm Channel Thickness and Ultrascaled Channel Length. *Samanta, S.*, +, *TED March 2021 1050-1056*
- Amorphous  $ZnSn_xO_y$  Fabricated at Room-Temperature for Flexible pH-EG-FET Sensor. *Singh, K.*, +, *TED Feb. 2021 793-797*
- Analytical Surface Potential-Based Compact Model for Independent Dual Gate a-IGZO TFT. *Guo, J.*, +, *TED April 2021 2049-2055*
- Capacitance Scaling in  $In_{0.71}Ga_{0.29}As/InP$  MOSFETs With Self-Aligned a:Si Spacers. *Garigapati, N.S.*, +, *TED Aug. 2021 3762-3767*
- Carrier Velocity in Amorphous Metal-Oxide-Semiconductor Transistors. *Wang, X.*, +, *TED Jan. 2021 125-131*
- Compact DC and Quasi-Static Capacitances Modeling of a-Si:H TFTs, Including Parasitic Capacitances. *Lime, F.*, +, *TED July 2021 3384-3389*
- Degradation Behavior of Etch-Stopper-Layer Structured a-InGaZnO Thin-Film Transistors Under Hot-Carrier Stress and Illumination. *Lin, D.*, +, *TED Feb. 2021 556-559*
- Effect of Femtosecond Laser Postannealing on a-IGZO Thin-Film Transistors. *Lee, J.*, +, *TED July 2021 3371-3378*
- Effects of Ambient/Carrier Gas on Amorphous InGaZnO-Based Thin-Film Transistors Using Ultrasonic Spray Pyrolysis Deposition. *Liu, H.*, +, *TED June 2021 2729-2735*
- Enhanced Thermal Stability of Elevated-Metal Metal-Oxide Thin-Film Transistors via Low-Temperature Nitrogen Post-Annealing. *Wei, Y.*, +, *TED April 2021 1649-1653*
- Formation of F-Doped Offset Region for Spray Pyrolyzed Self-Aligned Coplanar Amorphous Zinc-Tin-Oxide Thin-Film Transistor by  $NF_3$  Plasma Treatment. *Kim, Y.G.*, +, *TED March 2021 1057-1062*
- HfZrO<sub>x</sub>-Based Switchable Diode for Logic-in-Memory Applications. *Kao, R.*, +, *TED Feb. 2021 545-549*
- High Field Temperature-Independent Field-Effect Mobility of Amorphous Indium-Gallium-Zinc Oxide Thin-Film Transistors: Understanding the Importance of Equivalent-Oxide-Thickness Downscaling. *Han, K.*, +, *TED Jan. 2021 118-124*
- High-Performance Thin-Film IGZO Schottky Diodes With Sputtered PdO<sub>x</sub> Anode. *Yan, S.*, +, *TED Sept. 2021 4444-4449*
- Hot-Carrier Effects in a-InGaZnO Thin-Film Transistors Under Pulse Drain Bias Stress. *Song, T.*, +, *TED June 2021 2742-2747*
- Hydrogen Behavior in Top Gate Amorphous In-Ga-Zn-O Device Fabrication Process During Gate Insulator Deposition and Gate Insulator Etching. *Song, A.*, +, *TED June 2021 2723-2728*
- Hydrogenation of Mg-Doped InGaZnO Thin-Film Transistors for Enhanced Electrical Performance and Stability. *Abliz, A.*, *TED July 2021 3379-3383*
- Indirectly Heated Switch as a Platform for Nanosecond Probing of Phase Transition Properties in Chalcogenides. *Wainstein, N.*, +, *TED March 2021 1298-1303*
- Low Subthreshold Swing and High Performance of Ultrathin PEALD InGaZnO Thin-Film Transistors. *Jeong, S.*, +, *TED April 2021 1670-1675*
- Low-Temperature Self-Aligned-Silicide-Capable Transistor Process Using Solid-Phase-Epitaxy and Lift-Off for Hybrid Substrates. *Tarighat, R.S.*, +, *TED Jan. 2021 244-250*
- On the Optimization of Performance and Reliability in a-InGaZnO Thin-Film Transistors by Versatile Light Shielding Design. *Kuo, C.*, +, *TED April 2021 1654-1658*
- Roles of Gate Voltage and Stress Power in Self-Heating Degradation of a-InGaZnO Thin-Film Transistors. *Du, M.*, +, *TED April 2021 1644-1648*
- Room-Temperature Negative Differential Resistance in Amorphous Carbon: The Role of Electron Trapping Defects at Device Interfaces. *Le, P.Y.*, +, *TED Feb. 2021 720-725*
- Simulation and Experimental Validation of the Uniformity of Thermally Evaporated Amorphous Selenium Films for Large-Area Imaging and Radiation Detection Applications. *Farahmandzadeh, M.*, +, *TED Feb. 2021 626-631*
- Study of a High-Performance Chemoresistive Ethanol Gas Sensor Synthesized With Au Nanoparticles and an Amorphous IGZO Thin Film. *Peng, R.*, +, *TED Feb. 2021 753-760*
- Tunable Negative Differential Resistance and Resistive Switching Properties of Amorphous WO<sub>x</sub> Devices. *Zhang, K.*, +, *TED Aug. 2021 3807-3812*
- Vertical Electric Field-Induced Abnormal Capacitance-Voltage Electrical Characteristics in a-InGaZnO TFTs. *Kuo, C.*, +, *TED Sept. 2021 4431-4436*
- Amorphous silicon**
- The Photosensitive Mechanism of Gap-Type Amorphous Silicon TFT. *Tai, Y.*, +, *TED Dec. 2021 6177-6181*
- Amorphous state**
- Stress Engineering as a Strategy to Achieve High Ferroelectricity in Thick Hafnia Using Interlayer. *Joh, H.*, +, *TED May 2021 2538-2542*
- Amplifiers**
- CMOS-MEMS Accelerometer With Stepped Suspended Gate FET Array: Design & Analysis. *Martha, P.*, +, *TED Oct. 2021 5133-5141*

- Design and Simulation of a 0.23-THz Extended Interaction Amplifier With Trapezoid-Neck Cavities. *Ji, Y.*, +, *TED June 2021 3010-3014*
- Simulation of Drive-Induced Oscillations in Helix Traveling-Wave Tubes. *Hagermann, M.*, +, *TED Jan. 2021 353-358*
- Analog circuits**
- Hybrid Design Using Metal–Oxide– Semiconductor Field-Effect Transistors and Negative-Capacitance Field-Effect Transistors for Analog Circuit Applications. *Han, K.*, +, *TED Feb. 2021 846-852*
- Analog storage**
- OxRRAM-Based Analog in-Memory Computing for Deep Neural Network Inference: A Conductance Variability Study. *Doevenspeck, J.*, +, *TED May 2021 2301-2305*
- Analog-digital conversion**
- CMOS Image Sensor With Two-Step Single-Slope ADC Using Differential Ramp Generator. *Park, S.*, +, *TED Oct. 2021 4966-4971*
- Impact of Random Phase Distribution in Ferroelectric Transistors-Based 3-D NAND Architecture on In-Memory Computing. *Choe, G.*, +, *TED May 2021 2543-2548*
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- Analysis of the Effect of Residual Holes on Lateral Migration During the Retention Operation in 3-D NAND Flash Memory. *Kim, S.*, +, *TED Dec. 2021 6094-6099*
- Analytical Modeling of Sheet Carrier Density and on-Resistance in Polarization Super-Junction HFETs. *Yan, H.*, +, *TED Nov. 2021 5714-5719*
- Analytical Modeling, Design, and Performance Analysis of a Micromirror for Space-Based Multiobject Spectroscopy. *Kumar, A.*, +, *TED Nov. 2021 5773-5778*
- Approximate Analytical Solution to the Temperature Field in Annular Thermoelectric Generator Made of Temperature-Dependent Material. *Niu, W.*, +, *TED Dec. 2021 6386-6392*
- Bridging TCAD and AI: Its Application to Semiconductor Design. *Jeong, C.*, +, *TED Nov. 2021 5364-5371*
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- Efficient TCAD Thermal Analysis of Semiconductor Devices. *Catoggio, E.*, +, *TED Nov. 2021 5462-5468*
- Annealing**
- A Highly Efficient Annealing Process With Supercritical N<sub>2</sub>O at 120 °C for SiO<sub>2</sub>/4H–SiC Interface. *Wang, M.*, +, *TED April 2021 1841-1846*
- A Novel Analytical Model for Ohmic Contacts to Planar Devices: Theoretical Design and Experimental Verification. *Sun, Z.*, +, *TED Jan. 2021 299-306*
- Analysis of Mo Sidewall Ohmic Contacts to InGaAs Fins. *Choi, D.*, +, *TED Oct. 2021 4847-4853*
- Anomalous Behavior of Gate Current and TDDB Lifetime by Constant Voltage Stress in NO-Annealed SiC-MOSFETs. *Murakami, E.*, +, *TED March 2021 1207-1213*
- Back-Channel-Etched IGZO TFTs With Cu-Based Multilayer Electrodes Using MoAl Alloy and MoMn Alloy as Buffer Layers. *Xu, K.*, +, *TED Dec. 2021 6202-6207*
- Boron-Doped Diamond MOSFETs With High Output Current and Extrinsic Transconductance. *Liu, J.*, +, *TED Aug. 2021 3963-3967*
- Breakdown Voltage Enhancement in ScAlN/GaN High-Electron-Mobility Transistors by High-*k* Bismuth Zinc Niobate Oxide. *Cheng, J.*, +, *TED July 2021 3333-3338*
- Channel Properties of Ga<sub>2</sub>O<sub>3</sub>-on-SiC MOSFETs. *Wang, Y.*, +, *TED March 2021 1185-1189*
- Characterization of Al<sub>2</sub>O<sub>3</sub>/LaAlO<sub>3</sub>/SiO<sub>2</sub> Gate Stack on 4H-SiC After Post-Deposition Annealing. *Huang, L.*, +, *TED April 2021 2133-2137*
- CMOS-Compatible Ti/TiN/Al Refractory Ohmic Contact for GaAs Heterojunction Bipolar Transistors Grown on Ge/Si Substrate. *Wang, Y.*, +, *TED Dec. 2021 6065-6068*
- Comprehensive Annealing Effects on AlGaN/GaN Schottky Barrier Diodes With Different Work-Function Metals. *Zhang, T.*, +, *TED June 2021 2661-2666*
- Effect of Femtosecond Laser Postannealing on a-IGZO Thin-Film Transistors. *Lee, J.*, +, *TED July 2021 3371-3378*
- Enhanced Linearity in CBRAM Synapse by Post Oxide Deposition Annealing for Neuromorphic Computing Applications. *Hsu, C.*, +, *TED Nov. 2021 5578-5584*
- Enhanced Thermal Stability of Elevated-Metal Metal-Oxide Thin-Film Transistors via Low-Temperature Nitrogen Post-Annealing. *Wei, Y.*, +, *TED April 2021 1649-1653*
- Enhancement-Mode Atomic-Layer-Deposited In<sub>2</sub>O<sub>3</sub> Transistors With Maximum Drain Current of 2.2 A/mm at Drain Voltage of 0.7 V by Low-Temperature Annealing and Stability in Hydrogen Environment. *Si, M.*, +, *TED March 2021 1075-1080*
- Experimental Investigation of As Preamorphization Implant on Electrical Property of Ti-Based Silicide Contacts. *Mao, S.*, +, *TED April 2021 1835-1840*
- Fabrication and Characterization of High-Voltage NiO/ $\beta$ -Ga<sub>2</sub>O<sub>3</sub> Heterojunction Power Diodes. *Luo, H.*, +, *TED Aug. 2021 3991-3996*
- Ferroelectric Hafnium Zirconium Oxide Compatible With Back-End-of-Line Process. *Hur, J.*, +, *TED July 2021 3176-3180*
- Flexible High-Temperature Polycrystalline Silicon Thin Film Transistor on Metal Foil With S/D Doped by Diffusion. *Yu, B.*, +, *TED Aug. 2021 3857-3862*
- Gate-First Negative Capacitance Field-Effect Transistor With Self-Aligned Nickel-Silicide Source and Drain. *Kim, S.*, +, *TED Sept. 2021 4754-4757*
- High-Performance Amorphous InGaZnO Thin-Film Transistor Gated by HfAlO<sub>x</sub> Dielectric With Ultralow Subthreshold Swing. *Zhu, L.*, +, *TED Dec. 2021 6154-6158*
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- High-Resistance State Reduction During Initial Cycles of AlO<sub>x</sub>N<sub>y</sub>-Based RRAM. *Duan, Y.*, +, *TED Nov. 2021 5606-5611*
- Impact of Nonuniform Ozone Anneal Treatment on the Resistance Levels in an IGZO-ReRAM Fabricated on ITO-Coated Glass Substrate. *Kishore, R.*, +, *TED Dec. 2021 6087-6093*
- Improved RF Power Performance of AlGaN/GaN HEMT Using by Ti/Au/Al/Ni/Au Shallow Trench Etching Ohmic Contact. *Lu, H.*, +, *TED Oct. 2021 4842-4846*
- Improvement of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> MIS-SBD Interface Using Al-Reacted Interfacial Layer. *He, M.*, +, *TED July 2021 3314-3319*
- Improvement of Both n- and p-Channel Mobilities in 4H-SiC MOSFETs by High-Temperature N<sub>2</sub> Annealing. *Tachiki, K.*, +, *TED Feb. 2021 638-644*
- InAlN/GaN HEMT on Si With f<sub>max</sub> = 270 GHz. *Cui, P.*, +, *TED March 2021 994-999*
- Investigation of Metal Interconnect for Wafer-Level and Sealable Miniaturized MEMS Encapsulation. *Tsai, Y.*, +, *TED Nov. 2021 5779-5783*
- Low Thermal Budget Fabrication and Performance Comparison of MFM Capacitors With Thermal and Plasma-Enhanced Atomic Layer Deposited Hf<sub>0.45</sub>Zr<sub>0.55</sub>O<sub>x</sub> Ferroelectrics. *Xiao, D.*, +, *TED Dec. 2021 6359-6364*
- Low-Frequency Noise Analysis of the Optimized Post High-*k* Deposition Annealing in FinFET Technology. *Deng, W.*, +, *TED March 2021 1202-1206*
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- Modeling of Repeated FET Hot-Carrier Stress and Anneal Cycles Using Si–H Bond Dissociation/Passivation Energy Distributions. *Vandemaele, M.*, +, *TED April 2021 1454-1460*
- Nonalloyed Ohmic Contacts in AlGaN/GaN HEMTs With MOCVD Regrowth of InGaN for *Ka*-Band Applications. *Cakmak, H.*, +, *TED March 2021 1006-1010*
- Performance and Reliability Optimization of Supercritical-Nitridation-Treated AlGaN/GaN High-Electron-Mobility Transistors. *Wu, P.*, +, *TED Sept. 2021 4317-4321*
- Self-Heating Stress-Induced Severe Humps in Transfer Characteristics of Amorphous InGaZnO Thin-Film Transistors. *Yang, H.*, +, *TED Dec. 2021 6197-6201*



- Solution-Driven HfLaO<sub>x</sub>-Based Gate Dielectrics for Thin Film Transistors and Unipolar Inverters. Wang, W., +, *TED Sept. 2021 4437-4443*
- Structural and Electrical Characteristics of ALD-TiO<sub>2</sub>/SiON/n-Si Gate-Stack for Advanced CMOS Device Applications. Gupta, R., +, *TED June 2021 2625-2632*
- Sub-mA/cm<sup>2</sup> Dark Current Density, Buffer-Less Germanium (Ge) Photodiodes on a 200-nm Ge-on-Insulator Substrate. Lin, Y., +, *TED April 2021 1730-1737*
- The Influence of Top and Bottom Metal Electrodes on Ferroelectricity of Hafnia. Lee, Y., +, *TED Feb. 2021 523-528*
- Thermally Robust Perpendicular SOT-MTJ Memory Cells With STT-Assisted Field-Free Switching. Tsou, Y., +, *TED Dec. 2021 6623-6628*
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- Anodes**
- A High-Current-Density Electron Beam for Millimeter-Wave Amplifiers. Cook, A.M., +, *TED June 2021 3040-3044*
- A Modified CLTdsCR With Low Leakage and Low Capacitance for ESD Protection. Sun, K., +, *TED Feb. 2021 934-937*
- An Axial Output Relativistic Magnetron Fed by a Split Cathode and Magnetically Insulated by a Low-Power Solenoid. Leopold, J.G., +, *TED Oct. 2021 5227-5231*
- An Efficient Inverted Relativistic Magnetron With Virtual Cathode. Cheng, R., +, *TED May 2021 2499-2503*
- An Improved Compact and High-Efficiency Relativistic Magnetron With TE<sub>11</sub> Mode Radiation. Yang, W., +, *TED Nov. 2021 5841-5845*
- Analytic Solutions for Space-Charge-Limited Current Density From a Sharp Tip. Harsha, N.R.S., +, *TED Dec. 2021 6525-6531*
- Compact High Efficiency Relativistic Magnetron With TE<sub>11</sub> Mode Output. Fang, X., +, *TED Aug. 2021 4110-4115*
- Development of a Magnetic Cusp Gun for a 1-THz Harmonic Gyrotron. Li, F., +, *TED Dec. 2021 6505-6511*
- Electron-Optic System With a Converged Sheet Electron Beam for a 0.2-THz Traveling-Wave Tube. Navrotsky, I.A., +, *TED Feb. 2021 798-803*
- Electrostatic Design and Fabrication a New Tunable Perveance Pierce Electron Gun. Gharaati, A., +, *TED Jan. 2021 318-323*
- Experimental Generation of 1.1-kA Gyration Electron Beam Current From an Explosive Emission Cathode Magnetron Injection Gun. An, C., +, *TED Sept. 2021 4664-4668*
- High-Performance Thin-Film IGZO Schottky Diodes With Sputtered PdO<sub>x</sub> Anode. Yan, S., +, *TED Sept. 2021 4444-4449*
- Lateral AlGaIn/GaN Schottky Barrier Diode With Arrayed p-GaN Islands Termination. Wang, H., +, *TED Dec. 2021 6046-6051*
- Performance Enhancement of Terahertz Laser Diode via Resonant Cavities. Liu, Y., +, *TED Dec. 2021 6465-6469*
- Pseudospark-Driven High-Current Miniaturized Voltage-Tunable Sheet-Electron-Beam Source. Kumar, N., +, *TED Dec. 2021 6482-6486*
- Simulation Study of a p-GaN HEMT With an Integrated Schottky Barrier Diode. Yi, B., +, *TED Dec. 2021 6039-6045*
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- Design of a Fan-Out Panel-Level SiC MOSFET Power Module Using Ant Colony Optimization-Back Propagation Neural Network. Qian, Y., +, *TED July 2021 3460-3467*
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- Laser-Induced Graphene Printed Wearable Flexible Antenna-Based Strain Sensor for Wireless Human Motion Monitoring. Sindhu, B., +, *TED July 2021 3189-3194*
- Antiferroelectricity**
- Impact of the Nonlinear Dielectric Hysteresis Properties of a Charge Trap Layer in a Novel Hybrid High-Speed and Low-Power Ferroelectric or Antiferroelectric HSO/HZO Boosted Charge Trap Memory. Ali, T., +, *TED April 2021 2098-2106*
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- Multilayer Nanomagnet Threshold Logic. Zhou, P., +, *TED April 2021 1944-1949*
- Antimony compounds**
- A Robust and Efficient Compact Model for Phase-Change Memory Circuit Simulations. Chen, X., +, *TED Sept. 2021 4404-4410*
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- Modeling of Photovoltaic Solar Cell Based on CuSbS<sub>2</sub> Absorber for the Enhancement of Performance. Sadanand, ., +, *TED March 2021 1121-1128*
- Tunable Alloying Improved Wide Spectrum UV-Vis-NIR and Polarization-Sensitive Photodetector Based on Sb-S-Se Nanowires. Yu, Y., +, *TED Aug. 2021 3887-3893*
- Antireflection coatings**
- Controlling Phosphor Particle Distribution for High-Angular-Color-Uniformity and Low-Cost LEDs Based on Thermalcapillary Flow. Liu, J., +, *TED Feb. 2021 592-596*
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- Pulse Lengthening of the Microwave Generated by TM<sub>02</sub> Mode Ka-Band RBWO Operating With Low Guiding Magnetic Field. Wang, D., +, *TED June 2021 3015-3020*
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Advanced DFT–NEGF Transport Techniques for Novel 2-D Material and Device Exploration Including HfS<sub>2</sub>/WSe<sub>2</sub> van der Waals Heterojunction TFET and WTe<sub>2</sub>/WS<sub>2</sub> Metal/Semiconductor Contact. *Afzal, A.*, +, *TED Nov. 2021 5372-5379*

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Low Subthreshold Swing and High Performance of Ultrathin PEALD InGaZnO Thin-Film Transistors. *Jeong, S.*, +, *TED April 2021 1670-1675*

Low Thermal Budget Fabrication and Performance Comparison of MFM Capacitors With Thermal and Plasma-Enhanced Atomic Layer Deposited Hf<sub>0.45</sub>Zr<sub>0.55</sub>O<sub>x</sub> Ferroelectrics. *Xiao, D.*, +, *TED Dec. 2021 6359-6364*

Origin of Ambipolar Behavior in p-Type Tin Monoxide Semiconductors: Impact of Oxygen Vacancy Defects. *Kim, T.*, +, *TED Sept. 2021 4467-4472*

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System-Level IEC ESD Failures in High-Voltage DeNMOS-SCR: Physical Insights and Design Guidelines. *Kranthi, N.K.*, +, *TED Sept. 2021 4242-4250*

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Electric-Field-Dependence Mechanism for Cosmic Ray Failure in Power Semiconductor Devices. *Oda, T.*, +, *TED July 2021 3505-3512*

Impact Ionization Coefficients in (Al<sub>x</sub>Ga<sub>1-x</sub>)<sub>0.52</sub>In<sub>0.48</sub>P and Al<sub>x</sub>Ga<sub>1-x</sub>As Lattice-Matched to GaAs. *Lewis, H.I.J.*, +, *TED Aug. 2021 4045-4050*

Investigation on Single Pulse Avalanche Failure of 1200-V SiC MOSFETs via Optimized Thermoelectric Simulation. *Bai, Z.*, +, *TED March 2021 1168-1175*

New Failure Mechanism Induced by Current Limit for Superjunction MOSFET Under Single-Pulse UIS Stress. *Tong, X.*, +, *TED July 2021 3483-3489*

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- Random Telegraph Signal in n<sup>+</sup>/p-Well CMOS Single-Photon Avalanche Diodes. *Jiang, W.*, +, *TED June 2021 2764-2769*
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- Design of a Fan-Out Panel-Level SiC MOSFET Power Module Using Ant Colony Optimization-Back Propagation Neural Network. *Qian, Y.*, +, *TED July 2021 3460-3467*
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- High-Power Backward-Wave Oscillator Using Folded Waveguide With Distributed Power Extraction Operating at an Exceptional Point. *Mealy, T.*, +, *TED July 2021 3588-3595*
- Pulse Lengthening of the Microwave Generated by TM<sub>02</sub> Mode *Ka*-Band RBWO Operating With Low Guiding Magnetic Field. *Wang, D.*, +, *TED June 2021 3015-3020*
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- Creation of Step-Shaped Energy Band in a Novel Double-Gate GNR-FET to Diminish Ambipolar Conduction. *K. Anvarifard, M.*, +, *TED May 2021 2549-2555*
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- Guidelines for Ferroelectric-Semiconductor Tunnel Junction Optimization by Band Structure Engineering. *Chang, P.*, +, *TED July 2021 3526-3531*
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A Physical Model of Contact Resistance in Ti-Contacted Graphene-Based Field Effect Transistors. *Wang, B.*, +, *TED Feb. 2021 892-898*

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Asymmetric Au Electrodes-Induced Self-Powered Organic-Inorganic Perovskite Photodetectors. *Zhao, K.*, +, *TED March 2021 1149-1154*

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Effective Leakage Current Reduction in GaN Ultraviolet Avalanche Photodiodes With an Ion-Implantation Isolation Method. *Cho, M.*, +, *TED June 2021 2759-2763*

Enhanced Photodetection Performance in Graphene-Assisted Tunneling Photodetector. *You, C.*, +, *TED April 2021 1702-1709*

Exceptional Responsivity (>6 kA/W) and Dark Current (<70 fA) Tradeoff of n-Ga<sub>2</sub>O<sub>3</sub>/p-CuO Quasi-Heterojunction-Based Deep UV Photodetector. *Kumar, A.*, +, *TED Jan. 2021 144-151*

Low-Temperature Electrical Performance of PureB Photodiodes Revealing Al-Metallization-Related Degradation of Dark Currents. *Knezevic, T.*, +, *TED June 2021 2810-2817*

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High-Detectivity and Stable Planar MAPbI<sub>3</sub>/IDT-BT Photodetectors With Assisted MoO<sub>3</sub> Interlayer. *Zhao, K.*, +, *TED Dec. 2021 6266-6272*

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A High-Efficiency Double-Side Silicon-Embedded Inductor for Integrated DC-DC Converter Applications. *Lv, G.*, +, *TED Sept. 2021 4801-4804*

Efficient 1-V Boost Converter Using Sub-50-mV NEMS Without Body Bias. *Saha, S.*, +, *TED June 2021 2944-2950*

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Gas Sensor Based on Semihydrogenated and Semifluorinated h-BN for SF<sub>6</sub> Decomposition Components Detection. *Peng, Z.*, +, *TED April 2021 1878-1885*

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Fully On-Chip MAC at 14 nm Enabled by Accurate Row-Wise Programming of PCM-Based Weights and Parallel Vector-Transport in Duration-Format. *Narayanan, P.*, +, *TED Dec. 2021 6629-6636*

Model of the Weak Reset Process in HfO<sub>x</sub> Resistive Memory for Deep Learning Frameworks. *Majumdar, A.*, +, *TED Oct. 2021 4925-4932*

Noise-Resilient DNN: Tolerating Noise in PCM-Based AI Accelerators via Noise-Aware Training. *Kariyappa, S.*, +, *TED Sept. 2021 4356-4362*

OxRRAM-Based Analog in-Memory Computing for Deep Neural Network Inference: A Conductance Variability Study. *Doevenspeck, J.*, +, *TED May 2021 2301-2305*

#### Deep level transient spectroscopy

Implementation of RTCVD-SiN<sub>x</sub> Gate Dielectric Into Enhancement-Mode GaN MIS-HEMTs Fabricated on Ultrathin-Barrier AlGaIn/GaN-on-Si Platform. *Shi, W.*, +, *TED Sept. 2021 4274-4277*

Radiation Resistance of High-Voltage Silicon and 4H-SiC Power p-i-n Diodes. *Hazdra, P.*, +, *TED Jan. 2021 202-207*

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Tunable Electronic Trap Energy in Sol-Gel Processed Dielectrics. *Mondal, S.*, +, *TED March 2021 1190-1195*

#### Deep levels

Analysis and Modeling of Vertical Current Conduction and Breakdown Mechanisms in Semi-Insulating GaN Grown on GaN: Role of Deep Levels. *Stoklas, R.*, +, *TED May 2021 2365-2371*

Investigation of Endurance Behavior on HfZrO-Based Charge-Trapping FinFET Devices by Random Telegraph Noise and Subthreshold Swing Techniques. *Gong, T.*, +, *TED July 2021 3716-3719*

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#### Defect states

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Formation of Graphene-Silicon Junction by Room Temperature Reduction With Simultaneous Defects Removal. *Yi, H.*, +, *TED Feb. 2021 873-878*

Performance Improvement for Spray-Coated ZnO TFT by F Doping With Spray-Coated Zr-Al-O Gate Insulator. *Saha, J.K.*, +, *TED March 2021 1063-1069*

Statistical Characterization of Time-Dependent Variability Defects Using the Maximum Current Fluctuation. *Saraza-Canflanca, P.*, +, *TED Aug. 2021 4039-4044*

#### Degradation

Efficient Modeling of Charge Trapping at Cryogenic Temperatures—Part II: Experimental. *Michl, J.*, +, *TED Dec. 2021 6372-6378*

Lifetime Color Consistency Analysis of Cool-White LED Luminaires for General Applications. *Padmasali, A.N.*, +, *TED Nov. 2021 5634-5639*

Passivation of Solution-Processed a-IGZO Thin-Film Transistor by Solution Processable Zinc Porphyrin Self-Assembled Monolayer. *Zalte, M.B.*, +, *TED Nov. 2021 5920-5924*

PCM-Based Analog Compute-In-Memory: Impact of Device Non-Idealities on Inference Accuracy. *Sun, X.*, +, *TED Nov. 2021 5585-5591*

#### Delamination

A High-Efficiency IGBT Health Status Assessment Method Based on Data Driven. *Zhang, Z.*, +, *TED Jan. 2021 168-174*

#### Delay lines

Drive-Induced Backward-Wave Oscillations in Helix Traveling-Wave Tubes—A Case Study. *Hagermann, M.*, +, *TED Dec. 2021 6492-6497*

#### Delays

Aging-Aware Gate-Level Modeling for Circuit Reliability Analysis. *Zhang, Z.*, +, *TED Sept. 2021 4201-4207*

Air-Gap Technology With a Large Void-Fraction for Global Interconnect Delay Reduction. *Prawoto, C.*, +, *TED Oct. 2021 5078-5084*

The Complementary FET (CFET) 6T-SRAM. *Gupta, M.K.*, +, *TED Dec. 2021 6106-6111*

#### Density functional theory

A Novel Device to Implement Full Set of Three-Input Logic Gates Using a Naphthalene-Based Single-Molecule Field-Effect Transistor. *Fakheri, M.T.*, +, *TED Feb. 2021 733-738*

Efficient Bilayer Light-Emitting Diode Based on Distyrylarylene-Containing Polymers: Numerical and DFT Simulation. *Chouk, R.*, +, *TED Feb. 2021 578-583*

Electrical Degradation of *In Situ* SiN/AlGaIn/GaN MIS-HEMTs Caused by Dehydrogenation and Trap Effect Under Hot Carrier Stress. *Niu, X.*, +, *TED Sept. 2021 4283-4288*

Gas Sensor Based on Semihydrogenated and Semifluorinated h-BN for SF<sub>6</sub> Decomposition Components Detection. *Peng, Z.*, +, *TED April 2021 1878-1885*

- PbSnS<sub>2</sub>-Based Gas Sensor to Detect SF<sub>6</sub> Decompositions: DFT and NEGF Calculations. *Guo, H.*, +, *TED Oct. 2021 5322-5325*
- Performance Optimization of Monolayer 1T/1T'-2H MoX<sub>2</sub> Lateral Heterojunction Transistors. *Yin, D.*, +, *TED July 2021 3649-3657*
- Silicene/MoS<sub>2</sub> Heterojunction for High-Performance Photodetector. *Kharadi, M.A.*, +, *TED Jan. 2021 138-143*
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- Density measurement**
- Bifacial Heterojunction Back Contact Solar Cell: 29-mW/cm<sup>2</sup> Output Power Density in Standard Albedo Condition. *Sugiura, T.*, +, *TED Nov. 2021 5645-5651*
- Dentistry**
- Compact X-Ray Tube With Ceramic Vacuum Seal for Portable and Robust Dental Imaging. *Gupta, A.P.*, +, *TED Sept. 2021 4705-4710*
- Depression**
- Enhanced Linearity in CBRAM Synapse by Post Oxide Deposition Annealing for Neuromorphic Computing Applications. *Hsu, C.*, +, *TED Nov. 2021 5578-5584*
- Design automation**
- Foreword Special Issue on "New Simulation Methodologies for Next-Generation TCAD Tools". *Jungemann, C.*, +, *TED Nov. 2021 5346-5349*
- Design engineering**
- System-Level IEC ESD Failures in High-Voltage DeNMOS-SCR: Physical Insights and Design Guidelines. *Kranthi, N.K.*, +, *TED Sept. 2021 4242-4250*
- Desorption**
- Gas Sensor Based on Semihydrogenated and Semifluorinated h-BN for SF<sub>6</sub> Decomposition Components Detection. *Peng, Z.*, +, *TED April 2021 1878-1885*
- Detectors**
- 100- $\mu$ m-Scale High-Detectivity Infrared Detector With Thermopile/Absorber Double-Deck Structure Formed in (111) Silicon. *Xue, D.*, +, *TED Dec. 2021 6233-6239*
- Diagnostic radiography**
- Engineering of a Blocking Layer Structure for Low-Lag Operation of the a-PbO-Based X-Ray Detector. *Grynko, O.*, +, *TED May 2021 2335-2341*
- Stable and Printable Direct X-Ray Detectors Based on Micropyramid  $\omega$ -Bi<sub>2</sub>O<sub>3</sub> With Low Detection Limit. *Mao, L.*, +, *TED July 2021 3411-3416*
- Diamond**
- 1.26 W/mm Output Power Density at 10 GHz for Si<sub>3</sub>N<sub>4</sub> Passivated H-Terminated Diamond MOSFETs. *Yu, X.*, +, *TED Oct. 2021 5068-5072*
- A Study of Linearity of C-H Diamond FETs for S-Band Power Application. *Fu, Y.*, +, *TED Aug. 2021 3950-3955*
- Boron-Doped Diamond MOSFETs With High Output Current and Extrinsic Transconductance. *Liu, J.*, +, *TED Aug. 2021 3963-3967*
- Dramatic Improvement in the Rectifying Properties of Pd Schottky Contacts on  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> During Their High-Temperature Operation. *Hou, C.*, +, *TED April 2021 1791-1797*
- Electrical and Thermal Performance of Ga<sub>2</sub>O<sub>3</sub>-Al<sub>2</sub>O<sub>3</sub>-Diamond Super-Junction Schottky Barrier Diodes. *Mishra, A.*, +, *TED Oct. 2021 5055-5061*
- Fabrication of Dual-Barrier Planar Structure Diamond Schottky Diodes by Rapid Thermal Annealing. *Wang, J.*, +, *TED March 2021 1176-1180*
- High Output Power Density of 2DHG Diamond MOSFETs With Thick ALD-Al<sub>2</sub>O<sub>3</sub>. *Kudara, K.*, +, *TED Aug. 2021 3942-3949*
- Large Area Diamond Disk Growth Experiments and Thermomechanical Investigations for the Broadband Brewster Window in DEMO. *Aiello, G.*, +, *TED Sept. 2021 4669-4674*
- Low ON-Resistance (2.5 m $\Omega$  · cm<sup>2</sup>) Vertical-Type 2-D Hole Gas Diamond MOSFETs With Trench Gate Structure. *Tsunoda, J.*, +, *TED July 2021 3490-3496*
- Normally-OFF Diamond Reverse Blocking MESFET. *Canas, J.*, +, *TED Dec. 2021 6279-6285*
- Operation of Diamond Solution-Gated Field-Effect Transistor in the Frequency Domain. *Chang, X.*, +, *TED Dec. 2021 6400-6406*
- Quantum Dot With a Diamond-Shaped Channel MOSFET on a Bulk Si Substrate. *Gu, J.*, +, *TED Jan. 2021 405-410*
- Schottky Barrier Height Modulation of Zr/p-Diamond Schottky Contact by Inserting Ultrathin Atomic Layer-Deposited Al<sub>2</sub>O<sub>3</sub>. *Wang, J.*, +, *TED Dec. 2021 5995-6000*
- Suppressing Nitrogen-Vacancy Centers to Enhance Performance of Diamond Ultraviolet Photodetector via Growing With Tungsten. *Chang, X.*, +, *TED Dec. 2021 6228-6232*
- Thermal Design Rules of AlGaIn/GaN-Based Microwave Transistors on Diamond. *Gerrer, T.*, +, *TED April 2021 1530-1536*
- Transfer Doping in Diamond for Channel Doping and Electrical Contacts. *Huddleston, L.*, +, *TED Sept. 2021 4231-4236*
- Dielectric constant**
- Design and Investigation of Dielectrically Modulated Dual-Material Gate-Oxide-Stack Double-Gate TFET for Label-Free Detection of Biomolecules. *Singh, K.S.*, +, *TED Nov. 2021 5784-5791*
- Dielectric devices**
- A Comprehensive Gate and Drain Trapping/De trapping Noise Model and its Implications for Thin-Dielectric MOSFETs. *Asanovski, R.*, +, *TED Oct. 2021 4826-4833*
- Dielectric-Supported Staggered Dual Meander-Line Slow Wave Structure for an E-Band TWT. *Wang, H.*, +, *TED Jan. 2021 369-375*
- Dielectric hysteresis**
- Effect of Insertion of Dielectric Layer on the Performance of Hafnia Ferroelectric Devices. *Hwang, J.*, +, *TED Feb. 2021 841-845*
- Ferroelectric Undoped HfO<sub>x</sub> Capacitor With Symmetric Synaptic for Neural Network Accelerator. *Luo, J.*, +, *TED March 2021 1374-1377*
- Impact of the Nonlinear Dielectric Hysteresis Properties of a Charge Trap Layer in a Novel Hybrid High-Speed and Low-Power Ferroelectric or Antiferroelectric HSO/HZO Boosted Charge Trap Memory. *Ali, T.*, +, *TED April 2021 2098-2106*
- Study on the Roles of Charge Trapping and Fixed Charge on Subthreshold Characteristics of FeFETs. *Jin, C.*, +, *TED March 2021 1304-1312*
- Variability Analysis in a 3-D Multigranular Ferroelectric Capacitor. *Pandey, N.*, +, *TED Aug. 2021 3780-3786*
- Dielectric losses**
- Dispersion and Dielectric Attenuation Properties of a Wideband Double-Staggered Grating Waveguide for Subterahertz Sheet-Beam Traveling-Wave Amplifiers. *Shu, G.*, +, *TED Nov. 2021 5826-5833*
- Dielectric materials**
- A Novel Multipactor Suppression Circulator Using Transformation Dielectrics. *Li, B.*, +, *TED March 2021 1284-1288*
- Compact Multilayer Bandpass Filter Using Low-Temperature Additively Manufacturing Solution. *Li, M.*, +, *TED July 2021 3163-3169*
- Demonstration of CMOS-Compatible Multi-Level Graphene Interconnects With Metal Vias. *Agashiwala, K.*, +, *TED April 2021 2083-2091*
- Electrical and Reliability Characteristics of FinFETs With High-*k* Gate Stack and Plasma Treatments. *Li, Y.*, +, *TED Jan. 2021 4-9*
- Electrostatic Engineering Using Extreme Permittivity Materials for Ultra-Wide Bandgap Semiconductor Transistors. *Kalarickal, N.K.*, +, *TED Jan. 2021 29-35*
- High-Voltage a-IGZO TFTs With the Stair Gate-Dielectric Structure. *Yang, G.*, +, *TED Sept. 2021 4462-4466*
- Inelastic Electron Tunneling Spectroscopy: Investigation of Bulk Dielectrics and Molecules. *Kim, Y.*, +, *TED April 2021 1411-1419*
- Sputtered Oxide Thin-Film Transistors With Tunable Synaptic Spiking Behavior at 1 V. *Fu, Y.M.*, +, *TED June 2021 2736-2741*
- Suppression of Gate Leakage Current in Ka-Band AlGaIn/GaN HEMT With 5-nm SiN Gate Dielectric Grown by Plasma-Enhanced ALD. *Zhang, S.*, +, *TED Jan. 2021 49-52*
- Using Anisotropic Insulators to Engineer the Electrostatics of Conventional and Tunnel Field-Effect Transistors. *Bennett, R.K.A.*, +, *TED Feb. 2021 865-872*
- Dielectric measurement**
- Dispersion and Dielectric Attenuation Properties of a Wideband Double-Staggered Grating Waveguide for Subterahertz Sheet-Beam Traveling-Wave Amplifiers. *Shu, G.*, +, *TED Nov. 2021 5826-5833*

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- An Interface-Induced Dielectric Properties Degradation in Heterogeneous Stacked Device With P(VDF-TrFE)-Based Ferroelectric Polymers. *Chen, Y.*, +, *TED Feb. 2021 739-745*
- Effect of Insertion of Dielectric Layer on the Performance of Hafnia Ferroelectric Devices. *Hwang, J.*, +, *TED Feb. 2021 841-845*
- Ferroelectric Hafnium Zirconium Oxide Compatible With Back-End-of-Line Process. *Hur, J.*, +, *TED July 2021 3176-3180*
- Ferroelectric Undoped HfO<sub>x</sub> Capacitor With Symmetric Synaptic for Neural Network Accelerator. *Luo, J.*, +, *TED March 2021 1374-1377*
- Impact of Charge Trapping and Depolarization on Data Retention Using Simultaneous  $P-V$  and  $I-V$  in HfO<sub>2</sub>-Based Ferroelectric FET. *Higashi, Y.*, +, *TED Sept. 2021 4391-4396*
- Influence of High-Pressure Annealing Conditions on Ferroelectric and Interfacial Properties of Zr-Rich Hf<sub>x</sub>Zr<sub>1-x</sub>O<sub>2</sub> Capacitors. *Das, D.*, +, *TED April 2021 1996-2002*
- Nonconventional Analog Comparators Based on Graphene and Ferroelectric Hafnium Zirconium Oxide. *Liu, J.*, +, *TED March 2021 1334-1339*
- Quantitative Characterization of Ferroelectric/Dielectric Interface Traps by Pulse Measurements. *Li, J.*, +, *TED March 2021 1214-1220*
- Stress Engineering as a Strategy to Achieve High Ferroelectricity in Thick Hafnia Using Interlayer. *Joh, H.*, +, *TED May 2021 2538-2542*
- The Critical Role of Charge Balance on the Memory Characteristics of Ferroelectric Field-Effect Transistors. *Si, M.*, +, *TED Oct. 2021 5108-5113*
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- Variability Analysis in a 3-D Multigranular Ferroelectric Capacitor. *Pandey, N.*, +, *TED Aug. 2021 3780-3786*

**Dielectric thin films**

- CAD-Oriented Equivalent Circuit Modeling of a Two-Port Ground-Shielded MIM Capacitor. *Moctezuma-Pascual, E.*, +, *TED Feb. 2021 923-927*
- Solution-Driven HfLaO<sub>x</sub>-Based Gate Dielectrics for Thin Film Transistors and Unipolar Inverters. *Wang, W.*, +, *TED Sept. 2021 4437-4443*
- Tunable Electronic Trap Energy in Sol-Gel Processed Dielectrics. *Mondal, S.*, +, *TED March 2021 1190-1195*

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- An Empirical Investigation on the Effect of Oxygen Vacancy in ZrO<sub>2</sub> Thin Film on the Frequency-Dependent Capacitance Degradation in the Metal-Insulator-Metal Capacitor. *Han, D.H.*, +, *TED Nov. 2021 5753-5757*
- Design and Fabrication of 1.92 kV 4H-SiC Super-Junction SBD With Wide-Trench Termination. *Wang, B.*, +, *TED Nov. 2021 5674-5681*
- Design and Performance of Additively Manufactured In-Circuit Board Planar Capacitors. *Sokol, D.*, +, *TED Nov. 2021 5747-5752*
- Fabrication of an Electrostatic Actuated Dielectric Mirror With Free-Standing Layers of Polymer. *Vergara, P.*, +, *TED Dec. 2021 6240-6248*
- High-Performance Atomic-Layer-Deposited Indium Oxide 3-D Transistors and Integrated Circuits for Monolithic 3-D Integration. *Si, M.*, +, *TED Dec. 2021 6605-6609*
- Materials to Systems Co-Optimization Platform for Rapid Technology Development Targeting Future Generation CMOS Nodes. *Bazizi, E.M.*, +, *TED Nov. 2021 5358-5363*
- Permittivity Characterization of Dielectric Surfaces Using Nanofabricated In-Plane Capacitors. *Mousavi Karimi, Z.*, +, *TED Aug. 2021 4033-4038*

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- A Nonlinearized Lumped-Charge Model for Power Semiconductor Devices. *Colalongo, L.*, +, *TED Aug. 2021 3974-3981*
- Device Parameter-Based Analytical Modeling of Power Supply Induced Jitter in CMOS Inverters. *Arora, P.*, +, *TED July 2021 3268-3275*
- Nonuniform Space Charge Limited Current for 2-D Bipolar Flow in Vacuum Diode. *Zhu, Y.B.*, +, *TED Dec. 2021 6538-6545*

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- Design, Microfabrication, and Characterization of a Subterahertz-Band High-Order Overmoded Double-Staggered Grating Waveguide for Multiple-Sheet Electron Beam Devices. *Shu, G.*, +, *TED June 2021 3021-3027*

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- Fabrication of Binder-Free TiO<sub>2</sub> Nanofiber Electrodes via Electrophoretic Deposition for Low-Power Electronic Applications. *Rani, S.*, +, *TED Jan. 2021 251-256*

- Flexible High-Temperature Polycrystalline Silicon Thin Film Transistor on Metal Foil With S/D Doped by Diffusion. *Yu, B.*, +, *TED Aug. 2021 3857-3862*

- Low-Temperature Processing of Electronic Materials Using Uniform Microwave Fields. *Hubbard, R.L.*, *TED July 2021 3170-3175*

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- Characteristics of Stacked Gate-All-Around Si Nanosheet MOSFETs With Metal Sidewall Source/Drain and Their Impacts on CMOS Circuit Properties. *Sung, W.*, +, *TED June 2021 3124-3128*

**Diodes**

- A Noniterative Parameter-Extraction Method for Single-Diode Lumped Parameter Model of Solar Cells. *Xu, C.*, +, *TED Sept. 2021 4529-4535*
- Simulation of Space-Charge-Limited Current for Hot Electrons With Initial Velocity in a Vacuum Diode. *Huang, J.B.*, +, *TED July 2021 3604-3610*

**Direct energy conversion**

- Thermoradiative Cell Equivalent Circuit Model. *Phillips, J.D.*, *TED Feb. 2021 928-930*

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- Characteristics of Pseudospark Discharge in Particle-in-Cell Simulations. *Zhang, L.*, +, *TED June 2021 3003-3009*
- Design of Multigap Pseudospark Discharge-Based Plasma Cathode Electron Source at Different Configurations of Electrode Apertures. *Varun, .*, +, *TED Nov. 2021 5799-5806*

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- A Multiscale Simulation Framework for Steep-Slope Si Nanowire Cold Source FET. *Gan, W.*, +, *TED Nov. 2021 5455-5461*
- Advanced DFT-NEGF Transport Techniques for Novel 2-D Material and Device Exploration Including HfS<sub>2</sub>/WSe<sub>2</sub> van der Waals Heterojunction TFET and WTe<sub>2</sub>/WS<sub>2</sub> Metal/Semiconductor Contact. *Afzaljan, A.*, +, *TED Nov. 2021 5372-5379*
- First-Principles-Based Quantum Transport Simulations of Interfacial Point Defect Effects on InAs Nanowire Tunnel FETs. *Lee, H.*, +, *TED Nov. 2021 5901-5907*
- Performance Investigation of p-FETs Based on Highly Air-Stable Monolayer Pentagonal PdSe<sub>2</sub>. *Nandan, K.*, +, *TED Dec. 2021 6551-6557*

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- A Wearable Ultrathin Flexible Sensor Inserted Into Nasal Cavity for Precise Sleep Respiratory Monitoring. *Zhang, H.*, +, *TED Aug. 2021 4090-4097*
- Ultrathin Flexible Inorganic Device for Long-Term Monitoring of Light and Temperature. *Wang, Z.*, +, *TED July 2021 3558-3561*

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- Sub-mA/cm<sup>2</sup> Dark Current Density, Buffer-Less Germanium (Ge) Photodiodes on a 200-mm Ge-on-Insulator Substrate. *Lin, Y.*, +, *TED April 2021 1730-1737*

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- An Extended Interaction Oscillator Capable of Continuous Multimode Operation. *Chang, Z.*, +, *TED Dec. 2021 6470-6475*
- Design and Analysis of Width-Modulated Two-Section Sine Waveguide for G-Band Traveling-Wave Tube. *Nayek, N.*, +, *TED Dec. 2021 6458-6464*
- Dispersion and Dielectric Attenuation Properties of a Wideband Double-Staggered Grating Waveguide for Subterahertz Sheet-Beam Traveling-Wave Amplifiers. *Shu, G.*, +, *TED Nov. 2021 5826-5833*
- Many-Particle Models and Short-Pulse Amplification in Traveling Wave Tubes. *Aliane, K.*, +, *TED Dec. 2021 6476-6481*
- Novel Rectangular-Ring Vertex Double-Bar Slow Wave Structure for High-Power High-Efficiency Traveling-Wave Tubes. *Wei, W.*, +, *TED Dec. 2021 6512-6517*

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- Clarifying Analytically Calculated Dispersion Relations of Finite-Length Overmoded Corrugated Cylindrical Azimuthally Symmetric Slow Wave Structures Using Numerical Simulations. *Bi, L.*, +, *TED June 2021 2990-2995*

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- High Performance Dual Gate Blue Laser Annealed Poly-Si Thin-Film Transistor for High-Resolution Displays. *Jeong, D.Y.*, +, *TED Aug. 2021 3863-3869*

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PbSnS<sub>2</sub>-Based Gas Sensor to Detect SF<sub>6</sub> Decompositions: DFT and NEGFCalculations. *Guo, H.*, +, *TED Oct. 2021 5322-5325*

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Formation of Graphene-Silicon Junction by Room Temperature Reduction With Simultaneous Defects Removal. *Yi, H.*, +, *TED Feb. 2021 873-878*

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A Godunov-Type Stabilization Scheme for Large-Signal Simulations of a THz Nanowire Transistor Based on the Boltzmann Equation. *Noei, M.*, +, *TED Nov. 2021 5407-5413*

Accurate and Efficient Algorithm for Computing Structure Functions From the Spatial Distribution of Thermal Properties in Electronic Devices. *Codecasa, L.*, +, *TED Nov. 2021 5386-5393*

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Dielectric-Modulated Bulk-Planar Junctionless Field-Effect Transistor for Biosensing Applications. *Singh, D.*, +, *TED July 2021 3545-3551*

Electrospun Mn<sub>2</sub>O<sub>3</sub> Nanofiber Networks as Bio-Transducers: Electrical Characterization, Modeling, and DNA Sensing. *Tripathy, S.*, +, *TED April 2021 1892-1898*

Flash-DNA: Identifying NAND Flash Memory Origins Using Intrinsic Array Properties. *Sakib, S.*, +, *TED Aug. 2021 3794-3800*

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A Bulk Full-Gate SOI-LDMOS Device With Bulk Channel and Electron Accumulation Effect. *Chen, W.*, +, *TED Dec. 2021 6286-6291*

A Multiscale Simulation Framework for Steep-Slope Si Nanowire Cold Source FET. *Gan, W.*, +, *TED Nov. 2021 5455-5461*

Design and Fabrication of 1.92 kV 4H-SiC Super-Junction SBD With Wide-Trench Termination. *Wang, B.*, +, *TED Nov. 2021 5674-5681*

InSnZnO Thin-Film Transistors With Nitrogenous Self-Assembled Multilayers Passivation. *Chen, Y.*, +, *TED Nov. 2021 5612-5617*

Normally-OFF Diamond Reverse Blocking MESFET. *Canas, J.*, +, *TED Dec. 2021 6279-6285*

Systematic Design and Parametric Analysis of GaN Vertical Trench MOS Barrier Schottky Diode With p-GaN Shielding Rings. *Chen, S.*, +, *TED Nov. 2021 5707-5713*

The Characterization of Dye-Sensitized Solar Cell Modified by Reduced Graphene Oxide- and ZrO<sub>2</sub>-Doped TiO<sub>2</sub> Nanofibers at Low Light Intensities. *Nien, Y.*, +, *TED March 2021 1155-1161*

The Influence of Fe Doping Tail in Unintentionally Doped GaN Layer on DC and RF Performance of AlGaIn/GaN HEMTs. *Jia, F.*, +, *TED Dec. 2021 6069-6075*

Tunability of Ferroelectric Hafnium Zirconium Oxide for Varactor Applications. *Abdulazhanov, S.*, +, *TED Oct. 2021 5269-5276*

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3-D TCAD Methodology for Simulating Double-Hysteresis Filamentary *I-V* Behavior and Holding Current in ESD Protection SCRs. *Karaca, H.*, +, *TED Sept. 2021 4214-4222*

A Lateral Power p-Channel Trench MOSFET Improved by Variation Vertical Doping. *Cheng, J.*, +, *TED April 2021 2138-2141*

An Interface-Induced Dielectric Properties Degradation in Heterogeneous Stacked Device With P(VDF-TrFE)-Based Ferroelectric Polymers. *Chen, Y.*, +, *TED Feb. 2021 739-745*

Analytical Design and Experimental Verification of Lateral Superjunction Based on Global Region Normalization Method. *Zhang, W.*, +, *TED May 2021 2372-2377*

Capacitance-Voltage Technique Based on Time Varying Magnetic Field for VDMOSFET—Part II: Measurements and Parameter Extractions. *Tahi, H.*, +, *TED May 2021 2181-2188*

Creation of Step-Shaped Energy Band in a Novel Double-Gate GNR FET to Diminish Ambipolar Conduction. *K. Anvarifard, M.*, +, *TED May 2021 2549-2555*

Dark-Current-Blocking Mechanism in BIB Far-Infrared Detectors by Interfacial Barriers. *Pan, C.*, +, *TED June 2021 2804-2809*

Doping Profile Engineered Triple Heterojunction TFETs With 12-nm Body Thickness. *Chen, C.*, +, *TED June 2021 3104-3111*

Electrothermal Analysis of the Charge-Discharge Related Energy Loss of the Output Capacitance in OFF-State Superjunction MOSFETs. *Lin, Z.*, +, *TED Sept. 2021 4582-4586*

FDTD-Based Optimization of Geometrical Parameters and Material Properties for GaAs-Truncated Nanopyramid Solar Cells. *Prashant, D.V.*, +, *TED March 2021 1135-1141*

Investigation on Single Pulse Avalanche Failure of 1200-V SiC MOSFETs via Optimized Thermoelectric Simulation. *Bai, Z.*, +, *TED March 2021 1168-1175*

Low-Voltage Thyristor Heterostructure for High-Current Pulse Generation at High Repetition Rate. *Slipchenko, S.O.*, +, *TED June 2021 2855-2860*

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Variability Analysis in a 3-D Multigranular Ferroelectric Capacitor. *Pandey, N.*, +, *TED Aug. 2021 3780-3786*

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S-Curve Engineering for ON-State Performance Using Anti-Ferroelectric/Ferroelectric Stack Negative-Capacitance FinFET. *Huang, S.*, +, *TED Sept. 2021 4787-4792*

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**Ferroelectric materials**

A Dynamic Current Model for MFIS Negative Capacitance Transistors. *Huang, X.*, +, *TED July 2021 3665-3671*

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An Interface-Induced Dielectric Properties Degradation in Heterogeneous Stacked Device With P(VDF-TrFE)-Based Ferroelectric Polymers. *Chen, Y.*, +, *TED Feb. 2021 739-745*

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Influence of High-Pressure Annealing Conditions on Ferroelectric and Interfacial Properties of Zr-Rich Hf<sub>x</sub>Zr<sub>1-x</sub>O<sub>2</sub> Capacitors. *Das, D.*, +, *TED April 2021 1996-2002*

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Optically Controlled Ferroelectric Nanodomains for Logic-in-Memory Photonic Devices With Simplified Structures. *Xue, F.*, +, *TED April 2021 1992-1995*

Performance Improvement by Modifying Deposition Temperature in HfZrO<sub>x</sub> Ferroelectric Memory. *Chen, W.*, +, *TED Aug. 2021 3838-3842*

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Ferroelectric Field Effect Transistors as a Synapse for Neuromorphic Application. *Lederer, M.*, +, *TED May 2021 2295-2300*

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Impact of the Nonlinear Dielectric Hysteresis Properties of a Charge Trap Layer in a Novel Hybrid High-Speed and Low-Power Ferroelectric or Antiferroelectric HSO/HZO Boosted Charge Trap Memory. *Ali, T.*, +, *TED April 2021 2098-2106*

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The Critical Role of Charge Balance on the Memory Characteristics of Ferroelectric Field-Effect Transistors. *Si, M.*, +, *TED Oct. 2021 5108-5113*

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**Ferroelectric thin films**

Effect of Insertion of Dielectric Layer on the Performance of Hafnia Ferroelectric Devices. *Hwang, J.*, +, *TED Feb. 2021 841-845*

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- Stress Engineering as a Strategy to Achieve High Ferroelectricity in Thick Hafnia Using Interlayer. *Joh, H.*, +, *TED May 2021 2538-2542*
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- Temporal Electron-Spin Splitter Based on a Semiconductor Microstructure Constructed on Surface of  $\text{InAs}/\text{Al}_x\text{In}_{1-x}$  As Heterostructure by Patterning a Ferromagnetic Stripe and a Schottky-Metal Stripe. *Lu, M.*, +, *TED Feb. 2021 860-864*
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- Empirical Large-Signal Modeling of mm-Wave FDSOI CMOS Based on Angelov Model. *Le, Q.H.*, +, *TED April 2021 1446-1453*
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- Experimental Demonstration of Gate-Level Logic Camouflaging and Runtime Reconfigurability Using Ferroelectric FET for Hardware Security. *Dutta, S.*, +, *TED Feb. 2021 516-522*
- High-Performance  $\text{In}_2\text{O}_3$ -Based 1T1R FET for BEOL Memory Application. *Lin, Z.*, +, *TED Aug. 2021 3775-3779*
- Impact of Trapped-Charge Variations on Scaled Ferroelectric FET Nonvolatile Memories. *Liu, Y.*, +, *TED April 2021 1639-1643*
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- Field effect transistor switches**
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- Efficient 1-V Boost Converter Using Sub-50-mV NEMS Without Body Bias. *Saha, S.*, +, *TED June 2021 2944-2950*
- Electrothermal Analysis of the Charge-Discharge Related Energy Loss of the Output Capacitance in OFF-State Superjunction MOSFETs. *Lin, Z.*, +, *TED Sept. 2021 4582-4586*
- Reliability of p-GaN Gate HEMTs in Reverse Conduction. *Cingu, D.*, +, *TED Feb. 2021 645-652*
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- 2-D Quantum Confined Threshold Voltage Shift Model for Asymmetric Short-Channel Junctionless Quadruple-Gate FETs. *Bae, M.S.*, +, *TED Nov. 2021 5504-5510*
- A Compact Current- and Voltage-Mode Model of Antenna-Coupled FET Terahertz Detectors. *Perenzoni, M.*, +, *TED Feb. 2021 471-478*
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- A Novel Device to Implement Full Set of Three-Input Logic Gates Using a Naphthalene-Based Single-Molecule Field-Effect Transistor. *Fakheri, M.T.*, +, *TED Feb. 2021 733-738*
- A Physical Model of Contact Resistance in Ti-Contacted Graphene-Based Field Effect Transistors. *Wang, B.*, +, *TED Feb. 2021 892-898*
- A Review of Low Temperature Process Modules Leading Up to the First ( $\leq 500$  °C) Planar FDSOI CMOS Devices for 3-D Sequential Integration. *Fenouillet-Beranger, C.*, +, *TED July 2021 3142-3148*
- A SPICE Compact Model for Ambipolar 2-D-Material FETs Aiming at Circuit Design. *Ahsan, S.A.*, +, *TED June 2021 3096-3103*
- A Surface Potential Model for Field-Effect Transistors With Bound-Charge Engineering. *Prentki, R.J.*, *TED Sept. 2021 4625-4629*
- Amorphous  $\text{ZnSn}_x\text{O}_y$  Fabricated at Room-Temperature for Flexible pH-EG-FET Sensor. *Singh, K.*, +, *TED Feb. 2021 793-797*
- An Analytical Method for Parameter Extraction in Oxide Semiconductor Field-Effect Transistors. *Chien, Y.*, +, *TED June 2021 2717-2722*
- An Analytical Model of Hot Carrier Degradation in LDMOS Transistors: Rediscovery of Universal Scaling. *Mahajan, B.K.*, +, *TED Aug. 2021 3923-3929*
- An Efficient GFET Structure. *Nastasi, G.*, +, *TED Sept. 2021 4729-4734*
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- Compact Modeling of Multidomain Ferroelectric FETs: Charge Trapping, Channel Percolation, and Nucleation-Growth Domain Dynamics. *Xiang, Y.*, +, *TED April 2021 2107-2115*
- Compact Modeling of pH-Sensitive FETs Based on 2-D Semiconductors. *Grou, T.E.*, +, *TED Nov. 2021 5916-5919*
- Creation of Step-Shaped Energy Band in a Novel Double-Gate GNR-FET to Diminish Ambipolar Conduction. *K. Anvarifard, M.*, +, *TED May 2021 2549-2555*
- Design of a Low-Power Short-Channel Electrostatically Doped Silicene Nanoribbon FET. *Gooran-Shoorakchaly, A.*, +, *TED April 2021 1956-1961*
- Drain-Bias-Dependent Study of Reverse Gate-Leakage Current in AlGaIn/GaN HFETs. *Singh, I.P.*, +, *TED Feb. 2021 503-509*
- Effect of Gaussian Disorder on Power-Law Contact Resistance and Mobility in Organic Field-Effect Transistors. *Jung, S.*, +, *TED Jan. 2021 307-310*
- Effect of the Si Doping Content in  $\text{HfO}_2$  Film on the Key Performance Metrics of Ferroelectric FETs. *Mulaosmanovic, H.*, +, *TED Sept. 2021 4773-4779*
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- Electrical Characteristics of Vertical GaN Nanowire Vacuum Field Emitter Devices. *Doundoulakis, G.*, +, *TED June 2021 3034-3039*
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- Enhanced High-Frequency Performance of Top-Gated Graphene FETs Due to Substrate-Induced Improvements in Charge Carrier Saturation Velocity. *Asad, M.*, +, *TED Feb. 2021 899-902*
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- Epitaxial Al-InAs Heterostructures as Platform for Josephson Junction Field-Effect Transistor Logic Devices. *Wen, F.*, +, *TED April 2021 1524-1529*
- Exploiting Carbon Nanotube FET and Magnetic Tunneling Junction for Near-Memory-Computing Paradigm. *Yang, N.*, +, *TED April 2021 1975-1979*
- Fabrication of Glutathione-S-Transferase-ZnO Nanoconjugate Ensemble FET Device for Detection of Glutathione. *Barman, U.*, +, *TED March 2021 1242-1249*
- Ferroelectric Field Effect Transistors as a Synapse for Neuromorphic Application. *Lederer, M.*, +, *TED May 2021 2295-2300*

- Finger Gate Vacuum Channel Field Emission Transistors: Performance and Sensitivity Analysis. *Khoshbijari, F.K.*, +, *TED Oct. 2021 5250-5256*
- Flexible Dual-Gate MoS<sub>2</sub> Neuromorphic Transistors on Freestanding Proton-Conducting Chitosan Membranes. *Chen, C.*, +, *TED June 2021 3119-3123*
- Gate-First Negative Capacitance Field-Effect Transistor With Self-Aligned Nickel-Silicide Source and Drain. *Kim, S.*, +, *TED Sept. 2021 4754-4757*
- Hybrid Design Using Metal-Oxide-Semiconductor Field-Effect Transistors and Negative-Capacitance Field-Effect Transistors for Analog Circuit Applications. *Han, K.*, +, *TED Feb. 2021 846-852*
- Impact of Random Phase Distribution in Ferroelectric Transistors-Based 3-D NAND Architecture on In-Memory Computing. *Choe, G.*, +, *TED May 2021 2543-2548*
- Improved Mobility Extraction Methodology for Reconfigurable Transistors Considering Resistive Components and Effective Drain Bias. *Mane, S.*, +, *TED Sept. 2021 4797-4800*
- Improved Retention Characteristics of Z<sup>2</sup>-FET Employing Half Back-Gate Control. *Kwon, S.*, +, *TED March 2021 1041-1044*
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- Influence of Si-Substrate Concentration on Electrical Properties of Back-and-Top-Gate MoS<sub>2</sub> Transistors. *Zhao, X.*, +, *TED June 2021 3087-3090*
- Input-Referred Low-Frequency Noise Analysis for Single-Layer Graphene FETs. *Mavredakis, N.*, +, *TED Sept. 2021 4762-4765*
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- Mobility Degradation and Series Resistance in Graphene Field-Effect Transistors. *Jeppson, K.*, +, *TED June 2021 3091-3095*
- Modeling and Analysis of High-Q Resonant-Fin Transistors. *Hager, E.*, +, *TED Sept. 2021 4780-4786*
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- Monolithic Integration of Oxide Semiconductor FET and Ferroelectric Capacitor Enabled by Sn-Doped InGaZnO for 3-D Embedded RAM Application. *Wu, J.*, +, *TED Dec. 2021 6617-6622*
- Multiobjective Design of 2-D-Material-Based Field-Effect Transistors With Machine Learning Methods. *Wu, T.*, +, *TED Nov. 2021 5476-5482*
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- On the Operation Modes of Dual-Gate Reconfigurable Nanowire Transistors. *Sun, B.*, +, *TED July 2021 3684-3689*
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- Reconfigurable MoTe<sub>2</sub> Field-Effect Transistors and its Application in Compact CMOS Circuits. *Chen, J.*, +, *TED Sept. 2021 4748-4753*
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- Response Comparison of Resistor- and Si FET-Type Gas Sensors on the Same Substrate. *Jung, G.*, +, *TED July 2021 3552-3557*
- Self-Consistent Modeling of B or N Substitution Doped Bottom Gated Graphene FET With Nonzero Bandgap. *Chandrasekar, L.*, +, *TED July 2021 3658-3664*
- Steep-Slope Transistors Based on Chiral Graphene Nanoribbons With Intrinsic Cold Source. *Ye, S.*, +, *TED Aug. 2021 4123-4128*
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- Temperature-Dependent Current Dispersion Study in  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> FETs Using Submicrosecond Pulsed I-V Characteristics. *Vaidya, A.*, +, *TED Aug. 2021 3755-3761*
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- Unified Mechanism for Graphene FET's Electrothermal Breakdown and Its Implications on Safe Operating Limits. *Mishra, A.*, +, *TED May 2021 2530-2537*
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- A Highly Sensitive and Robust GaN Ultraviolet Photodetector Fabricated on 150-mm Si (111) Wafer. *Pokharia, R.S.*, +, *TED June 2021 2796-2803*
- Complementary Vacuum Field Emission Transistor. *Bhattacharya, R.*, +, *TED Oct. 2021 5244-5249*
- Dynamics of a Field Emitted Beam From a Microscopic Inhomogeneous Cathode. *Torfason, K.*, +, *TED May 2021 2461-2466*
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- Field emission electron microscopy**
- Improving Photovoltaic Performance of Dye-Sensitized Solar Cell by Modification of Photoanode With g-C<sub>3</sub>N<sub>4</sub>/TiO<sub>2</sub> Nanofibers. *Nien, Y.*, +, *TED Oct. 2021 4982-4988*
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- Hydrothermal Synthesis and Improved CH<sub>3</sub>OH-Sensing Performance of ZnO Nanorods With Adsorbed Au NPs. *Young, S.*, +, *TED April 2021 1886-1891*
- On the Channel Hot-Electron's Interaction With C-Doped GaN Buffer and Resultant Gate Degradation in AlGaIn/GaN HEMTs. *Chaudhuri, R.R.*, +, *TED Oct. 2021 4869-4876*
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### H

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- Low-Frequency Noise Analysis of the Optimized Post High-k Deposition Annealing in FinFET Technology. *Deng, W.*, +, *TED March 2021 1202-1206*
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- Using Anisotropic Insulators to Engineer the Electrostatics of Conventional and Tunnel Field-Effect Transistors. *Bennett, R.K.A.*, +, *TED Feb. 2021 865-872*
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- Improved Tradeoff Between Subthreshold Swing and Hysteresis for  $\text{MoS}_2$  Negative-Capacitance FETs by Optimizing Gate-Stack of  $\text{Hf}_{1-x}\text{Zr}_x\text{O}_2/\text{Al}_2\text{O}_3$ . *Wang, J.*, +, *TED Dec. 2021 6546-6550*
- Indium-Gallium-Zinc-Oxide (IGZO) Nanowire Transistors. *Han, K.*, +, *TED Dec. 2021 6610-6616*
- Low Thermal Budget Fabrication and Performance Comparison of MFM Capacitors With Thermal and Plasma-Enhanced Atomic Layer Deposited  $\text{Hf}_{0.45}\text{Zr}_{0.55}\text{O}_x$  Ferroelectrics. *Xiao, D.*, +, *TED Dec. 2021 6359-6364*
- Simulation-Based Study of High-Permittivity Inserted-Oxide FinFET With Low-Permittivity Inner Spacers. *Wu, Y.*, +, *TED Nov. 2021 5529-5534*
- Tunability Properties and Compact Modeling of  $\text{HfO}_2$ -Based Complementary Resistive Switches Using a Three-Terminal Subcircuit. *Saludes-Tapia, M.*, +, *TED Dec. 2021 5981-5988*
- Hall effect**
- $\text{AlGaN}/\text{GaN}$  2-D Electron Gas for Highly Sensitive and High-Temperature Current Sensing. *Nguyen, H.Q.*, +, *TED April 2021 1495-1500*
- Interface Charge Effects on 2-D Electron Gas in Vertical-Scaled Ultrathin-Barrier  $\text{AlGaN}/\text{GaN}$  Heterostructure. *Huang, S.*, +, *TED Jan. 2021 36-41*
- Low Subthreshold Swing and High Performance of Ultrathin PEALD  $\text{InGaZnO}$  Thin-Film Transistors. *Jeong, S.*, +, *TED April 2021 1670-1675*
- Hall effect devices**
- Graphene Quantum Hall Effect Devices for AC and DC Electrical Metrology. *Kruskopf, M.*, +, *TED July 2021 3672-3677*
- Hall mobility**
- Sub-30-nm  $\text{In}_{0.8}\text{Ga}_{0.2}\text{As}$  Composite-Channel High-Electron-Mobility Transistors With Record High-Frequency Characteristics. *Jo, H.*, +, *TED April 2021 2010-2016*
- Handwritten character recognition**
- Energy-Efficient All-Spin BNN Using Voltage-Controlled Spin-Orbit Torque Device for Digit Recognition. *Shreya, S.*, +, *TED Jan. 2021 385-392*
- Model of the Weak Reset Process in  $\text{HfO}_x$  Resistive Memory for Deep Learning Frameworks. *Majumdar, A.*, +, *TED Oct. 2021 4925-4932*
- Hardware**
- A Drift-Resilient Hardware Implementation of Neural Accelerators Based on Phase Change Memory Devices. *Munoz-Martin, I.*, +, *TED Dec. 2021 6076-6081*
- Hardware description languages**
- Performance Projection of 2-D Material-Based CMOS Inverters for Sub-10-nm Channel Length. *Rawat, A.*, +, *TED July 2021 3622-3629*
- Hardware-software codesign**
- Compact Reliability Model of Analog RRAM for Computation-in-Memory Device-to-System Codesign and Benchmark. *Liu, Y.*, +, *TED June 2021 2686-2692*
- Harmonic analysis**
- Angular Harmonic Hall Voltage and Magnetoresistance Measurements of  $\text{Pt}/\text{FeCoB}$  and  $\text{Pt-Ti}/\text{FeCoB}$  Bilayers for Spin Hall Conductivity Determination. *Skowronski, W.*, +, *TED Dec. 2021 6379-6385*
- Design of a 48 GHz Gyrokystron Amplifier. *Nix, L.J.R.*, +, *TED Nov. 2021 5792-5798*
- Efficiency Enhancement of a High Power Radial-Line Relativistic Klystron Amplifier Driven by Disk Intense Electron Beam. *Dang, F.*, +, *TED Nov. 2021 5834-5840*
- Efficient TCAD Thermal Analysis of Semiconductor Devices. *Catoggio, E.*, +, *TED Nov. 2021 5462-5468*
- Harmonic Analysis of the Nonlinear Response of Graphene Oxide-Based Memristors. *Vercik, A.*, *TED Oct. 2021 4938-4943*
- Harmonic distortion**
- Harmonic Analysis of the Nonlinear Response of Graphene Oxide-Based Memristors. *Vercik, A.*, *TED Oct. 2021 4938-4943*
- Modeling of Semiconductor Substrates for RF Applications: Part I—Static and Dynamic Physics of Carriers and Traps. *Rack, M.*, +, *TED Sept. 2021 4598-4605*
- Modeling of Semiconductor Substrates for RF Applications: Part II—Parameter Impact on Harmonic Distortion. *Rack, M.*, +, *TED Sept. 2021 4606-4613*
- Heat conduction**
- 2-D-Nonlinear Electrothermal Model for Investigating the Self-Heating Effect in GAAFET Transistors. *Belkhiria, M.*, +, *TED March 2021 954-961*
- Nonlinear Thermal Analysis of  $\text{AlGaN}/\text{GaN}$  HEMTs With Temperature-Dependent Parameters. *Tang, M.*, +, *TED Sept. 2021 4565-4570*
- Heat transfer**
- 100- $\mu\text{m}$ -Scale High-Detectivity Infrared Detector With Thermopile/Absorber Double-Deck Structure Formed in (111) Silicon. *Xue, D.*, +, *TED Dec. 2021 6233-6239*

- 3-D Modeling and Experimental Studies for a Thermionic Dispenser Cathode Activation Process. *Atmaca, N.Y.A.*, +, *TED May 2021 2455-2460*
- Modeling Peak Temperature in SOL-FinFET-Like Structures Considering 2-D Heat Flow. *Nidhin, K.*, +, *TED March 2021 981-986*
- Heat treatment**
- Data Sanitization of SRAM by Thermal Distortion. *Han, J.*, +, *TED July 2021 3706-3710*
- Heating**
- Electric Field and Self-Heating Effects on the Emission Time of Iron Traps in GaN HEMTs. *Cioni, M.*, +, *TED July 2021 3325-3332*
- Electric-Field-Dependence Mechanism for Cosmic Ray Failure in Power Semiconductor Devices. *Oda, T.*, +, *TED July 2021 3505-3512*
- Heating systems**
- 100- $\mu\text{m}$ -Scale High-Detectivity Infrared Detector With Thermopile/Absorber Double-Deck Structure Formed in (111) Silicon. *Xue, D.*, +, *TED Dec. 2021 6233-6239*
- Accurate and Efficient Algorithm for Computing Structure Functions From the Spatial Distribution of Thermal Properties in Electronic Devices. *Codecasa, L.*, +, *TED Nov. 2021 5386-5393*
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- Electrothermal Model for Power LEDs Based on the Equivalent Resistance Concept for LED Driver Design. *Adamas-Perez, H.*, +, *TED Dec. 2021 6249-6254*
- High-Performance III-Nitride Light-Emitting Diode Stripes. *Jin, H.*, +, *TED Nov. 2021 5629-5633*
- Investigation and Modeling of the Avalanche Failure Mechanism of 1.2-kV 4H-SiC J MOS. *Zhang, Y.*, +, *TED Dec. 2021 6313-6320*
- Thermal Coupling Among Channels and Its DC Modeling in Sub-7-nm Vertically Stacked Nanosheet Gate-All-Around Transistor. *Liu, R.*, +, *TED Dec. 2021 6563-6570*
- Thermoelectric Effects on Amorphization Process of Blade-Type Phase Change Random Access Memory. *Lian, X.*, +, *TED Dec. 2021 6139-6146*
- Helical waveguides**
- CW Multifrequency K-Band Source Based on a Helical-Waveguide Gyro-TWT With Delayed Feedback. *Rozental, R.M.*, +, *TED Jan. 2021 330-335*
- HEMT integrated circuits**
- Monolithic Comparator and Sawtooth Generator of AlGaIn/GaN MIS-HEMTs With Threshold Voltage Modulation for High-Temperature Applications. *Li, A.*, +, *TED June 2021 2673-2679*
- HEMTs**
- A High RF-Performance AlGaIn/GaN HEMT With Ultrathin Barrier and Stressor *In Situ* SiN. *Wu, S.*, +, *TED Nov. 2021 5553-5558*
- Analytical Modeling of Sheet Carrier Density and on-Resistance in Polarization Super-Junction HFETs. *Yan, H.*, +, *TED Nov. 2021 5714-5719*
- Bias Dependence Model of Peak Frequency of GaN Trap in GaN HEMTs Using Low-Frequency  $Y_{22}$  Parameters. *Oishi, T.*, +, *TED Nov. 2021 5565-5571*
- Enhancing the Sensitivity of GaN High Electron-Mobility Transistors-Based pH Sensor by Dual Function of Monolithic Integrated Planar Multi-Channel and Ultraviolet Light. *Yang, X.*, +, *TED Dec. 2021 6437-6443*
- High-Temperature Sensitivity of a Depletion-Mode AlGaIn/GaN MIS-HEMT. *Mutsafi, Z.*, +, *TED Nov. 2021 5695-5700*
- High-Temperature Time-Dependent Gate Breakdown of p-GaN HEMTs. *Millesimo, M.*, +, *TED Nov. 2021 5701-5706*
- Identifying the Properties of Traps in GaN High-Electron-Mobility Transistors via Amplitude Analysis Based on the Voltage-Transient Method. *Pan, S.*, +, *TED Nov. 2021 5541-5546*
- Lateral AlGaIn/GaN Schottky Barrier Diode With Arrayed p-GaN Islands Termination. *Wang, H.*, +, *TED Dec. 2021 6046-6051*
- Novel Surface Passivation Scheme by Using p-Type AlTiO to Mitigate Dynamic ON Resistance Behavior in AlGaIn/GaN HEMTs—Part II. *Gupta, S.D.*, +, *TED Nov. 2021 5728-5735*
- Part I: Physical Insights Into Dynamic  $R_{ON}$  Behavior and a Unique Time-Dependent Critical Stress Voltage in AlGaIn/GaN HEMTs. *Gupta, S.D.*, +, *TED Nov. 2021 5720-5727*
- Polarization-Engineered Quaternary Barrier InAlGaIn/AlGaIn Heterostructure Field-Effect Transistors Toward Robust High-Frequency Power Performance in AlGaIn Channel Electronics. *Li, L.*, +, *TED Nov. 2021 5535-5540*
- Simulation Study of a p-GaN HEMT With an Integrated Schottky Barrier Diode. *Yi, B.*, +, *TED Dec. 2021 6039-6045*
- Small-Signal Analysis of Channel Resistance  $R_{T1}$  at Low Gate Bias Voltages in AlGaIn/GaN HEMTs. *Kaushik, P.K.*, +, *TED Dec. 2021 6033-6038*
- Surface State Spectrum of AlGaIn/AlN/GaN Extracted From Static Equilibrium Electrostatics. *Yu, H.*, +, *TED Nov. 2021 5559-5564*
- Technology of GaN-Based Large Area CAVETs With Co-Integrated HEMTs. *Doring, P.*, +, *TED Nov. 2021 5547-5552*
- The Influence of Fe Doping Tail in Unintentionally Doped GaN Layer on DC and RF Performance of AlGaIn/GaN HEMTs. *Jia, F.*, +, *TED Dec. 2021 6069-6075*
- Heterojunction bipolar transistors**
- 1-D Drift-Diffusion Simulation of Two-Valley Semiconductors and Devices. *Muller, M.*, +, *TED March 2021 1221-1227*
- CMOS-Compatible Ti/TiN/Al Refractory Ohmic Contact for GaAs Heterojunction Bipolar Transistors Grown on Ge/Si Substrate. *Wang, Y.*, +, *TED Dec. 2021 6065-6068*
- Extraction of Compact Static Thermal Model Parameters for SiGe HBTs. *Huszka, Z.*, +, *TED Feb. 2021 491-496*
- Extraction of True Finger Temperature From Measured Data in Multifinger Bipolar Transistors. *Gupta, A.*, +, *TED March 2021 1385-1388*
- Improved Compact Modeling of SiGe HBT Linearity With MEXTRAM. *Zhang, H.*, +, *TED June 2021 2597-2603*
- Improvement of the Self-Heating Performance of an Advanced SiGe HBT Transistor Through the Peltier Effect. *Boulgheb, A.*, +, *TED Feb. 2021 479-484*
- Operation of Current Mirrors in SiGe BiCMOS Technology at Cryogenic Temperatures. *Ying, H.*, +, *TED April 2021 1439-1445*
- Variability of p-n Junctions and SiGe HBTs at Cryogenic Temperatures. *Ying, H.*, +, *TED March 2021 987-993*
- Heterojunctions**
- Advanced DFT-NEGF Transport Techniques for Novel 2-D Material and Device Exploration Including HfS<sub>2</sub>/WSe<sub>2</sub> van der Waals Heterojunction TFET and WTe<sub>2</sub>/WS<sub>2</sub> Metal/Semiconductor Contact. *Afzalian, A.*, +, *TED Nov. 2021 5372-5379*
- Bifacial Heterojunction Back Contact Solar Cell: 29-mW/cm<sup>2</sup> Output Power Density in Standard Albedo Condition. *Sugiura, T.*, +, *TED Nov. 2021 5645-5651*
- Study of In<sub>x</sub>Ga<sub>1-x</sub>N/GaN Homotype Heterojunction IMPATT Diodes. *Dai, Y.*, +, *TED Nov. 2021 5469-5475*
- Yb/MoO<sub>3</sub>/In<sub>2</sub>Se<sub>3</sub>/Ag Sensors Designed as Tunneling Diodes, MOSFETs, Microwave Resonators, Laser Sensors, and VLC Receivers Suitable for 4G/5G and VLC Technologies. *Qasrawi, A.F.*, +, *TED Dec. 2021 6444-6450*
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- 75 nm Gate Length PHEMT With  $f_{\text{max}} = 800$  GHz Using Asymmetric Gate Recess: RF and Noise Investigation. *Samnouni, M.*, +, *TED Sept. 2021 4289-4295*
- A Machine Learning-Assisted Model for GaN Ohmic Contacts Regarding the Fabrication Processes. *Wang, Z.*, +, *TED May 2021 2212-2219*
- A Novel Approach for the Modeling of the Dynamic ON-State Resistance of GaN-HEMTs. *Weiser, M.C.J.*, +, *TED Sept. 2021 4302-4309*
- A Study of the Gate-Stack Small-Signal Model and Determination of Interface Traps in GaN-Based MIS-HEMTs. *Huang, Z.*, +, *TED April 2021 1507-1512*
- AlGaIn/GaN Enhancement-Mode MOSHEMTs Utilizing Hybrid Gate-Recessed Structure and Ferroelectric Charge Trapping/Storage Stacked LiNbO<sub>3</sub>/HfO<sub>2</sub>/Al<sub>2</sub>O<sub>3</sub> Structure. *Lee, H.*, +, *TED Aug. 2021 3768-3774*
- AlGaIn/GaN-Based Laterally Gated High-Electron-Mobility Transistors With Optimized Linearity. *Odabasi, O.*, +, *TED March 2021 1016-1023*
- AlN/GaN Superlattice Channel HEMTs on Silicon Substrate. *Liu, S.*, +, *TED July 2021 3296-3301*
- AlN/GaN/InGaIn Coupling-Channel HEMTs for Improved  $g_m$  and Gain Linearity. *Lu, H.*, +, *TED July 2021 3308-3313*

- Analysis of Dependence of Breakdown Voltage on Gate–Drain Distance in AlGaIn/GaN HEMTs With High- $k$  Passivation Layer. *Tomita, R.*, +, *TED April 2021 1550-1556*
- Analysis of the Effects of High-Energy Electron Irradiation of GaN High-Electron-Mobility Transistors Using the Voltage-Transient Method. *Pan, S.*, +, *TED Aug. 2021 3968-3973*
- Analytical Model for Gate Capacitance and Threshold Voltage in Fin-Shaped GaN HEMTs. *Sruthi, M.P.*, +, *TED Sept. 2021 4793-4796*
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- Degradation Behavior and Trap Analysis Based on Low-Frequency Noise of AlGaIn/GaN HEMTs Subjected to Radio Frequency Overdrive Stress. *Chen, Q.*, +, *TED Jan. 2021 66-71*
- Determination of the Gate Breakdown Mechanisms in p-GaN Gate HEMTs by Multiple-Gate-Sweep Measurements. *Zhou, G.*, +, *TED April 2021 1518-1523*
- Drain Field Plate Impact on the Hard-Switching Performance of AlGaIn/GaN HEMTs. *Minetto, A.*, +, *TED Oct. 2021 5003-5008*
- Effect of Atmosphere on Electrical Characteristics of AlGaIn/GaN HEMTs Under Hot-Electron Stress. *Liu, C.*, +, *TED March 2021 1000-1005*
- Effect of Fixed Charges at Interface Between InP and Bonding Layer on Heterogeneous Integration of InP HEMTs. *Chen, Y.*, +, *TED May 2021 2226-2232*
- Electric Field and Self-Heating Effects on the Emission Time of Iron Traps in GaN HEMTs. *Cioni, M.*, +, *TED July 2021 3325-3332*
- Electrical Degradation of *In Situ* SiN/AlGaIn/GaN MIS-HEMTs Caused by Dehydrogenation and Trap Effect Under Hot Carrier Stress. *Niu, X.*, +, *TED Sept. 2021 4283-4288*
- Epi-Gd<sub>2</sub>O<sub>3</sub>-MOSHEMT: A Potential Solution Toward Leveraging the Application of AlGaIn/GaN/Si HEMT With Improved  $I_{ON}/I_{OFF}$  Operating at 473 K. *Sarkar, R.*, +, *TED June 2021 2653-2660*
- Experimental Results for AlGaIn/GaN HEMTs Improving Breakdown Voltage and Output Current by Electric Field Modulation. *Duan, B.*, +, *TED May 2021 2240-2245*
- Fabrication and Characterization of Flexible AlGaIn/GaN HEMTs on Kapton Tape. *Hsu, K.*, +, *TED July 2021 3320-3324*
- Gate Current Partitioning Model for Schottky Gate GaN HEMTs. *Debnath, A.*, +, *TED Jan. 2021 425-429*
- Gate-Induced Threshold Voltage Instabilities in p-Gate GaN HEMTs. *Oeder, T.*, +, *TED Sept. 2021 4322-4328*
- High Breakdown Voltage and Low-Current Dispersion in AlGaIn/GaN HEMTs With High-Quality AlN Buffer Layer. *Kim, J.*, +, *TED April 2021 1513-1517*
- Hybrid Electrothermal Simulations of GaN HEMT Devices Based on Self-Heating Free Virtual Electrical Characteristics. *Valletta, A.*, +, *TED Aug. 2021 3740-3747*
- Implementation of RTCVD-SiN<sub>x</sub> Gate Dielectric Into Enhancement-Mode GaN MIS-HEMTs Fabricated on Ultrathin-Barrier AlGaIn/GaN-on-Si Platform. *Shi, W.*, +, *TED Sept. 2021 4274-4277*
- Improved RF Power Performance of AlGaIn/GaN HEMT Using by Ti/Au/Al/Ni/Au Shallow Trench Etching Ohmic Contact. *Lu, H.*, +, *TED Oct. 2021 4842-4846*
- InAlN/GaN HEMT on Si With  $f_{max} = 270$  GHz. *Cui, P.*, +, *TED March 2021 994-999*
- Influence of Carbon on pBTI Degradation in GaN-on-Si E-Mode MOS-HEMT. *Viey, A.G.*, +, *TED April 2021 2017-2024*
- Influence of Fin-Like Configuration Parameters on the Linearity of AlGaIn/GaN HEMTs. *Wang, P.*, +, *TED April 2021 1563-1569*
- Interface Charge Effects on 2-D Electron Gas in Vertical-Scaled Ultrathin-Barrier AlGaIn/GaN Heterostructure. *Huang, S.*, +, *TED Jan. 2021 36-41*
- Interplay Between Surface and Buffer Traps in Governing Breakdown Characteristics of AlGaIn/GaN HEMTs—Part II. *Joshi, V.*, +, *TED Jan. 2021 80-87*
- Interplay of Various Charge Sources in AlGaIn/GaN Epi-Stack Governing HEMT Breakdown. *Soni, A.*, +, *TED May 2021 2378-2386*
- Low ON-State Resistance Normally-OFF AlGaIn/GaN MIS-HEMTs With Partially Recessed Gate and ZrO<sub>x</sub> Charge Trapping Layer. *Cai, Y.*, +, *TED Sept. 2021 4310-4316*
- Mechanisms Underlying the Bidirectional  $V_T$  Shift After Negative-Bias Temperature Instability Stress in Carbon-Doped Fully Recessed AlGaIn/GaN MIS-HEMTs. *Zagni, N.*, +, *TED May 2021 2564-2567*
- Millimeter-Wave Donor–Acceptor-Doped DpHEMT. *Pashkovskii, A.B.*, +, *TED Jan. 2021 53-56*
- Model of Electron Population and Energy Band Diagram of Multiple-Channel GaN Heterostructures. *Chen, X.*, +, *TED April 2021 1557-1562*
- Modeling of Bias-Dependent Effective Velocity and Its Impact on Saturation Transconductance in AlGaIn/GaN HEMTs. *Pampori, A.U.H.*, +, *TED July 2021 3302-3307*
- Nonalloyed Ohmic Contacts in AlGaIn/GaN HEMTs With MOCVD Regrowth of InGaIn for *Ka*-Band Applications. *Cakmak, H.*, +, *TED March 2021 1006-1010*
- Nonlinear Thermal Analysis of AlGaIn/GaN HEMTs With Temperature-Dependent Parameters. *Tang, M.*, +, *TED Sept. 2021 4565-4570*
- Numerical Study of Novel GaN HEMTs With Integrated SBDs for Ultrahigh Reverse Conduction Capability. *Li, S.*, +, *TED Feb. 2021 931-933*
- On the Channel Hot-Electron's Interaction With C-Doped GaN Buffer and Resultant Gate Degradation in AlGaIn/GaN HEMTs. *Chaudhuri, R.R.*, +, *TED Oct. 2021 4869-4876*
- Performance and Reliability Optimization of Supercritical-Nitridation-Treated AlGaIn/GaN High-Electron-Mobility Transistors. *Wu, P.*, +, *TED Sept. 2021 4317-4321*
- Performance Optimization of Monolayer 1T/1T'-2H MoX<sub>2</sub> Lateral Heterojunction Transistors. *Yin, D.*, +, *TED July 2021 3649-3657*
- Physical Insights Into the Impact of Surface Traps on Breakdown Characteristics of AlGaIn/GaN HEMTs—Part I. *Joshi, V.*, +, *TED Jan. 2021 72-79*
- Pt-Decorated Graphene Gate AlGaIn/GaN MIS-HEMT for Ultrahigh Sensitive Hydrogen Gas Detection. *Ahn, J.*, +, *TED March 2021 1255-1261*
- Quadruple Gate-Recessed AlGaIn/GaN Fin-Nanochannel Array Metal-Oxide-Semiconductor High-Electron Mobility Transistors. *Lee, H.*, +, *TED Jan. 2021 42-48*
- Simulation Study of an Ultralow Switching Loss p-GaN Gate HEMT With Dynamic Charge Storage Mechanism. *Wang, F.*, +, *TED Jan. 2021 175-183*
- Single-Event Damage-Induced Gate-Leakage Mechanisms in AlGaIn/GaN High-Electron-Mobility Transistors. *Yue, S.*, +, *TED June 2021 2667-2672*
- Stackable InGaAs-on-Insulator HEMTs for Monolithic 3-D Integration. *Jeong, J.*, +, *TED May 2021 2205-2211*
- Sub-30-nm In<sub>0.8</sub>Ga<sub>0.2</sub>As Composite-Channel High-Electron-Mobility Transistors With Record High-Frequency Characteristics. *Jo, H.*, +, *TED April 2021 2010-2016*
- Substrate Bias Enhanced Trap Effects on Time-Dependent Dielectric Breakdown of GaN MIS-HEMTs. *Yang, W.*, +, *TED May 2021 2233-2239*
- Suppression of Gate Leakage Current in *Ka*-Band AlGaIn/GaN HEMT With 5-nm SiN Gate Dielectric Grown by Plasma-Enhanced ALD. *Zhang, S.*, +, *TED Jan. 2021 49-52*
- Temperature-Dependent Dynamic Degradation of Carbon-Doped GaN HEMTs. *Gu, Y.*, +, *TED July 2021 3290-3295*
- Thermal Design Rules of AlGaIn/GaN-Based Microwave Transistors on Diamond. *Gerrer, T.*, +, *TED April 2021 1530-1536*
- Time-Dependent Threshold Voltage Instability Mechanisms of p-GaN Gate AlGaIn/GaN HEMTs Under High Reverse Bias Conditions. *Li, S.*, +, *TED Jan. 2021 443-446*
- Tri-Gate GaN Junction HEMTs: Physics and Performance Space. *Ma, Y.*, +, *TED Oct. 2021 4854-4861*
- Ultrathin Mg<sub>0.05</sub>Sn<sub>0.95</sub>O<sub>x</sub>-Based Thin-Film Transistor by Mist Chemical Vapor Deposition. *Liu, H.*, +, *TED July 2021 3390-3395*
- Understanding High-Energy 75-MeV Sulfur-Ion Irradiation-Induced Degradation in GaN-Based Heterostructures: The Role of the GaN Channel Layer. *Challa, S.R.*, +, *TED Jan. 2021 24-28*
- High-frequency discharges**
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**High- $k$  dielectric materials**

Temperature-Dependent Electrical Properties of nMOSFETs With Different Thickness  $\text{Al}_2\text{O}_3$  Capping Layer and TiN Gate. *Wang, D.*, +, *TED Dec. 2021 6020-6025*

**High- $k$  dielectric thin films**

3-D AND-Type Flash Memory Architecture With High- $\kappa$  Gate Dielectric for High-Density Synaptic Devices. *Seo, Y.*, +, *TED Aug. 2021 3801-3806*

Analytical Study on a 700 V Triple RESURF LDMOS With a Variable High- $K$  Dielectric Trench. *Cao, Z.*, +, *TED June 2021 2872-2878*

Breakdown Voltage Enhancement in ScAlN/GaN High-Electron-Mobility Transistors by High- $k$  Bismuth Zinc Niobate Oxide. *Cheng, J.*, +, *TED July 2021 3333-3338*

Characterization of  $\text{Al}_2\text{O}_3/\text{LaAlO}_3/\text{SiO}_2$  Gate Stack on 4H-SiC After Post-Deposition Annealing. *Huang, L.*, +, *TED April 2021 2133-2137*

Effect of the Si Doping Content in  $\text{HfO}_2$  Film on the Key Performance Metrics of Ferroelectric FETs. *Mulaosmanovic, H.*, +, *TED Sept. 2021 4773-4779*

Enhancement-Mode Atomic-Layer-Deposited  $\text{In}_2\text{O}_3$  Transistors With Maximum Drain Current of 2.2 A/mm at Drain Voltage of 0.7 V by Low-Temperature Annealing and Stability in Hydrogen Environment. *Si, M.*, +, *TED March 2021 1075-1080*

Exploiting Fringing Fields Created by High- $\kappa$  Gate Insulators to Enhance the Performance of Ultrascaled 2-D-Material-Based Transistors. *Bennett, R.K.A.*, +, *TED Sept. 2021 4618-4624*

High Field Temperature-Independent Field-Effect Mobility of Amorphous Indium-Gallium-Zinc Oxide Thin-Film Transistors: Understanding the Importance of Equivalent-Oxide-Thickness Downscaling. *Han, K.*, +, *TED Jan. 2021 118-124*

Impact of the Nonlinear Dielectric Hysteresis Properties of a Charge Trap Layer in a Novel Hybrid High-Speed and Low-Power Ferroelectric or Antiferroelectric HSO/HZO Boosted Charge Trap Memory. *Ali, T.*, +, *TED April 2021 2098-2106*

Interfacial Properties of nMOSFETs With Different  $\text{Al}_2\text{O}_3$  Capping Layer Thickness and TiN Gate Stacks. *Wang, D.*, +, *TED March 2021 948-953*

Low-Frequency Noise Analysis of the Optimized Post High- $k$  Deposition Annealing in FinFET Technology. *Deng, W.*, +, *TED March 2021 1202-1206*

Low-Voltage Operating Field-Effect Transistors and Inverters Based on  $\text{In}_2\text{O}_3$  Nanofiber Networks. *Xia, Y.*, +, *TED May 2021 2522-2529*

Novel LDMOS With Integrated Triple Direction High- $k$  Gate and Field Dielectrics. *Yao, J.*, +, *TED Aug. 2021 3997-4003*

Polycrystalline/Amorphous  $\text{HfO}_2$  Bilayer Structure as a Gate Dielectric for  $\beta\text{-Ga}_2\text{O}_3$  MOS Capacitors. *Yang, J.Y.*, +, *TED March 2021 1011-1015*

Quantum Dot With a Diamond-Shaped Channel MOSFET on a Bulk Si Substrate. *Gu, J.*, +, *TED Jan. 2021 405-410*

Vertical Sandwich GAA FETs With Self-Aligned High- $k$  Metal Gate Made by Quasi Atomic Layer Etching Process. *Zhang, Y.*, +, *TED June 2021 2604-2610*

**High-pressure solid-state phase transformations**

Influence of High-Pressure Annealing Conditions on Ferroelectric and Interfacial Properties of Zr-Rich  $\text{Hf}_x\text{Zr}_{1-x}\text{O}_2$  Capacitors. *Das, D.*, +, *TED April 2021 1996-2002*

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- Crosstalk Suppression in Monolithic GaN Devices Based on Inverted E-Field Decoupling. *Sun, R.*, +, *TED April 2021 1542-1549*
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- Impact of Random Phase Distribution in Ferroelectric Transistors-Based 3-D NAND Architecture on In-Memory Computing. *Choe, G.*, +, *TED May 2021 2543-2548*
- Variability and Energy Consumption Tradeoffs in Multilevel Programming of RRAM Arrays. *Perez, E.*, +, *TED June 2021 2693-2698*
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- Heterogeneous Integration of III–V Materials by Direct Wafer Bonding for High-Performance Electronics and Optoelectronics. *Caimi, D.*, +, *TED July 2021 3149-3156*
- Intelligent Forward-Wave Amplifier Design With Deep Learning and Genetic Algorithm. *Liu, K.*, +, *TED July 2021 3568-3575*
- Low-Voltage, High-Brightness Silicon Micro-LEDs for CMOS Photonics. *Xue, J.*, +, *TED Aug. 2021 3870-3875*
- Optically Controlled Ferroelectric Nanodomains for Logic-in-Memory Photonic Devices With Simplified Structures. *Xue, F.*, +, *TED April 2021 1992-1995*
- Sub-mA/cm<sup>2</sup> Dark Current Density, Buffer-Less Germanium (Ge) Photodiodes on a 200-mm Ge-on-Insulator Substrate. *Lin, Y.*, +, *TED April 2021 1730-1737*
- Theoretical Prediction of High-Performance Room-Temperature InGaAs/Si Single-Photon Avalanche Diode Fabricated by Semiconductor Interlayer Bonding. *Ke, S.*, +, *TED April 2021 1694-1701*
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- Phosphor-Based InGaIn/GaN White Light-Emitting Diodes With Monolithically Integrated Photodetectors. *Yin, J.*, +, *TED Jan. 2021 132-137*
- Scalable mmWave Non-Volatile Phase Change GeTe-Based Compact Monolithically Integrated Wideband Digital Switched Attenuator. *Singh, T.*, +, *TED May 2021 2306-2312*
- Silicene/MoS<sub>2</sub> Heterojunction for High-Performance Photodetector. *Kharadi, M.A.*, +, *TED Jan. 2021 138-143*
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- Electronic Skin With Embedded Carbon Nanotubes Proximity Sensors. *Ben-Yasharand, G.*, +, *TED Aug. 2021 4098-4103*
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- A Highly Efficient Annealing Process With Supercritical N<sub>2</sub>O at 120 °C for SiO<sub>2</sub>/4H–SiC Interface. *Wang, M.*, +, *TED April 2021 1841-1846*

- A Novel Approach for the Modeling of the Dynamic ON-State Resistance of GaN-HEMTs. *Weiser, M.C.J.*, +, *TED Sept. 2021 4302-4309*
- A Study of the Gate-Stack Small-Signal Model and Determination of Interface Traps in GaN-Based MIS-HEMTs. *Huang, Z.*, +, *TED April 2021 1507-1512*
- An Interface-Induced Dielectric Properties Degradation in Heterogeneous Stacked Device With P(VDF-TrFE)-Based Ferroelectric Polymers. *Chen, Y.*, +, *TED Feb. 2021 739-745*
- Analysis of Mobility for 4H-SiC N/P-Channel MOSFETs Up To 300 °C. *Yang, L.*, +, *TED Aug. 2021 3936-3941*
- Applicability of Shockley–Read–Hall Theory for Interface States. *Ruch, B.*, +, *TED April 2021 2092-2097*
- Capacitance–Voltage Technique Based on Time Varying Magnetic Field for VDMOSFET—Part II: Measurements and Parameter Extractions. *Tahi, H.*, +, *TED May 2021 2181-2188*
- Characterization of Al<sub>2</sub>O<sub>3</sub>/LaAlO<sub>3</sub>/SiO<sub>2</sub> Gate Stack on 4H-SiC After Post-Deposition Annealing. *Huang, L.*, +, *TED April 2021 2133-2137*
- Compact Modeling of Temperature Effects in FDSOI and FinFET Devices Down to Cryogenic Temperatures. *Pahwa, G.*, +, *TED Sept. 2021 4223-4230*
- Dynamic Model of FWC Dependent on the Energy-Level Distribution of Interface-State Traps in Pinned Photodiodes. *Xia, C.*, +, *TED April 2021 1682-1687*
- Effects of Ambient/Carrier Gas on Amorphous InGaZnO-Based Thin-Film Transistors Using Ultrasonic Spray Pyrolysis Deposition. *Liu, H.*, +, *TED June 2021 2729-2735*
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- Enhancement-Mode Atomic-Layer-Deposited In<sub>2</sub>O<sub>3</sub> Transistors With Maximum Drain Current of 2.2 A/mm at Drain Voltage of 0.7 V by Low-Temperature Annealing and Stability in Hydrogen Environment. *Si, M.*, +, *TED March 2021 1075-1080*
- High-Performance Thin-Film IGZO Schottky Diodes With Sputtered PdO<sub>x</sub> Anode. *Yan, S.*, +, *TED Sept. 2021 4444-4449*
- Hydrogenation of Mg-Doped InGaZnO Thin-Film Transistors for Enhanced Electrical Performance and Stability. *Abliz, A.*, *TED July 2021 3379-3383*
- Impact of Trapped-Charge Variations on Scaled Ferroelectric FET Nonvolatile Memories. *Liu, Y.*, +, *TED April 2021 1639-1643*
- Implementation of RTCVD-Si<sub>3</sub>N<sub>4</sub> Gate Dielectric Into Enhancement-Mode GaN MIS-HEMTs Fabricated on Ultrathin-Barrier AlGaIn/GaN-on-Si Platform. *Shi, W.*, +, *TED Sept. 2021 4274-4277*
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- Improvement of Both n- and p-Channel Mobilities in 4H-SiC MOSFETs by High-Temperature N<sub>2</sub> Annealing. *Tachiki, K.*, +, *TED Feb. 2021 638-644*
- Interface Charge Effects on 2-D Electron Gas in Vertical-Scaled Ultrathin-Barrier AlGaIn/GaN Heterostructure. *Huang, S.*, +, *TED Jan. 2021 36-41*
- Interface Optimization of Passivated Er<sub>2</sub>O<sub>3</sub>/Al<sub>2</sub>O<sub>3</sub>/InP MOS Capacitors and Modulation of Leakage Current Conduction Mechanism. *Qiao, L.*, +, *TED June 2021 2899-2905*
- Interface States Characterization of UTB SOI MOSFETs From the Sub-threshold Current. *Vermeer, M.L.*, +, *TED Feb. 2021 497-502*
- Investigation of the Impact of Hot-Carrier-Induced Interface State Generation on Carrier Mobility in nMOSFET. *Wu, Z.*, +, *TED July 2021 3246-3253*
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- Low Subthreshold Swing and High Performance of Ultrathin PEALD InGaZnO Thin-Film Transistors. *Jeong, S.*, +, *TED April 2021 1670-1675*
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- Modeling of Semiconductor Substrates for RF Applications: Part I—Static and Dynamic Physics of Carriers and Traps. *Rack, M.*, +, *TED Sept. 2021 4598-4605*
- On Noise Performance of Dual-Gated Silicon FET Biosensors With Schottky Contacts. *Gao, W.*, +, *TED June 2021 2965-2970*
- ON-Resistance of Ga<sub>2</sub>O<sub>3</sub> Trench-MOS Schottky Barrier Diodes: Role of Sidewall Interface Trapping. *Li, W.*, +, *TED May 2021 2420-2426*
- Quantitative Characterization of Ferroelectric/Dielectric Interface Traps by Pulse Measurements. *Li, J.*, +, *TED March 2021 1214-1220*
- Schottky Barrier Height Modulation of Zr/p-Diamond Schottky Contact by Inserting Ultrathin Atomic Layer-Deposited Al<sub>2</sub>O<sub>3</sub>. *Wang, J.*, +, *TED Dec. 2021 5995-6000*
- Structural and Electrical Characteristics of ALD-TiO<sub>2</sub>/SiON/n-Si Gate-Stack for Advanced CMOS Device Applications. *Gupta, R.*, +, *TED June 2021 2625-2632*
- Super Single Pulse Charge Pumping Technique for Profiling Interfacial Defects. *Chen, Y.*, +, *TED Feb. 2021 726-732*
- Temperature-Dependent Low-Frequency Noise Analysis of ZnO Nanowire Field-Effect Transistors. *Xue, H.*, +, *TED July 2021 3532-3536*
- The Effect of Interface Traps at the Si/SiO<sub>2</sub> Interface on the Transient Negative Capacitance of Ferroelectric FETs. *Sun, X.*, +, *TED Sept. 2021 4735-4740*
- The Relationship Between Resistive Protective Oxide (RPO) and Hot Carrier Stress (HCS) Degradation in n-Channel LD SOI MOSFET. *Lin, Y.*, +, *TED March 2021 962-967*
- Transfer Doping in Diamond for Channel Doping and Electrical Contacts. *Huddleston, L.*, +, *TED Sept. 2021 4231-4236*
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- Strategy of Mitigating Breakdown Interference and Yield Loss in Crossbar Memory. *Chang, C.*, +, *TED Dec. 2021 6082-6086*
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- A Study of Linearity of C-H Diamond FETs for S-Band Power Application. *Fu, Y.*, +, *TED Aug. 2021 3950-3955*
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- Degradation Behavior and Defect Analysis for SiC Power MOSFETs Based on Low-Frequency Noise Under Repetitive Power-Cycling Stress. *Yang, X.*, +, *TED Feb. 2021 666-671*
- Stress Engineering as a Strategy to Achieve High Ferroelectricity in Thick Hafnia Using Interlayer. *Joh, H.*, +, *TED May 2021 2538-2542*
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- Spintronic Computing-in-Memory Architecture Based on Voltage-Controlled Spin–Orbit Torque Devices for Binary Neural Networks. *Wang, H.*, +, *TED Oct. 2021 4944-4950*
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- Investigation of Electrical and Optical Properties of AlGaInP Red Vertical Micro-Light-Emitting Diodes With Cu/Invar/Cu Metal Substrates. *Sinha, S.*, +, *TED June 2021 2818-2822*

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- Effect of Femtosecond Laser Postannealing on a-IGZO Thin-Film Transistors. *Lee, J.*, +, *TED July 2021 3371-3378*
- Energy Storage and Reuse in Negative Capacitance. *Kao, M.*, +, *TED April 2021 1861-1865*
- Flexible Complementary Oxide Thin-Film Transistor-Based Inverter With High Gain. *Hsu, S.*, +, *TED March 2021 1070-1074*
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- Performance Projection of 2-D Material-Based CMOS Inverters for Sub-10-nm Channel Length. *Rawat, A.*, +, *TED July 2021 3622-3629*
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- Gate Oxide Damage of SiC MOSFETs Induced by Heavy-Ion Strike. *Zhou, X.*, +, *TED Aug. 2021 4010-4015*
- New Concerns on Heavy Ion Irradiation Induced Variation Degradation in Nanoscale CMOS Devices. *Ren, Z.*, +, *TED April 2021 2142-2146*
- Simulation Study on Single-Event Burnout in Rated 1.2-kV 4H-SiC Super-Junction VDMOS. *Yu, C.*, +, *TED Oct. 2021 5034-5040*
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- 1100 V, 22.9 mΩcm<sup>2</sup> 4H-SiC RESURF Lateral Double-Implanted MOSFET With Trench Isolation. *Hu, J.*, +, *TED Oct. 2021 5009-5013*
- A Compact Trench-Assisted Space-Modulated JTE Design for High-Voltage 4H-SiC Devices. *Dai, T.*, +, *TED March 2021 1162-1167*
- A Novel High-Performance Planar InAs/GaSb Face-Tunneling FET With Implanted Drain for Leakage Current Reduction. *Lyu, Z.*, +, *TED March 2021 1313-1317*
- Channel Properties of Ga<sub>2</sub>O<sub>3</sub>-on-SiC MOSFETs. *Wang, Y.*, +, *TED March 2021 1185-1189*
- Corrections to “Optimized Si-Based Blocked Impurity Band Detector Under Alternative Operational Mode” [Sep 19 3891-3895]. *Zhu, H.*, +, *TED Jan. 2021 447*
- Effective Leakage Current Reduction in GaN Ultraviolet Avalanche Photodiodes With an Ion-Implantation Isolation Method. *Cho, M.*, +, *TED June 2021 2759-2763*
- Experimental Investigation of As Preamorphization Implant on Electrical Property of Ti-Based Silicide Contacts. *Mao, S.*, +, *TED April 2021 1835-1840*
- Investigation of *V*<sub>th</sub> Distribution Tails of Ground-Select-Line Cells and Edge Dummy Cells in a 3-D NAND Flash Memory. *Chou, Y.*, +, *TED May 2021 2260-2264*
- Low-Temperature Processing of Electronic Materials Using Uniform Microwave Fields. *Hubbard, R.L.*, *TED July 2021 3170-3175*
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- Suppression of Stress-Induced Defects in FinFET by Implantation and STI Co-Optimization. *Ye, B.*, +, *TED May 2021 2587-2589*
- Ultrashallow Junction (USJ) Fabrication by Advanced Ion Implantation Processes. *Qin, S.*, *TED April 2021 1855-1860*
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- Enhanced pH Sensitivity of AlGaN/GaN Ion-Sensitive Field-Effect Transistor by Recess Process and Ammonium Hydroxide Treatment. *He, Y.*, +, *TED March 2021 1250-1254*

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- Temperature Dependence of Electron and Hole Impact Ionization Coefficients in GaN. *Cao, L.*, +, *TED March 2021 1228-1234*

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- Evaluation of Single-Event-Transient Effects in Reconfigurable Field Effect Transistor Beyond 3 nm Technology Node. *Sun, Y.*, +, *TED Dec. 2021 6001-6006*
- Impact of Nonuniform Ozone Anneal Treatment on the Resistance Levels in an IGZO-ReRAM Fabricated on ITO-Coated Glass Substrate. *Kishore, R.*, +, *TED Dec. 2021 6087-6093*
- Machine Learning Regression-Based Single-Event Transient Modeling Method for Circuit-Level Simulation. *Xu, C.*, +, *TED Nov. 2021 5758-5764*
- Nonuniform Space Charge Limited Current for 2-D Bipolar Flow in Vacuum Diode. *Zhu, Y.B.*, +, *TED Dec. 2021 6538-6545*
- Study of a Highly Sensitive Formaldehyde Sensor Prepared With a Tungsten Trioxide Thin Film and Gold Nanoparticles. *Niu, J.*, +, *TED Dec. 2021 6422-6429*

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- Efficient Modeling of Charge Trapping at Cryogenic Temperatures—Part I: Theory. *Michl, J.*, +, *TED Dec. 2021 6365-6371*

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- First Experimental Demonstration of Robust HZO/ $\beta$ -Ga<sub>2</sub>O<sub>3</sub> Ferroelectric Field-Effect Transistors as Synaptic Devices for Artificial Intelligence Applications in a High-Temperature Environment. *Noh, J.*, +, *TED May 2021 2515-2521*
- High Field-Effect Mobility Two-Channel InGaZnO Thin-Film Transistors for Low-Voltage Operation. *Yun, K.*, +, *TED Dec. 2021 6166-6170*
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- Highly Reliable Electrocaloric Behaviors of Antiferroelectric Al:ZrO<sub>2</sub> Thin Films for Solid-State Cooling in Integrated Circuits. *Liu, Y.*, +, *TED Dec. 2021 6352-6358*
- Improved Tradeoff Between Subthreshold Swing and Hysteresis for MoS<sub>2</sub> Negative-Capacitance FETs by Optimizing Gate-Stack of Hf<sub>1-x</sub>Zr<sub>x</sub>O<sub>2</sub>/Al<sub>2</sub>O<sub>3</sub>. *Wang, J.*, +, *TED Dec. 2021 6546-6550*
- Interplay of Various Charge Sources in AlGaN/GaN Epi-Stack Governing HEMT Breakdown. *Soni, A.*, +, *TED May 2021 2378-2386*
- Mechanism of Extraordinary High Mobility in Multilayered Amorphous Oxide Thin Film Transistor. *Lee, J.Y.*, +, *TED Nov. 2021 5618-5622*
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- Multigate Ferroelectric Transistor Design Toward 3-nm Technology Node. *Choe, G.*, +, *TED Nov. 2021 5908-5911*
- Study of the Nonenzymatic CZO Lactic Acid Sensor Modified by Graphitic Carbon Nitride and Iron-Platinum Nanoparticles. *Nien, Y.*, +, *TED Oct. 2021 5142-5148*
- The Influence of Fe Doping Tail in Unintentionally Doped GaN Layer on DC and RF Performance of AlGaN/GaN HEMTs. *Jia, F.*, +, *TED Dec. 2021 6069-6075*
- Threshold Selector and Capacitive Coupled Assist Techniques for Write Voltage Reduction in Metal-Ferroelectric-Metal Field-Effect Transistor. *Raman, S.R.S.*, +, *TED Dec. 2021 6132-6138*

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- Experimental Demonstration of Angle-Dependent GMR Effect in Py/WSe<sub>2</sub>/Co Spin Valve Structure. *Cao, Y.*, +, *TED July 2021 3690-3695*
- First Demonstration of 25-nm Quad Interface p-MTJ Device With Low Resistance-Area Product MgO and Ten Years Retention for High Reliable STT-MRAM. *Nishioka, K.*, +, *TED June 2021 2680-2685*



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## J

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A High-Performance 4H-SiC JFET With Reverse Recovery Capability and Low Switching Loss. *Kong, M.*, +, *TED Oct. 2021 5022-5028*

A Novel Approach to Inactivate the Body p-i-n Diode of SiC MOSFET by Using the Normally-OFF JFET. *Li, P.*, +, *TED April 2021 1784-1790*

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A TCAD Simulation Study of Three-Independent-Gate Field-Effect Transistors at the 10-nm Node. *Cadareanu, P.*, +, *TED Aug. 2021 4129-4135*

Digital Performance Assessment of the Dual-Material Gate GaAs/InAs/Ges Junctionless TFET. *Vadizadeh, M.*, +, *TED April 2021 1986-1991*

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Evaluation of Single-Event-Transient Effects in Reconfigurable Field Effect Transistor Beyond 3 nm Technology Node. *Sun, Y.*, +, *TED Dec. 2021 6001-6006*

Investigation of Leaky Characteristic in a Single-Transistor-Based Leaky Integrate-and-Fire Neuron. *Han, J.*, +, *TED Nov. 2021 5912-5915*

Nitrogen-Implanted Guard Rings for 600-V Quasi-Vertical GaN-on-Si Schottky Barrier Diodes With a BFOM of 0.26 GW/cm<sup>2</sup>. *Guo, X.*, +, *TED Nov. 2021 5682-5686*

Plasma Spreading Layers: An Effective Method for Improving Surge and Avalanche Robustness of SiC Devices. *Ren, N.*, +, *TED Nov. 2021 5687-5694*

## K

#### Kalman filters

Room-Temperature Hydrogen- and Ammonia Gas-Sensing Characteristics of a GaN-Based Schottky Diode Synthesized With a Hybrid Surface Structure. *Chen, W.*, +, *TED Feb. 2021 761-768*

#### Kidney

Fabrication of Glutathione-S-Transferase–ZnO Nanoconjugate Ensemble FET Device for Detection of Glutathione. *Barman, U.*, +, *TED March 2021 1242-1249*

#### Klystrons

Concept and Simulations of 800 MHz Two-Stage MBK for FCC. *Teryaev, V.E.*, +, *TED March 2021 1271-1275*

Demonstration of the Electronic Cutoff Field in Millimeter-Wave Extended Interaction Oscillators. *Xu, C.*, +, *TED May 2021 2473-2479*

Design of a 48 GHz Gyroklystron Amplifier. *Nix, L.J.R.*, +, *TED Nov. 2021 5792-5798*

Efficiency Enhancement of a High Power Radial-Line Relativistic Klystron Amplifier Driven by Disk Intense Electron Beam. *Dang, F.*, +, *TED Nov. 2021 5834-5840*

Electron Flow Modulation in Double-Gap Cavity With a Multiple Ratio of the Two Modes Frequencies. *Muchkaev, V.Y.*, +, *TED Feb. 2021 835-840*

Experimental Investigation of a Super Klystron-Like Relativistic Backward Wave Oscillator Operating With Low Magnetic Field. *Wang, H.*, +, *TED June 2021 3045-3050*

High Efficiency Compact Microwave Sources Using Electrostatic Potential Depression. *Xu, H.*, +, *TED April 2021 1930-1935*  
 Numerical Analysis of Resonant Multipolar Instabilities in High Power Klystrons. *Cai, J.*, +, *TED July 2021 3617-3621*  
 Study of a Dual-Mode Multibeam Interaction Circuit With Coaxial Structure for Ka-Band High-Power EIK. *Zhang, X.*, +, *TED Feb. 2021 822-828*

## L

### Lab-on-a-chip

Application of a Thin-Film Transistor Array for Cellular-Resolution Electrophysiology and Electrochemistry. *Eiler, A.*, +, *TED April 2021 2041-2048*  
 Flexible Printed Circuit Board as Novel Electrodes for Acoustofluidic Devices. *Sun, C.*, +, *TED Jan. 2021 393-398*

### Laminar flow

Development of Laser-Induced Graphene-Based Automated Electro Microfluidic Viscometer for Biochemical Sensing Applications. *Wagh, M.D.*, +, *TED Oct. 2021 5184-5191*

### Laminates

Interface Optimization of Passivated Er<sub>2</sub>O<sub>3</sub>/Al<sub>2</sub>O<sub>3</sub>/InP MOS Capacitors and Modulation of Leakage Current Conduction Mechanism. *Qiao, L.*, +, *TED June 2021 2899-2905*

### Lanthanum compounds

Characterization of Al<sub>2</sub>O<sub>3</sub>/LaAlO<sub>3</sub>/SiO<sub>2</sub> Gate Stack on 4H-SiC After Post-Deposition Annealing. *Huang, L.*, +, *TED April 2021 2133-2137*  
 Solution-Driven HfLaO<sub>x</sub>-Based Gate Dielectrics for Thin Film Transistors and Unipolar Inverters. *Wang, W.*, +, *TED Sept. 2021 4437-4443*

### Laplace equations

Novel Vertical Power MOSFET With Step Hk Insulator Close to Super Junction Limit Relationship Between Breakdown Voltage and Specific ON-Resistance by Improving Electric Field Modulation. *Duan, B.*, +, *TED Oct. 2021 5048-5054*

### Laser ablation

Miniaturized PMMA Electrochemical Platform With Carbon Fiber for Multiplexed and Noninterfering Biosensing of Real Samples. *Mohan, J.M.*, +, *TED Feb. 2021 769-774*  
 Portable Electrochemiluminescence Platform With Laser-Induced Graphene-Based U-Shaped Bipolar Electrode for Selective Sensing of Various Analytes. *Bhaiyya, M.*, +, *TED May 2021 2447-2454*  
 Portable Thermal Management Platform for Synthesis of ZnO Nanoparticle in a Microfluidic Device: Validated for Electrochemical Sensing and Glucose Fuel Cell Applications. *Kulkarni, M.B.*, +, *TED Aug. 2021 4070-4076*

### Laser beam annealing

A Review of Low Temperature Process Modules Leading Up to the First ( $\leq 500$  °C) Planar FDSOI CMOS Devices for 3-D Sequential Integration. *Fenouillet-Beranger, C.*, +, *TED July 2021 3142-3148*  
 Effect of Femtosecond Laser Postannealing on a-IGZO Thin-Film Transistors. *Lee, J.*, +, *TED July 2021 3371-3378*  
 High Performance Dual Gate Blue Laser Annealed Poly-Si Thin-Film Transistor for High-Resolution Displays. *Jeong, D.Y.*, +, *TED Aug. 2021 3863-3869*

### Laser beam effects

Fabricating In-Plane MoTe<sub>2</sub> p-n Homojunction Photodetector Using Laser-Induced p-Type Doping. *Chen, J.*, +, *TED Sept. 2021 4485-4490*  
 Tunable Alloying Improved Wide Spectrum UV-Vis-NIR and Polarization-Sensitive Photodetector Based on Sb-S-Se Nanowires. *Yu, Y.*, +, *TED Aug. 2021 3887-3893*  
 UV Light Detection Using Resonance Frequency of Piezoelectric Quartz Crystal. *Das, S.*, +, *TED June 2021 2791-2795*

### Laser beams

190 °C High-Temperature Operation of 905-nm VCSELs With High Performance. *Xun, M.*, +, *TED June 2021 2829-2834*  
 Low-Voltage Thyristor Heterostructure for High-Current Pulse Generation at High Repetition Rate. *Slipchenko, S.O.*, +, *TED June 2021 2855-2860*  
 Side-Illuminated Photoconductive Semiconductor Switch Based on High Purity Semi-Insulating 4H-SiC. *Choi, P.H.*, +, *TED Dec. 2021 6216-6221*

### Laser cavity resonators

190 °C High-Temperature Operation of 905-nm VCSELs With High Performance. *Xun, M.*, +, *TED June 2021 2829-2834*  
 Analysis of Thermal Properties of 940-nm Vertical Cavity Surface Emitting Laser Arrays. *Xun, M.*, +, *TED Jan. 2021 158-163*

### Laser excitation

Enhanced Color Quality of Phosphor-Converted White Laser Diodes Through Bicolor Phosphor-in-Glass. *Wang, H.*, +, *TED Nov. 2021 5652-5655*

### Laser modes

190 °C High-Temperature Operation of 905-nm VCSELs With High Performance. *Xun, M.*, +, *TED June 2021 2829-2834*

### Laser stability

Comparison of Chromium- and Aluminum-Gated Nanocrystalline Silicon TFTs. *Anutgan, T.*, +, *TED Dec. 2021 6182-6189*  
 Effect of Transition Mechanism of Photon-Induced Carriers on Time Jitter of GaAs Photoconductive Semiconductor Switches. *Zhang, L.*, +, *TED Dec. 2021 6262-6265*

### Laser tuning

Heterogeneous Integration of III-V Materials by Direct Wafer Bonding for High-Performance Electronics and Optoelectronics. *Caimi, D.*, +, *TED July 2021 3149-3156*

### Lattices

Efficient TCAD Thermal Analysis of Semiconductor Devices. *Catoggio, E.*, +, *TED Nov. 2021 5462-5468*  
 Performance Investigation of p-FETs Based on Highly Air-Stable Monolayer Pentagonal PdSe<sub>2</sub>. *Nandan, K.*, +, *TED Dec. 2021 6551-6557*

### Layout

Investigation and Suppression of Holding Voltage Deterioration in Multifinger SCR for Robust High-Voltage ESD Engineering. *Du, F.*, +, *TED Dec. 2021 6338-6343*  
 Power Combining of Dual X-Band Coaxial Magnetrons Based on Peer-to-Peer Locking. *Liu, J.*, +, *TED Dec. 2021 6518-6524*

### Lead

High-Detectivity and Stable Planar MAPbI<sub>3</sub>/IDT-BT Photodetectors With Assisted MoO<sub>3</sub> Interlayer. *Zhao, K.*, +, *TED Dec. 2021 6266-6272*  
 Investigation of CsSn<sub>0.5</sub>Ge<sub>0.5</sub>I<sub>3</sub>-on-Si Tandem Solar Device Utilizing SCAPS Simulation. *Islam, M.T.*, +, *TED Feb. 2021 618-625*

### Lead compounds

Engineering of a Blocking Layer Structure for Low-Lag Operation of the a-PbO-Based X-Ray Detector. *Grynko, O.*, +, *TED May 2021 2335-2341*  
 PbSnS<sub>2</sub>-Based Gas Sensor to Detect SF<sub>6</sub> Decompositions: DFT and NEGF Calculations. *Guo, H.*, +, *TED Oct. 2021 5322-5325*

### Leakage currents

1.2-kV Vertical GaN Fin-JFETs: High-Temperature Characteristics and Avalanche Capability. *Liu, J.*, +, *TED April 2021 2025-2032*  
 1300 V Normally-OFF p-GaN Gate HEMTs on Si With High ON-State Drain Current. *Jiang, H.*, +, *TED Feb. 2021 653-657*  
 650-V 4H-SiC Planar Inversion-Channel Power JBSFETs With 55-nm Gate Oxide: Relative Performance of Three Cell Types. *Agarwal, A.*, +, *TED May 2021 2395-2400*  
 75 nm Gate Length PHEMT With  $f_{\max} = 800$  GHz Using Asymmetric Gate Recess: RF and Noise Investigation. *Samnoui, M.*, +, *TED Sept. 2021 4289-4295*  
 A 4T2R RRAM Bit Cell for Highly Parallel Ternary Content Addressable Memory. *Wang, X.*, +, *TED Oct. 2021 4933-4937*  
 A Novel High-Performance Planar InAs/GaSb Face-Tunneling FET With Implanted Drain for Leakage Current Reduction. *Lyu, Z.*, +, *TED March 2021 1313-1317*  
 A Physical Model for Bulk Gate Insulator Trap Generation During Bias-Temperature Stress in Differently Processed p-Channel FETs. *Samadder, T.*, +, *TED Feb. 2021 485-490*  
 A Study on the Isolation Ability of LOCAL Oxidation of SiC (LOCOSiC) for 4H-SiC CMOS Process. *Tsui, B.*, +, *TED Dec. 2021 6644-6647*  
 An Analytical Effective-Diode-Based Analysis of Industrial Solar Cells From Three-Diode Lumped-Parameter Model. *Xu, C.*, +, *TED June 2021 2753-2758*

- Analysis of Dependence of Breakdown Voltage on Gate–Drain Distance in AlGaIn/GaN HEMTs With High- $k$  Passivation Layer. *Tomita, R.*, +, *TED April 2021 1550-1556*
- Analysis of Single Event Effects in Capacitor-Less 1T-DRAM Based on an InGaAs Transistor. *Yan, G.*, +, *TED April 2021 1604-1609*
- Anomalous GIDL Effect With Back Bias in FinFET: Physical Insights and Compact Modeling. *Dabhi, C.K.*, +, *TED July 2021 3261-3267*
- Benchmarking Silicon FinFET With the Carbon Nanotube and 2D-FETs for Advanced Node CMOS Logic Application. *Das, U.K.*, +, *TED July 2021 3643-3648*
- Characteristics of InAs/GaSb Line-Tunneling FETs With Buried Drain Technique. *Lu, B.*, +, *TED April 2021 1537-1541*
- Characterization and Modeling of Native MOSFETs Down to 4.2 K. *Zhang, Y.*, +, *TED Sept. 2021 4267-4273*
- Comprehensive Annealing Effects on AlGaIn/GaN Schottky Barrier Diodes With Different Work-Function Metals. *Zhang, T.*, +, *TED June 2021 2661-2666*
- Controlled Majority-Inverter Graph Logic With Highly Nonlinear, Self-Rectifying Memristor. *Ni, R.*, +, *TED Oct. 2021 4897-4902*
- Cryogenic Characteristics of Multinanoscale Field-Effect Transistors. *Liu, Y.*, +, *TED Feb. 2021 456-463*
- Degradation Behavior and Defect Analysis for SiC Power MOSFETs Based on Low-Frequency Noise Under Repetitive Power-Cycling Stress. *Yang, X.*, +, *TED Feb. 2021 666-671*
- Drain-Bias-Dependent Study of Reverse Gate-Leakage Current in AlGaIn/GaN HFETs. *Singh, I.P.*, +, *TED Feb. 2021 503-509*
- Dramatic Improvement in the Rectifying Properties of Pd Schottky Contacts on  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> During Their High-Temperature Operation. *Hou, C.*, +, *TED April 2021 1791-1797*
- Effect of Atmosphere on Electrical Characteristics of AlGaIn/GaN HEMTs Under Hot-Electron Stress. *Liu, C.*, +, *TED March 2021 1000-1005*
- Effect of Femtosecond Laser Postannealing on a-IGZO Thin-Film Transistors. *Lee, J.*, +, *TED July 2021 3371-3378*
- Effect of Random Dopant Fluctuation on Data Retention Time Distribution in DRAM. *Kim, K.Y.*, +, *TED Nov. 2021 5572-5577*
- Effective Leakage Current Reduction in GaN Ultraviolet Avalanche Photodiodes With an Ion-Implantation Isolation Method. *Cho, M.*, +, *TED June 2021 2759-2763*
- Efficient 1-V Boost Converter Using Sub-50-mV NEMS Without Body Bias. *Saha, S.*, +, *TED June 2021 2944-2950*
- Electrical and Reliability Characteristics of FinFETs With High- $k$  Gate Stack and Plasma Treatments. *Li, Y.*, +, *TED Jan. 2021 4-9*
- Electronic Fluctuation of Graphene Nanoribbon MOSFETs Under a Full Quantum Dynamics Framework. *Ly, Y.*, +, *TED April 2021 1980-1985*
- Energy Band Adjustment in a Reliable Novel Charge Plasma SiGe Source TFET to Intensify the BTBT Rate. *Anvarifard, M.K.*, +, *TED Oct. 2021 5284-5290*
- Enhancement of DRAM Performance by Adopting Metal–Interlayer–Semiconductor Source/Drain Contact Structure on DRAM Cell. *Son, M.*, +, *TED May 2021 2275-2280*
- Epi-Gd<sub>2</sub>O<sub>3</sub>-MOSHEMT: A Potential Solution Toward Leveraging the Application of AlGaIn/GaN/Si HEMT With Improved  $I_{ON}/I_{OFF}$  Operating at 473 K. *Sarkar, R.*, +, *TED June 2021 2653-2660*
- Fabrication of Dual-Barrier Planar Structure Diamond Schottky Diodes by Rapid Thermal Annealing. *Wang, J.*, +, *TED March 2021 1176-1180*
- Finger Gate Vacuum Channel Field Emission Transistors: Performance and Sensitivity Analysis. *Khoshkijari, F.K.*, +, *TED Oct. 2021 5250-5256*
- HfZrO<sub>x</sub>-Based Switchable Diode for Logic-in-Memory Applications. *Kao, R.*, +, *TED Feb. 2021 545-549*
- High Breakdown Voltage and Low-Current Dispersion in AlGaIn/GaN HEMTs With High-Quality AlN Buffer Layer. *Kim, J.*, +, *TED April 2021 1513-1517*
- Improvement of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> MIS-SBD Interface Using Al-Reacted Interfacial Layer. *He, M.*, +, *TED July 2021 3314-3319*
- Interface Optimization of Passivated Er<sub>2</sub>O<sub>3</sub>/Al<sub>2</sub>O<sub>3</sub>/InP MOS Capacitors and Modulation of Leakage Current Conduction Mechanism. *Qiao, L.*, +, *TED June 2021 2899-2905*
- Leakage-Prevention Mechanism to Maintain Driving Capability of Compensation Pixel Circuit for Low Frame Rate AMOLED Displays. *Lin, C.*, +, *TED May 2021 2313-2319*
- Low Leakage and High Forward Current Density Quasi-Vertical GaN Schottky Barrier Diode With Post-Mesa Nitridation. *Kang, X.*, +, *TED March 2021 1369-1373*
- NiSi/p<sup>+</sup>-Si(n<sup>+</sup>-Si)/n-Si(p-Si) Diodes With Dopant Segregation (DS): p-n or Schottky Junctions?. *Zhang, D.*, +, *TED June 2021 2886-2891*
- Nitrogen-Implanted Guard Rings for 600-V Quasi-Vertical GaN-on-Si Schottky Barrier Diodes With a BFOM of 0.26 GW/cm<sup>2</sup>. *Guo, X.*, +, *TED Nov. 2021 5682-5686*
- Noise Analysis of the Leakage Current in Time-Dependent Dielectric Breakdown in a GaN SLCFET. *Dalcanale, S.*, +, *TED May 2021 2220-2225*
- Novel TCAD Approach for the Investigation of Charge Transport in Thick Amorphous SiO<sub>2</sub> Insulators. *Giuliano, F.*, +, *TED Nov. 2021 5438-5447*
- Online Monitoring for Threshold Voltage of SiC MOSFET Considering the Coupling Impact on BTI and Junction Temperature. *Xin, J.*, +, *TED April 2021 1772-1777*
- Performance and Reliability Optimization of Supercritical-Nitridation-Treated AlGaIn/GaN High-Electron-Mobility Transistors. *Wu, P.*, +, *TED Sept. 2021 4317-4321*
- Quantitative Characterization of Ferroelectric/Dielectric Interface Traps by Pulse Measurements. *Li, J.*, +, *TED March 2021 1214-1220*
- Radiation Resistance of High-Voltage Silicon and 4H-SiC Power p-i-n Diodes. *Hazdra, P.*, +, *TED Jan. 2021 202-207*
- Recessed AlGaIn/GaN Schottky Barrier Diodes With TiN and NiN Dual Anodes. *Wang, T.*, +, *TED June 2021 2867-2871*
- Recessed Anode AlGaIn/GaN Schottky Barrier Diode for Temperature Sensor Application. *Pu, T.*, +, *TED Oct. 2021 5162-5166*
- Simulation Study on Single-Event Burnout in Rated 1.2-kV 4H-SiC Super-Junction VDMOS. *Yu, C.*, +, *TED Oct. 2021 5034-5040*
- Single-Event Damage-Induced Gate-Leakage Mechanisms in AlGaIn/GaN High-Electron-Mobility Transistors. *Yue, S.*, +, *TED June 2021 2667-2672*
- Structural and Electrical Characteristics of ALD-TiO<sub>2</sub>/SiON/n-Si Gate-Stack for Advanced CMOS Device Applications. *Gupta, R.*, +, *TED June 2021 2625-2632*
- Study of a GaN-Based Light-Emitting Diode With a Ga<sub>2</sub>O<sub>3</sub> Current Blocking Layer and a Ga<sub>2</sub>O<sub>3</sub> Surface Passivation Layer. *Hsu, C.*, +, *TED Aug. 2021 3894-3900*
- Suppression of Gate Leakage Current in  $K_a$ -Band AlGaIn/GaN HEMT With 5-nm SiN Gate Dielectric Grown by Plasma-Enhanced ALD. *Zhang, S.*, +, *TED Jan. 2021 49-52*
- Suppression of Stress-Induced Defects in FinFET by Implantation and STI Co-Optimization. *Ye, B.*, +, *TED May 2021 2587-2589*
- Synaptic Device With High Rectification Ratio Resistive Switching and Its Impact on Spiking Neural Network. *Kim, C.S.*, +, *TED April 2021 1610-1615*
- TCAD-Based Investigation of Double Gate Junctionless Transistor for UV Photodetector. *Kumari, V.*, +, *TED June 2021 2841-2847*
- Three Orders of Reverse Leakage Reduction by Using Supercritical CO<sub>2</sub> Nitriding Process on GaN Quasi-Vertical Schottky Barrier Diode. *Liu, J.*, +, *TED Jan. 2021 197-201*
- Threshold Switching Enabled Sub-pW-Leakage, Hysteresis-Free Circuits. *Cheng, B.*, +, *TED June 2021 3112-3118*
- Total-Ionizing-Dose Radiation-Induced Dual-Channel Leakage Current at Unclosed Edge Termination for High Voltage SOI LDMOS. *Zhou, X.*, +, *TED June 2021 2861-2866*
- Transient Current Enhancement in MIS Tunnel Diodes With Lateral Electric Field Induced by Designed High-Low Oxide Layers. *Huang, S.*, +, *TED Dec. 2021 6580-6585*
- Ultrahigh Uniformity and Stability in NbO<sub>x</sub>-Based Selector for 3-D Memory by Using Ru Electrode. *Zhao, X.*, +, *TED May 2021 2255-2259*
- Learning (artificial intelligence)**
- A Machine Learning-Assisted Model for GaN Ohmic Contacts Regarding the Fabrication Processes. *Wang, Z.*, +, *TED May 2021 2212-2219*

- A More Hardware-Oriented Spiking Neural Network Based on Leading Memory Technology and Its Application With Reinforcement Learning. *Kim, M.*, +, *TED Sept. 2021 4411-4417*
- Characterization and Modeling of Native MOSFETs Down to 4.2 K. *Zhang, Y.*, +, *TED Sept. 2021 4267-4273*
- Compensating Nonuniform OLED Pixel Brightness in a Vertical Blanking Interval by Learning TFT Characteristics. *Koh, J.*, +, *TED July 2021 3396-3402*
- Energy-Efficient All-Spin BNN Using Voltage-Controlled Spin-Orbit Torque Device for Digit Recognition. *Shreya, S.*, +, *TED Jan. 2021 385-392*
- Ferroelectric Field Effect Transistors as a Synapse for Neuromorphic Application. *Lederer, M.*, +, *TED May 2021 2295-2300*
- Redundancy and Analog Slicing for Precise In-Memory Machine Learning—Part I: Programming Techniques. *Pedretti, G.*, +, *TED Sept. 2021 4373-4378*
- Redundancy and Analog Slicing for Precise In-Memory Machine Learning—Part II: Applications and Benchmark. *Pedretti, G.*, +, *TED Sept. 2021 4379-4383*
- LED displays**
- Compensating Nonuniform OLED Pixel Brightness in a Vertical Blanking Interval by Learning TFT Characteristics. *Koh, J.*, +, *TED July 2021 3396-3402*
- Eliminating the Residual Ultraviolet Excitation Light and Increasing Quantum Dot Emission Intensity in LED Display Devices. *Yan, C.*, +, *TED Feb. 2021 584-591*
- Leakage-Prevention Mechanism to Maintain Driving Capability of Compensation Pixel Circuit for Low Frame Rate AMOLED Displays. *Lin, C.*, +, *TED May 2021 2313-2319*
- Reducing Power Consumption of Active-Matrix Mini-LED Backlit LCDs by Driving Circuit. *Deng, M.*, +, *TED May 2021 2347-2354*
- Legged locomotion**
- Approximate Analytical Solution to the Temperature Field in Annular Thermoelectric Generator Made of Temperature-Dependent Material. *Niu, W.*, +, *TED Dec. 2021 6386-6392*
- Life testing**
- An Analytical Model of Hot Carrier Degradation in LDMOS Transistors: Rediscovery of Universal Scaling. *Mahajan, B.K.*, +, *TED Aug. 2021 3923-3929*
- Electrical Characteristics and Reliability of Wafer-on-Wafer (WOW) Bumpless Through-Silicon Via. *Tsai, Y.*, +, *TED July 2021 3520-3525*
- New Erratic Program Disturbance Mechanism of 2T-SONOS Embedded Nonvolatile Memory. *Park, S.*, +, *TED April 2021 1585-1592*
- Preferable Parametric Model for the Lifetime of the Organic Light-Emitting Diode Under Accelerated Current Stress Tests. *Kittaneh, O.A.*, +, *TED Sept. 2021 4478-4484*
- Light absorption**
- Cladded Surface-Plasmon-Enhanced BP Photodetector Based on the Damage-Free Metal-Semiconductor Interface. *Yang, Z.*, +, *TED Jan. 2021 164-167*
- High-Responsivity Solar-Blind Ultraviolet Photodetectors Based on Carbon Nanodots/Graphene Hybrids. *Fang, Y.*, +, *TED March 2021 1101-1106*
- Light emitting diodes**
- A Sandwich Structure Light-Trapping Fluorescence Antenna With Large Field of View for Visible Light Communication. *Yu, B.*, +, *TED Feb. 2021 565-571*
- Active Thermal Management of High-Power LED Through Chip on Thermoelectric Cooler. *Li, S.*, +, *TED April 2021 1753-1756*
- Comparative Study of the Photoelectric and Thermal Performance Between Traditional and Chip-Scale Packaged White LED. *Chen, C.*, +, *TED April 2021 1710-1716*
- Controlling Phosphor Particle Distribution for High-Angular-Color-Uniformity and Low-Cost LEDs Based on Thermalcapillary Flow. *Liu, J.*, +, *TED Feb. 2021 592-596*
- Effective Modulation of GaN-on-Si LED via Indigenous MOSFET Engineering. *Piao, J.*, +, *TED Nov. 2021 5640-5644*
- Electrothermal Model for Power LEDs Based on the Equivalent Resistance Concept for LED Driver Design. *Adamas-Perez, H.*, +, *TED Dec. 2021 6249-6254*
- High-Performance III-Nitride Light-Emitting Diode Stripes. *Jin, H.*, +, *TED Nov. 2021 5629-5633*
- High-Stability Quantum Dot-Converted 3-in-1 Full-Color Mini-Light-Emitting Diodes Passivated With Low-Temperature Atomic Layer Deposition. *Huang, Y.*, +, *TED Feb. 2021 597-601*
- Hole Transport in Ultraviolet Light-Emitting Diode via p-Type Injection Channel. *Mondal, R.K.*, +, *TED May 2021 2320-2325*
- Investigation of Electrical and Optical Properties of AlGaInP Red Vertical Micro-Light-Emitting Diodes With Cu/Invar/Cu Metal Substrates. *Sinha, S.*, +, *TED June 2021 2818-2822*
- Lifetime Color Consistency Analysis of Cool-White LED Luminaires for General Applications. *Padmasali, A.N.*, +, *TED Nov. 2021 5634-5639*
- Low-Voltage, High-Brightness Silicon Micro-LEDs for CMOS Photonics. *Xue, J.*, +, *TED Aug. 2021 3870-3875*
- Phosphor-Based InGaN/GaN White Light-Emitting Diodes With Monolithically Integrated Photodetectors. *Yin, J.*, +, *TED Jan. 2021 132-137*
- Rational Superlattice Electron Blocking Layer Design for Boosting the Quantum Efficiency of 371 nm Ultraviolet Light-Emitting Diodes. *Du, P.*, +, *TED Dec. 2021 6255-6261*
- Reducing Power Consumption of Active-Matrix Mini-LED Backlit LCDs by Driving Circuit. *Deng, M.*, +, *TED May 2021 2347-2354*
- Reliable and Efficient Phosphor-in-Glass-Based Chip-Scale Packaging for High-Power White LEDs. *Zhang, X.*, +, *TED Sept. 2021 4473-4477*
- Solid-State Carbon Dots-Based White Light-Emitting Diodes With Ultrahigh Color Rendering Index and Good Thermal Stability. *Yin, L.*, +, *TED Aug. 2021 3901-3906*
- Study of a GaN-Based Light-Emitting Diode With a Ga<sub>2</sub>O<sub>3</sub> Current Blocking Layer and a Ga<sub>2</sub>O<sub>3</sub> Surface Passivation Layer. *Hsu, C.*, +, *TED Aug. 2021 3894-3900*
- Study on Convective Flow Behaviors of Phosphor Particles During Curing Process of Silicone and the Influences on the Optical Performance of White LEDs. *Ding, X.*, +, *TED June 2021 2778-2784*
- Unraveling the Origin of Low Optical Efficiency for Quantum Dot White Light-Emitting Diodes From the Perspective of Aggregation-Induced Scattering Effect. *Li, Z.*, +, *TED April 2021 1738-1745*
- Light polarization**
- Tunable Alloying Improved Wide Spectrum UV-Vis-NIR and Polarization-Sensitive Photodetector Based on Sb-S-Se Nanowires. *Yu, Y.*, +, *TED Aug. 2021 3887-3893*
- Light scattering**
- Study of the Nonenzymatic CZO Lactic Acid Sensor Modified by Graphitic Carbon Nitride and Iron-Platinum Nanoparticles. *Nien, Y.*, +, *TED Oct. 2021 5142-5148*
- Unraveling the Origin of Low Optical Efficiency for Quantum Dot White Light-Emitting Diodes From the Perspective of Aggregation-Induced Scattering Effect. *Li, Z.*, +, *TED April 2021 1738-1745*
- Light sources**
- A Sun-Tracking CMOS Image Sensor With Black-Sun Readout Scheme. *Kim, H.*, *TED March 2021 1115-1120*
- Lighting**
- Demonstration of High-Performance 4H-SiC MISIM Ultraviolet Photodetector With Operation Temperature of 550 °C and High Responsivity. *Du, F.*, +, *TED Nov. 2021 5662-5665*
- High-Performance III-Nitride Light-Emitting Diode Stripes. *Jin, H.*, +, *TED Nov. 2021 5629-5633*
- Lifetime Color Consistency Analysis of Cool-White LED Luminaires for General Applications. *Padmasali, A.N.*, +, *TED Nov. 2021 5634-5639*
- Phosphor-Based InGaN/GaN White Light-Emitting Diodes With Monolithically Integrated Photodetectors. *Yin, J.*, +, *TED Jan. 2021 132-137*
- Side-Illuminated Photoconductive Semiconductor Switch Based on High Purity Semi-Insulating 4H-SiC. *Choi, P.H.*, +, *TED Dec. 2021 6216-6221*
- The Photosensitive Mechanism of Gap-Type Amorphous Silicon TFT. *Tai, Y.*, +, *TED Dec. 2021 6177-6181*
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- Redundancy and Analog Slicing for Precise In-Memory Machine Learning—Part I: Programming Techniques. *Pedretti, G.*, +, *TED Sept. 2021 4373-4378*

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Enhanced Linearity in CBRAM Synapse by Post Oxide Deposition Annealing for Neuromorphic Computing Applications. *Hsu, C.*, +, *TED Nov. 2021 5578-5584*

**Liquid crystal devices**

Thermistor-Based Nematic Liquid Crystal IM95100-000. *Sun, J.*, +, *TED Aug. 2021 4064-4069*

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AlGaIn/GaN Enhancement-Mode MOSHEMTs Utilizing Hybrid Gate-Recessed Structure and Ferroelectric Charge Trapping/Storage Stacked LiNbO<sub>3</sub>/HfO<sub>2</sub>/Al<sub>2</sub>O<sub>3</sub> Structure. *Lee, H.*, +, *TED Aug. 2021 3768-3774*

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A Wearable Ultrathin Flexible Sensor Inserted Into Nasal Cavity for Precise Sleep Respiratory Monitoring. *Zhang, H.*, +, *TED Aug. 2021 4090-4097*

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A Seamless, Reconfigurable, and Highly Parallel In-Memory Stochastic Computing Approach With Resistive Random Access Memory Array. *Shen, W.*, +, *TED Jan. 2021 103-108*

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A More Hardware-Oriented Spiking Neural Network Based on Leading Memory Technology and Its Application With Reinforcement Learning. *Kim, M.*, +, *TED Sept. 2021 4411-4417*

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Epitaxial Al-InAs Heterostructures as Platform for Josephson Junction Field-Effect Transistor Logic Devices. *Wen, F.*, +, *TED April 2021 1524-1529*

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TCAD-Based Investigation of Statistical Variability Immunity in U-Channel FDSOI n-MOSFET for Sub-7-nm Technology. *Sudarsanan, A.*, +, *TED June 2021 2611-2617*

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A Bulk Full-Gate SOI-LDMOS Device With Bulk Channel and Electron Accumulation Effect. *Chen, W.*, +, *TED Dec. 2021 6286-6291*

A Compact Physical Drain Current Model of Multitube Carbon Nanotube Field Effect Transistor Including Diameter Dispersion Effects. *Zhang, Y.*, +, *TED Dec. 2021 6571-6579*

A Compact Spice Model for SiC Gate Turn-Off Thyristors With Complete Parameter Extraction Procedure. *Ma, H.*, +, *TED Dec. 2021 6296-6304*

A High RF-Performance AlGaIn/GaN HEMT With Ultrathin Barrier and Stressor *In Situ* SiN. *Wu, S.*, +, *TED Nov. 2021 5553-5558*

A Novel Device to Implement Full Set of Three-Input Logic Gates Using a Naphthalene-Based Single-Molecule Field-Effect Transistor. *Fakheri, M.T.*, +, *TED Feb. 2021 733-738*

A Novel Technique for Probing the Vertical Component of FinFET Source Resistance. *Wang, P.*, +, *TED Dec. 2021 6015-6019*

A TCAD Simulation Study of Three-Independent-Gate Field-Effect Transistors at the 10-nm Node. *Cadareanu, P.*, +, *TED Aug. 2021 4129-4135*

Advancing Monolayer 2-D nMOS and pMOS Transistor Integration From Growth to Van Der Waals Interface Engineering for Ultimate CMOS Scaling. *Dorow, C.*, +, *TED Dec. 2021 6592-6598*

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Comparative Study of Hall Effect Mobility in Inversion Layer of 4H-SiC MOSFETs With Nitrided and Phosphorus-Doped Gate Oxides. *Noguchi, M.*, +, *TED Dec. 2021 6321-6329*

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- Design and Investigation of Dielectrically Modulated Dual-Material Gate-Oxide-Stack Double-Gate TFET for Label-Free Detection of Biomolecules. *Singh, K.S.*, +, *TED Nov. 2021 5784-5791*
- Effect of Kr/O<sub>2</sub>-Plasma Reactive Sputtering on Ferroelectric Nondoped HfO<sub>2</sub> Formation for MFSFET With Pt Gate Electrode. *Ohmi, S.*, +, *TED May 2021 2427-2433*
- Effective Modulation of GaN-on-Si LED via Indigenous MOSFET Engineering. *Piao, J.*, +, *TED Nov. 2021 5640-5644*
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- Exploiting Carbon Nanotube FET and Magnetic Tunneling Junction for Near-Memory-Computing Paradigm. *Yang, N.*, +, *TED April 2021 1975-1979*
- First Experimental Demonstration of Robust HZO/ $\beta$ -Ga<sub>2</sub>O<sub>3</sub> Ferroelectric Field-Effect Transistors as Synaptic Devices for Artificial Intelligence Applications in a High-Temperature Environment. *Noh, J.*, +, *TED May 2021 2515-2521*
- First-Principles-Based Quantum Transport Simulations of Interfacial Point Defect Effects on InAs Nanowire Tunnel FETs. *Lee, H.*, +, *TED Nov. 2021 5901-5907*
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- High-Performance Amorphous InGaZnO Thin-Film Transistor Gated by HfAlO<sub>x</sub> Dielectric With Ultralow Subthreshold Swing. *Zhu, L.*, +, *TED Dec. 2021 6154-6158*
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- Impact of Random Phase Distribution in Ferroelectric Transistors-Based 3-D NAND Architecture on In-Memory Computing. *Choe, G.*, +, *TED May 2021 2543-2548*
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- The Photosensitive Mechanism of Gap-Type Amorphous Silicon TFT. *Tai, Y.*, +, *TED Dec. 2021 6177-6181*
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- Experimental Demonstration of Gate-Level Logic Camouflaging and Run-Time Reconfigurability Using Ferroelectric FET for Hardware Security. *Dutta, S.*, +, *TED Feb. 2021 516-522*
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- CMOS-Compatible Fabrication of Low-Power Ferroelectric Tunnel Junction for Neural Network Applications. *Kuo, Y.*, +, *TED Feb. 2021 879-884*
- Compact Single-Phase-Search Multistate Content-Addressable Memory Design Using One FeFET/Cell. *Rajaei, R.*, +, *TED Jan. 2021 109-117*
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- Deep Pipeline Circuit for Low-Power Spintronic Devices. *Pei, Z.*, +, *TED April 2021 1962-1968*
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- Energy-Efficient All-Spin BNN Using Voltage-Controlled Spin-Orbit Torque Device for Digit Recognition. *Shreya, S.*, +, *TED Jan. 2021 385-392*
- Exploiting Carbon Nanotube FET and Magnetic Tunneling Junction for Near-Memory-Computing Paradigm. *Yang, N.*, +, *TED April 2021 1975-1979*
- High Field Temperature-Independent Field-Effect Mobility of Amorphous Indium-Gallium-Zinc Oxide Thin-Film Transistors: Understanding the Importance of Equivalent-Oxide-Thickness Downscaling. *Han, K.*, +, *TED Jan. 2021 118-124*
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- Logic Device Based on Skyrmion Annihilation. *Song, M.*, +, *TED April 2021 1939-1943*
- Low-Voltage Thyristor Heterostructure for High-Current Pulse Generation at High Repetition Rate. *Slipchenko, S.O.*, +, *TED June 2021 2855-2860*
- Nanoelectromechanical-Switch-Based Ternary Content-Addressable Memory (NEMTCAM). *Lee, J.S.*, +, *TED Oct. 2021 4903-4909*
- Performance Improvement of 1T DRAM by Raised Source and Drain Engineering. *Ansari, M.H.R.*, +, *TED April 2021 1577-1584*
- Phase Transition Material-Assisted Low-Power SRAM Design. *Nibhanupudi, S.S.T.*, +, *TED May 2021 2281-2288*
- RADAR: A Fast and Energy-Efficient Programming Technique for Multiple Bits-Per-Cell RRAM Arrays. *Le, B.Q.*, +, *TED Sept. 2021 4397-4403*
- Radiation Hardness Study of  $L_G = 20$  nm FinFET and Nanowire SRAM Through TCAD Simulation. *Elwailly, A.*, +, *TED May 2021 2289-2294*
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- Redundancy and Analog Slicing for Precise In-Memory Machine Learning—Part II: Applications and Benchmark. *Pedretti, G.*, +, *TED Sept. 2021 4379-4383*
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- Transistor Subthreshold Swing Lowered by 2-D Heterostructures. *Wu, F.*, +, *TED Jan. 2021 411-414*
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A Noniterative Parameter-Extraction Method for Single-Diode Lumped Parameter Model of Solar Cells. *Xu, C.*, +, *TED Sept. 2021 4529-4535*

An Analytical Effective-Diode-Based Analysis of Industrial Solar Cells From Three-Diode Lumped-Parameter Model. *Xu, C.*, +, *TED June 2021 2753-2758*

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Rapid MOSFET Contact Resistance Extraction From Circuit Using SPICE-Augmented Machine Learning Without Feature Extraction. *Lu, T.*, +, *TED Dec. 2021 6026-6032*

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**Magnetic devices**

A Fokker–Planck Approach for Modeling the Stochastic Phenomena in Magnetic and Resistive Random Access Memory Devices. *Das, D.*, +, *TED Dec. 2021 6124-6131*

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- Magnetization reversal**
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Normally-OFF Diamond Reverse Blocking MESFET. *Canas, J.*, +, *TED Dec. 2021 6279-6285*

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- Fabricating In-Plane MoTe<sub>2</sub> p-n Homo Junction Photodetector Using Laser-Induced p-Type Doping. *Chen, J.*, +, *TED Sept. 2021 4485-4490*
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- Influence of Si-Substrate Concentration on Electrical Properties of Back- and Top-Gate MoS<sub>2</sub> Transistors. *Zhao, X.*, +, *TED June 2021 3087-3090*
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- An Efficient GFET Structure. *Nastasi, G.*, +, *TED Sept. 2021 4729-4734*
- Efficient Bilayer Light-Emitting Diode Based on Distyrylarylene-Containing Polymers: Numerical and DFT Simulation. *Chouk, R.*, +, *TED Feb. 2021 578-583*
- Negative-Capacitance FET With a Cold Source. *Guo, S.*, +, *TED Feb. 2021 911-918*
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- Crosstalk Suppression in Monolithic GaN Devices Based on Inverted E-Field Decoupling. *Sun, R.*, +, *TED April 2021 1542-1549*

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- 3-D Full-Band Monte Carlo Simulation of Hot-Electron Energy Distributions in Gate-All-Around Si Nanowire MOSFETs. *Reaz, M.*, +, *TED May 2021 2556-2563*
- Dielectric Passivation and Edge Effects in Planar GaN Schottky Barrier Diodes. *Orfao, B.*, +, *TED Sept. 2021 4296-4301*
- FBMC3D—A Large-Scale 3-D Monte Carlo Simulation Tool for Modern Electronic Devices. *Prigozhin, I.*, +, *TED Jan. 2021 279-287*
- Influence of Within-Die Transistor Characteristics Variation on FINFET Circuit Delay. *Pidin, S.*, *TED July 2021 3276-3282*
- Investigation of an Opposed-Contact GaAs Photoconductive Semiconductor Switch at 1-kHz Excitation. *Xu, M.*, +, *TED May 2021 2355-2359*
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- Boron-Doped Diamond MOSFETs With High Output Current and Extrinsic Transconductance. *Liu, J.*, +, *TED Aug. 2021 3963-3967*
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- Interface Optimization of Passivated Er<sub>2</sub>O<sub>3</sub>/Al<sub>2</sub>O<sub>3</sub>/InP MOS Capacitors and Modulation of Leakage Current Conduction Mechanism. *Qiao, L.*, +, *TED June 2021 2899-2905*
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- Investigation of Two Bits With Multistate Antifuse on nMOS Poly-Silicon Junctionless GAA OTP. *Chang, C.*, +, *TED Dec. 2021 6118-6123*
- Materials to Systems Co-Optimization Platform for Rapid Technology Development Targeting Future Generation CMOS Nodes. *Bazizi, E.M.*, +, *TED Nov. 2021 5358-5363*

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- Phase Transition Material-Assisted Low-Power SRAM Design. *Nibhanupudi, S.S.T.*, +, *TED May 2021 2281-2288*
- Single-Crystal Islands (SCI) for Monolithic 3-D and Back-End-of-Line FinFET Circuits. *Liu, Y.*, +, *TED Oct. 2021 5257-5262*

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- 2-D-Nonlinear Electrothermal Model for Investigating the Self-Heating Effect in GAAFET Transistors. *Belkhiria, M.*, +, *TED March 2021 954-961*
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- A Comparison of Analog Performance, Linearity, and Distortion Characteristics Between Symmetric InGaAs and Asymmetric InGaAs/InP MOSFETs. *Datta, E.*, +, *TED April 2021 1570-1576*
- A Comprehensive Gate and Drain Trapping/Detrapping Noise Model and its Implications for Thin-Dielectric MOSFETs. *Asanovski, R.*, +, *TED Oct. 2021 4826-4833*
- A Multi-epi Superjunction MOSFET With a Lightly Doped MOS-Channel Diode for Improving Reverse Recovery. *Huang, M.*, +, *TED May 2021 2401-2407*
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- A Physical Model for Bulk Gate Insulator Trap Generation During Bias-Temperature Stress in Differently Processed p-Channel FETs. *Samadder, T.*, +, *TED Feb. 2021 485-490*
- A Potential Model of Triple Macaroni Channel MOSFETs in Subthreshold Region. *Nguyen-Gia, Q.*, +, *TED Sept. 2021 4195-4200*
- A Simple Method to Create Corners for the Lookup Table-Based MOSFET Models Through Inputs and Outputs Mapping. *Xia, K.*, *TED April 2021 1432-1438*
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- Analysis of the Ultrafast Transient Heat Transport in Sub 7-nm SOI FinFETs Technology Nodes Using Phonon Hydrodynamic Equation. *Rezgui, H.*, +, *TED Jan. 2021 10-16*
- Analysis of Using Negative Capacitance FETs to Optimize Linearity Performance for Voltage Reference Generators. *Liu, H.*, +, *TED Nov. 2021 5864-5871*
- Anomalous GIDL Effect With Back Bias in FinFET: Physical Insights and Compact Modeling. *Dabhi, C.K.*, +, *TED July 2021 3261-3267*
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- Battery-Less Electronic Layer Detectors Array (ELDA) for In-Tool DUV Detection by FinFET CMOS Technology. *Wang, C.*, +, *TED Oct. 2021 4972-4976*
- Benchmarking Silicon FinFET With the Carbon Nanotube and 2D-FETs for Advanced Node CMOS Logic Application. *Das, U.K.*, +, *TED July 2021 3643-3648*
- Boron-Doped Diamond MOSFETs With High Output Current and Extrinsic Transconductance. *Liu, J.*, +, *TED Aug. 2021 3963-3967*
- Boundary Regions and Their Contribution to Current Spreading in Grounded Gate Nmos. *de Raad, G.J.*, *TED March 2021 968-975*
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- Capacitance–Voltage Technique Based on Time Varying Magnetic Field for VDMOSFET—Part I: Concept and Implementation. *Tahi, H.*, +, *TED May 2021 2173-2180*
- Capacitance–Voltage Technique Based on Time Varying Magnetic Field for VDMOSFET—Part II: Measurements and Parameter Extractions. *Tahi, H.*, +, *TED May 2021 2181-2188*
- Channel Properties of Ga<sub>2</sub>O<sub>3</sub>-on-SiC MOSFETs. *Wang, Y.*, +, *TED March 2021 1185-1189*
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- Characterization and Analysis on Performance and Avalanche Reliability of SiC MOSFETs With Varied JFET Region Width. *Zhu, Z.*, +, *TED Aug. 2021 3982-3990*
- Characterization and Modeling of Native MOSFETs Down to 4.2 K. *Zhang, Y.*, +, *TED Sept. 2021 4267-4273*
- Compact Modeling of Nonlinear Contact Effects in Short-Channel Coplanar and Staggered Organic Thin-Film Transistors. *Pruefer, J.*, +, *TED Aug. 2021 3843-3850*
- Compact Modeling of Temperature Effects in FDSOI and FinFET Devices Down to Cryogenic Temperatures. *Pahwa, G.*, +, *TED Sept. 2021 4223-4230*
- Compact Single-Phase-Search Multistate Content-Addressable Memory Design Using One FeFET/Cell. *Rajaei, R.*, +, *TED Jan. 2021 109-117*
- Comparative Study of Hall Effect Mobility in Inversion Layer of 4H-SiC MOSFETs With Nitrided and Phosphorus-Doped Gate Oxides. *Noguchi, M.*, +, *TED Dec. 2021 6321-6329*
- Defects and Passivation Mechanism of the Suboxide Layers at SiO<sub>2</sub>/4H-SiC (0001) Interface: A First-Principles Calculation. *Wang, Z.*, +, *TED Jan. 2021 288-293*
- Design and Analysis of Improved Phase-Transition FinFET Utilizing Negative Capacitance. *Yadav, S.*, +, *TED Feb. 2021 853-859*
- Detailing Influence of Contact Condition and Island Edge on Dual-Configuration Kelvin Pseudo-MOSFET Method. *Mori, D.*, +, *TED June 2021 2906-2911*
- Direct White Noise Characterization of Short-Channel MOSFETs. *Ohmori, K.*, +, *TED April 2021 1478-1482*
- Effect of Threshold Voltage Hysteresis on Switching Characteristics of Silicon Carbide MOSFETs. *Cai, Y.*, +, *TED Oct. 2021 5014-5021*
- Effective Modulation of GaN-on-Si LED via Indigenous MOSFET Engineering. *Piao, J.*, +, *TED Nov. 2021 5640-5644*
- Electrical and Reliability Characteristics of FinFETs With High-*k* Gate Stack and Plasma Treatments. *Li, Y.*, +, *TED Jan. 2021 4-9*
- Electronic Fluctuation of Graphene Nanoribbon MOSFETs Under a Full Quantum Dynamics Framework. *Lv, Y.*, +, *TED April 2021 1980-1985*
- Electrothermal Analysis of the Charge–Discharge Related Energy Loss of the Output Capacitance in OFF-State Superjunction MOSFETs. *Lin, Z.*, +, *TED Sept. 2021 4582-4586*
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- Energy Storage and Reuse in Negative Capacitance. *Kao, M.*, +, *TED April 2021 1861-1865*
- Experimental Validation of Process-Induced Variability Aware SPICE Simulation Platform for Sub-20 nm FinFET Technologies. *Rawat, A.*, +, *TED March 2021 976-980*
- Exploiting Carbon Nanotube FET and Magnetic Tunneling Junction for Near-Memory-Computing Paradigm. *Yang, N.*, +, *TED April 2021 1975-1979*
- Exploiting Fringing Fields Created by High- $\kappa$  Gate Insulators to Enhance the Performance of Ultrascaled 2-D-Material-Based Transistors. *Bennett, R.K.A.*, +, *TED Sept. 2021 4618-4624*
- Extraction of the Trench Sidewall Capacitances in an n-Type 4H-SiC Trench Metal–Oxide–Semiconductor Structure. *Guo, Z.*, +, *TED June 2021 2879-2885*
- Feedback Stabilization of a Negative-Capacitance Ferroelectric and its Application to Improve the  $f_T$  of a MOSFET. *Yuan, Z.C.*, +, *TED Oct. 2021 5101-5107*
- Gate Oxide Damage of SiC MOSFETs Induced by Heavy-Ion Strike. *Zhou, X.*, +, *TED Aug. 2021 4010-4015*
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- Impact of the Ohmic Electrode on the Endurance of Oxide-Based Resistive Switching Memory. *Wiefels, S.*, +, *IED March 2021 1024-1030*
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- Miniaturized PMMA Electrochemical Platform With Carbon Fiber for Multiplexed and Noninterfering Biosensing of Real Samples. *Mohan, J.M.*, +, *IED Feb. 2021 769-774*
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- A Novel Approach to Inactivate the Body p-i-n Diode of SiC MOSFET by Using the Normally-OFF JFET. *Li, P.*, +, *TED April 2021 1784-1790*
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- Plasma Spreading Layers: An Effective Method for Improving Surge and Avalanche Robustness of SiC Devices. *Ren, N.*, +, *TED Nov. 2021 5687-5694*
- Radiation Resistance of High-Voltage Silicon and 4H-SiC Power p-i-n Diodes. *Hazdra, P.*, +, *TED Jan. 2021 202-207*
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- A General Compact Pinned Photodiode Model Capable of Miniature PPD Modeling. *Alaibakhsh, H.*, +, *TED June 2021 2785-2790*
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- Dynamic Model of FWC Dependent on the Energy-Level Distribution of Interface-State Traps in Pinned Photodiodes. *Xia, C.*, +, *TED April 2021 1682-1687*
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- Room Temperature Operated Electrospun Nanofibers-Based SnO<sub>2</sub>/PTH Sensor for Acetone Sensing Applications. *Beniwal, A.*, +, *TED Aug. 2021 4084-4089*
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- A Novel Technique for Probing the Vertical Component of FinFET Source Resistance. *Wang, P.*, +, *TED Dec. 2021 6015-6019*
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- Novel Snapback-Free SOI LIGBT With Shorted Anode and Trench Barriers. *Sun, L.*, +, *TED May 2021 2408-2413*
- Numerical Simulation: Design of High-Efficiency Planar p-n Homojunction Perovskite Solar Cells. *Sengar, B.S.*, +, *TED May 2021 2360-2364*
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- Variability of p-n Junctions and SiGe HBTs at Cryogenic Temperatures. *Ying, H.*, +, *TED March 2021 987-993*

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- Room Temperature Hydrogen Sensor Using Schottky Contacted Zinc Oxide Thin-Film Transistor: A Comprehensive Investigation. *Ghosh, S.*, +, *TED Sept. 2021 4637-4643*
- Study of a New Hydrogen Gas Sensor Synthesized With a Sputtered Cerium Oxide Thin Film and Evaporated Palladium Nanoparticles. *Chen, K.*, +, *TED Aug. 2021 4077-4083*

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- High-Performance Thin-Film IGZO Schottky Diodes With Sputtered PdO<sub>x</sub> Anode. *Yan, S.*, +, *TED Sept. 2021 4444-4449*

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- Physics-Based Trench-Gate Field-Stop IGBT Modeling With Optimization-Based Parameter Extraction for Device Parameters. *Ding, Y.*, +, *TED Dec. 2021 6305-6312*

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- Impedance and Effective Resistance of Capacitors With Resistive Top and Bottom Plates. *Xia, K.*, +, *TED Oct. 2021 4834-4841*

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- Design of Multigap Pseudospark Discharge-Based Plasma Cathode Electron Source at Different Configurations of Electrode Apertures. *Varun, .*, +, *TED Nov. 2021 5799-5806*

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- Electron Flow Modulation in Double-Gap Cavity With a Multiple Ratio of the Two Modes Frequencies. *Muchkaev, V.Y.*, +, *TED Feb. 2021 835-840*
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- 1.26 W/mm Output Power Density at 10 GHz for Si<sub>3</sub>N<sub>4</sub> Passivated H-Terminated Diamond MOSFETs. *Yu, X.*, +, *TED Oct. 2021 5068-5072*
- 1300 V Normally-OFF p-GaN Gate HEMTs on Si With High ON-State Drain Current. *Jiang, H.*, +, *TED Feb. 2021 653-657*

- 3-D Full-Band Monte Carlo Simulation of Hot-Electron Energy Distributions in Gate-All-Around Si Nanowire MOSFETs. *Reaz, M.*, +, *TED May 2021 2556-2563*
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- Analysis of Dependence of Breakdown Voltage on Gate-Drain Distance in AlGaIn/GaN HEMTs With High-*k* Passivation Layer. *Tomita, R.*, +, *TED April 2021 1550-1556*
- Breakdown Voltage Enhancement in ScAlN/GaN High-Electron-Mobility Transistors by High-*k* Bismuth Zinc Niobate Oxide. *Cheng, J.*, +, *TED July 2021 3333-3338*
- Crosstalk Suppression in Monolithic GaN Devices Based on Inverted *E*-Field Decoupling. *Sun, R.*, +, *TED April 2021 1542-1549*
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- Determination of the Gate Breakdown Mechanisms in p-GaN Gate HEMTs by Multiple-Gate-Sweep Measurements. *Zhou, G.*, +, *TED April 2021 1518-1523*
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- Drain Field Plate Impact on the Hard-Switching Performance of AlGaIn/GaN HEMTs. *Minetto, A.*, +, *TED Oct. 2021 5003-5008*
- Effect of Sc<sub>2</sub>O<sub>3</sub> Passivation Layer on the Electrical Characteristics and Stability of InSnZnO Thin-Film Transistors. *Zhong, W.*, +, *TED Oct. 2021 4956-4961*
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- Interface Charge Effects on 2-D Electron Gas in Vertical-Scaled Ultrathin-Barrier AlGaIn/GaN Heterostructure. *Huang, S.*, +, *TED Jan. 2021 36-41*
- Interface Optimization of Passivated Er<sub>2</sub>O<sub>3</sub>/Al<sub>2</sub>O<sub>3</sub>/InP MOS Capacitors and Modulation of Leakage Current Conduction Mechanism. *Qiao, L.*, +, *TED June 2021 2899-2905*
- Interplay of Various Charge Sources in AlGaIn/GaN Epi-Stack Governing HEMT Breakdown. *Soni, A.*, +, *TED May 2021 2378-2386*
- Low-Frequency Noise Analysis of the Optimized Post High-*k* Deposition Annealing in FinFET Technology. *Deng, W.*, +, *TED March 2021 1202-1206*
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- Modeling of Semiconductor Substrates for RF Applications: Part I—Static and Dynamic Physics of Carriers and Traps. *Rack, M.*, +, *TED Sept. 2021 4598-4605*
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- Novel Surface Passivation Scheme by Using p-Type AlTiO to Mitigate Dynamic ON Resistance Behavior in AlGaIn/GaN HEMTs—Part II. *Gupta, S.D.*, +, *TED Nov. 2021 5728-5735*
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- Performance Improvement for Spray-Coated ZnO TFT by F Doping With Spray-Coated Zr-Al-O Gate Insulator. *Saha, J.K.*, +, *TED March 2021 1063-1069*
- Structural and Electrical Characteristics of ALD-TiO<sub>2</sub>/SiON/n-Si Gate-Stack for Advanced CMOS Device Applications. *Gupta, R.*, +, *TED June 2021 2625-2632*
- Study of a GaN-Based Light-Emitting Diode With a Ga<sub>2</sub>O<sub>3</sub> Current Blocking Layer and a Ga<sub>2</sub>O<sub>3</sub> Surface Passivation Layer. *Hsu, C.*, +, *TED Aug. 2021 3894-3900*
- Temperature-Dependent Current Dispersion Study in  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> FETs Using Submicrosecond Pulsed I-V Characteristics. *Vaidya, A.*, +, *TED Aug. 2021 3755-3761*
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- Ultrathin Flexible Inorganic Device for Long-Term Monitoring of Light and Temperature. *Wang, Z.*, +, *TED July 2021 3558-3561*
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- An Enhanced Thermoelectric Collaborative Cooling System With Thermoelectric Generator Serving as a Supplementary Power Source. *Wang, N.*, +, *TED April 2021 1847-1854*
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- Analytical Modeling, Design, and Performance Analysis of a Micromirror for Space-Based Multiobject Spectroscopy. *Kumar, A.*, +, *TED Nov. 2021 5773-5778*
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Impact of the Nonlinear Dielectric Hysteresis Properties of a Charge Trap Layer in a Novel Hybrid High-Speed and Low-Power Ferroelectric or Antiferroelectric HSO/HZO Boosted Charge Trap Memory. *Ali, T.*, +, *TED April 2021 2098-2106*

Interface Optimization of Passivated Er<sub>2</sub>O<sub>3</sub>/Al<sub>2</sub>O<sub>3</sub>/InP MOS Capacitors and Modulation of Leakage Current Conduction Mechanism. *Qiao, L.*, +, *TED June 2021 2899-2905*

Permittivity Characterization of Dielectric Surfaces Using Nanofabricated In-Plane Capacitors. *Mousavi Karimi, Z.*, +, *TED Aug. 2021 4033-4038*

Sensitivity Analysis and Design of Negative-Capacitance Junctionless Transistor for High-Performance Applications. *Gupta, M.*, +, *TED Aug. 2021 4136-4143*

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Simulation-Based Study of High-Permittivity Inserted-Oxide FinFET With Low-Permittivity Inner Spacers. *Wu, Y.*, +, *TED Nov. 2021 5529-5534*

Structural and Electrical Characteristics of ALD-TiO<sub>2</sub>/SiON/n-Si Gate-Stack for Advanced CMOS Device Applications. *Gupta, R.*, +, *TED June 2021 2625-2632*

The Influence of Top and Bottom Metal Electrodes on Ferroelectricity of Hafnia. *Lee, Y.*, +, *TED Feb. 2021 523-528*

Theoretical Study of Charge Carrier Lifetime and Recombination on the Performance of Eco-Friendly Perovskite Solar Cell. *Shukla, R.*, +, *TED July 2021 3446-3452*

Using Anisotropic Insulators to Engineer the Electrostatics of Conventional and Tunnel Field-Effect Transistors. *Bennett, R.K.A.*, +, *TED Feb. 2021 865-872*

#### Perpendicular magnetic anisotropy

A Fokker-Planck Approach for Modeling the Stochastic Phenomena in Magnetic and Resistive Random Access Memory Devices. *Das, D.*, +, *TED Dec. 2021 6124-6131*

Angular Harmonic Hall Voltage and Magnetoresistance Measurements of Pt/FeCoB and Pt-Ti/FeCoB Bilayers for Spin Hall Conductivity Determination. *Skowronski, W.*, +, *TED Dec. 2021 6379-6385*

First Demonstration of 25-nm Quad Interface p-MTJ Device With Low Resistance-Area Product MgO and Ten Years Retention for High Reliable STT-MRAM. *Nishioka, K.*, +, *TED June 2021 2680-2685*

On-Chip Coupled Solenoid Inductors for Integrated Power Conversion. *He, Y.*, +, *TED Dec. 2021 6292-6295*

#### PH measurement

Amorphous ZnSn<sub>x</sub>O<sub>y</sub> Fabricated at Room-Temperature for Flexible pH-EG-FET Sensor. *Singh, K.*, +, *TED Feb. 2021 793-797*

Enhanced pH Sensitivity of AlGaIn/GaN Ion-Sensitive Field-Effect Transistor by Recess Process and Ammonium Hydroxide Treatment. *He, Y.*, +, *TED March 2021 1250-1254*

#### Phase change materials

A □T<sub>j</sub> Reduced Power Module With Inbuilt Phase Change Material for Reliability Enhancement. *Jiang, H.*, +, *TED Sept. 2021 4557-4564*

A Drift-Resilient Hardware Implementation of Neural Accelerators Based on Phase Change Memory Devices. *Munoz-Martin, I.*, +, *TED Dec. 2021 6076-6081*

Capacitance Behavior With Voltage Bias in Phase-Change Memory for Fast Operation. *Chen, Z.*, +, *TED Nov. 2021 5592-5597*

Experimental Investigation of Thermal Actuation Crosstalk in Phase-Change RF Switches Using Transient Thermoreflectance Imaging. *Singh, T.*, +, *TED July 2021 3537-3544*

Fully On-Chip MAC at 14 nm Enabled by Accurate Row-Wise Programming of PCM-Based Weights and Parallel Vector-Transport in Duration-Format. *Narayanan, P.*, +, *TED Dec. 2021 6629-6636*

Indirectly Heated Switch as a Platform for Nanosecond Probing of Phase Transition Properties in Chalcogenides. *Wainstein, N.*, +, *TED March 2021 1298-1303*

- Modeling and Simulations of the Integrated Device of Phase Change Memory and Ovonic Threshold Switch Selector With a Confined Structure. *Chen, Z.*, +, *TED April 2021 1616-1621*
- PCM-Based Analog Compute-In-Memory: Impact of Device Non-Idealities on Inference Accuracy. *Sun, X.*, +, *TED Nov. 2021 5585-5591*
- Scalable mmWave Non-Volatile Phase Change GeTe-Based Compact Monolithically Integrated Wideband Digital Switched Attenuator. *Singh, T.*, +, *TED May 2021 2306-2312*
- Phase change memories**
- A Robust and Efficient Compact Model for Phase-Change Memory Circuit Simulations. *Chen, X.*, +, *TED Sept. 2021 4404-4410*
- Influence of Cu Doping in Si–Te-Based Chalcogenide Glasses and Thin Films: Electrical Switching, Morphological and Raman Studies. *Roy, D.*, +, *TED March 2021 1196-1201*
- Innovative Low-Power Self-Nanoconfined Phase-Change Memory. *Serra, A.L.*, +, *TED Feb. 2021 535-540*
- Modeling and Simulations of the Integrated Device of Phase Change Memory and Ovonic Threshold Switch Selector With a Confined Structure. *Chen, Z.*, +, *TED April 2021 1616-1621*
- Noise-Resilient DNN: Tolerating Noise in PCM-Based AI Accelerators via Noise-Aware Training. *Kariyappa, S.*, +, *TED Sept. 2021 4356-4362*
- Phase change random access memory**
- Thermoelectric Effects on Amorphization Process of Blade-Type Phase Change Random Access Memory. *Lian, X.*, +, *TED Dec. 2021 6139-6146*
- Phonon-phonon interactions**
- Applicability of Shockley–Read–Hall Theory for Interface States. *Ruch, B.*, +, *TED April 2021 2092-2097*
- Phonons**
- Analysis of the Ultrafast Transient Heat Transport in Sub 7-nm SOI FinFETs Technology Nodes Using Phonon Hydrodynamic Equation. *Rezgui, H.*, +, *TED Jan. 2021 10-16*
- Carrier Velocity in Amorphous Metal–Oxide–Semiconductor Transistors. *Wang, X.*, +, *TED Jan. 2021 125-131*
- Comparative Study of Hall Effect Mobility in Inversion Layer of 4H-SiC MOSFETs With Nitrided and Phosphorus-Doped Gate Oxides. *Noguchi, M.*, +, *TED Dec. 2021 6321-6329*
- Enhanced High-Frequency Performance of Top-Gated Graphene FETs Due to Substrate-Induced Improvements in Charge Carrier Saturation Velocity. *Asad, M.*, +, *TED Feb. 2021 899-902*
- Phosphors**
- Controlling Phosphor Particle Distribution for High-Angular-Color-Uniformity and Low-Cost LEDs Based on Thermalcapillary Flow. *Liu, J.*, +, *TED Feb. 2021 592-596*
- Enhanced Color Quality of Phosphor-Converted White Laser Diodes Through Bicolor Phosphor-in-Glass. *Wang, H.*, +, *TED Nov. 2021 5652-5655*
- Lifetime Color Consistency Analysis of Cool-White LED Luminaires for General Applications. *Padmasali, A.N.*, +, *TED Nov. 2021 5634-5639*
- Phosphor-Based InGaN/GaN White Light-Emitting Diodes With Monolithically Integrated Photodetectors. *Yin, J.*, +, *TED Jan. 2021 132-137*
- Reliable and Efficient Phosphor-in-Glass-Based Chip-Scale Packaging for High-Power White LEDs. *Zhang, X.*, +, *TED Sept. 2021 4473-4477*
- Solid-State Carbon Dots-Based White Light-Emitting Diodes With Ultra-high Color Rendering Index and Good Thermal Stability. *Yin, L.*, +, *TED Aug. 2021 3901-3906*
- Study on Convective Flow Behaviors of Phosphor Particles During Curing Process of Silicone and the Influences on the Optical Performance of White LEDs. *Ding, X.*, +, *TED June 2021 2778-2784*
- Terahertz Radiation Detection Using Glow Discharge Detectors by Electrical and Optical Modes. *Hou, L.*, +, *TED Oct. 2021 5179-5183*
- Phosphorus**
- Cladded Surface-Plasmon-Enhanced BP Photodetector Based on the Damage-Free Metal–Semiconductor Interface. *Yang, Z.*, +, *TED Jan. 2021 164-167*
- Defects and Passivation Mechanism of the Suboxide Layers at SiO<sub>2</sub>/4H-SiC (0001) Interface: A First-Principles Calculation. *Wang, Z.*, +, *TED Jan. 2021 288-293*
- Line-Edge Roughness Effects on the Electronic Properties of Armchair Black Phosphorene Nanoribbons. *Moetz, M.*, +, *TED Oct. 2021 5114-5119*
- Remarkably Stable Black Phosphorus Quantum Dots-Polyvinyl Alcohol Film as a Water Soluble Breath Sensor. *Amogh, B.S.*, +, *TED Oct. 2021 5167-5172*
- Self-Powered Multicolor Broadband Photodetector Based on GaSe/WSe<sub>2</sub>//WSe<sub>2</sub>/BP Van Der Waals Heterostructure. *Chen, J.*, +, *TED Aug. 2021 3881-3886*
- Uniformly Broadband Far-Infrared Response From the Photocarrier Tunneling of Mesa Si:P Blocked-Impurity-Band Detector. *Chen, J.*, +, *TED Feb. 2021 560-564*
- Phosphorus alloys**
- Electroless Ni–P Deposition on an Al5052 Substrate for Thermal Management Applications. *Sundararajan, M.*, +, *TED June 2021 2892-2898*
- Photoconducting materials**
- Engineering of a Blocking Layer Structure for Low-Lag Operation of the a-PbO-Based X-Ray Detector. *Grynko, O.*, +, *TED May 2021 2335-2341*
- Simulation and Experimental Validation of the Uniformity of Thermally Evaporated Amorphous Selenium Films for Large-Area Imaging and Radiation Detection Applications. *Farahmandzadeh, M.*, +, *TED Feb. 2021 626-631*
- Photoconducting switches**
- Investigation of an Opposed-Contact GaAs Photoconductive Semiconductor Switch at 1-kHz Excitation. *Xu, M.*, +, *TED May 2021 2355-2359*
- Photoconductivity**
- 16 × 4 Linear Solar-Blind UV Photoconductive Detector Array Based on β-Ga<sub>2</sub>O<sub>3</sub> Film. *Zhi, Y.*, +, *TED July 2021 3435-3438*
- Effective Leakage Current Reduction in GaN Ultraviolet Avalanche Photodiodes With an Ion-Implantation Isolation Method. *Cho, M.*, +, *TED June 2021 2759-2763*
- Enhanced Charge Extraction in Metal–Perovskite–Metal Back-Contact Solar Cell Structure Through Electrostatic Doping: A Numerical Study. *Pandey, R.*, +, *TED April 2021 1757-1763*
- Enhanced Photodetection Performance in Graphene-Assisted Tunneling Photodetector. *You, C.*, +, *TED April 2021 1702-1709*
- Enhanced Thermal Stability of Elevated-Metal Metal-Oxide Thin-Film Transistors via Low-Temperature Nitrogen Post-Annealing. *Wei, Y.*, +, *TED April 2021 1649-1653*
- Fabricating In-Plane MoTe<sub>2</sub> p-n Homo Junction Photodetector Using Laser-Induced p-Type Doping. *Chen, J.*, +, *TED Sept. 2021 4485-4490*
- Low-Voltage and High-Gain Ultraviolet Detector Based on 4H-SiC n-p-n Bipolar Phototransistor. *Guo, S.*, +, *TED May 2021 2342-2346*
- Performance Improvement of MoS<sub>2</sub> Gas Sensor at Room Temperature. *Peng, X.*, +, *TED Sept. 2021 4644-4650*
- Phosphor-Based InGaN/GaN White Light-Emitting Diodes With Monolithically Integrated Photodetectors. *Yin, J.*, +, *TED Jan. 2021 132-137*
- Silicene/MoS<sub>2</sub> Heterojunction for High-Performance Photodetector. *Kharadi, M.A.*, +, *TED Jan. 2021 138-143*
- Synergistic Modulation of Synaptic Plasticity in IGZO-Based Photoelectric Neuromorphic TFTs. *Zhu, L.*, +, *TED April 2021 1659-1663*
- Understanding the Correlation Between Temperature Dependent Performance and Trap Distribution for Nickel Oxide Based Inverted Perovskite Solar Cells. *Rana, A.*, +, *TED Aug. 2021 3907-3913*
- Uniformly Broadband Far-Infrared Response From the Photocarrier Tunneling of Mesa Si:P Blocked-Impurity-Band Detector. *Chen, J.*, +, *TED Feb. 2021 560-564*
- Yb/InSe/SiO<sub>2</sub>/Au Straddling-Type Tunneling Devices Designed As Photosensors, MOS Capacitors, and Gigahertz Bandstop Filters. *Alfhaid, L.H.K.*, +, *TED March 2021 1093-1100*
- Photodetectors**
- 16 × 4 Linear Solar-Blind UV Photoconductive Detector Array Based on β-Ga<sub>2</sub>O<sub>3</sub> Film. *Zhi, Y.*, +, *TED July 2021 3435-3438*
- A CMOS Photodetector for Direct Color Imaging. *Audet, Y.*, +, *TED March 2021 1107-1114*
- A Highly Sensitive and Robust GaN Ultraviolet Photodetector Fabricated on 150-mm Si (111) Wafer. *Pokharia, R.S.*, +, *TED June 2021 2796-2803*
- A Miniature GaN Chip for Surface Roughness Measurement. *Yin, J.*, +, *TED Oct. 2021 4977-4981*

- A Monolithic Amorphous-Selenium/CMOS Single-Photon-Counting X-Ray Detector. *El-Falou, A.*, +, *TED April 2021 1746-1752*
- Analysis of Charge Transfer Potential Barrier in Pinned Photodiode of CMOS Image Sensors. *Khan, U.*, +, *TED June 2021 2770-2777*
- Asymmetric Au Electrodes-Induced Self-Powered Organic-Inorganic Perovskite Photodetectors. *Zhao, K.*, +, *TED March 2021 1149-1154*
- Battery-Less Electronic Layer Detectors Array (ELDA) for In-Tool DUV Detection by FinFET CMOS Technology. *Wang, C.*, +, *TED Oct. 2021 4972-4976*
- Cladded Surface-Plasmon-Enhanced BP Photodetector Based on the Damage-Free Metal-Semiconductor Interface. *Yang, Z.*, +, *TED Jan. 2021 164-167*
- Corrections to "Optimized Si-Based Blocked Impurity Band Detector Under Alternative Operational Mode" [Sep 19 3891-3895]. *Zhu, H.*, +, *TED Jan. 2021 447*
- Design of Novel InP/InGaAs Photodetectors With NiO Transparent p-Region and Electrode. *Yang, D.*, +, *TED Aug. 2021 3876-3880*
- Engineering of a Blocking Layer Structure for Low-Lag Operation of the a-PbO-Based X-Ray Detector. *Grynko, O.*, +, *TED May 2021 2335-2341*
- Enhanced Photo Sensing and Lowered Power Consumption in Concentric MIS Devices by Monitoring Outer Ring Open-Circuit Voltage With Biased Inner Gate. *Huang, C.*, +, *TED July 2021 3417-3423*
- Enhanced Photodetection Performance in Graphene-Assisted Tunneling Photodetector. *You, C.*, +, *TED April 2021 1702-1709*
- Exceptional Responsivity (>6 kA/W) and Dark Current (<70 fA) Tradeoff of n-Ga<sub>2</sub>O<sub>3</sub>/p-CuO Quasi-Heterojunction-Based Deep UV Photodetector. *Kumar, A.*, +, *TED Jan. 2021 144-151*
- Fabricating In-Plane MoTe<sub>2</sub> p-n Homojunction Photodetector Using Laser-Induced p-Type Doping. *Chen, J.*, +, *TED Sept. 2021 4485-4490*
- High-Detectivity and Stable Planar MAPbI<sub>3</sub>/IDT-BT Photodetectors With Assisted MoO<sub>3</sub> Interlayer. *Zhao, K.*, +, *TED Dec. 2021 6266-6272*
- High-Performance Pentacene/ZnO UV-Visible Photodetector Using Solution Method. *Srivastava, A.*, +, *TED July 2021 3439-3445*
- High-Responsivity Solar-Blind Ultraviolet Photodetectors Based on Carbon Nanodots/Graphene Hybrids. *Fang, Y.*, +, *TED March 2021 1101-1106*
- Hysteresis Behavior and Photoresponse Enhancement in Au Nanoparticle-Decorated Ge Photodetectors. *Wang, L.*, +, *TED Nov. 2021 5623-5628*
- Low-Voltage and High-Gain Ultraviolet Detector Based on 4H-SiC n-p-n Bipolar Phototransistor. *Guo, S.*, +, *TED May 2021 2342-2346*
- Performance Improvement of MoS<sub>2</sub> Gas Sensor at Room Temperature. *Peng, X.*, +, *TED Sept. 2021 4644-4650*
- Phosphor-Based InGaN/GaN White Light-Emitting Diodes With Monolithically Integrated Photodetectors. *Yin, J.*, +, *TED Jan. 2021 132-137*
- Random Telegraph Signal in n<sup>+</sup>/p-Well CMOS Single-Photon Avalanche Diodes. *Jiang, W.*, +, *TED June 2021 2764-2769*
- Self-Powered Multicolor Broadband Photodetector Based on GaSe/WSe<sub>2</sub>//WSe<sub>2</sub>/BP Van Der Waals Heterostructure. *Chen, J.*, +, *TED Aug. 2021 3881-3886*
- Silicene/MoS<sub>2</sub> Heterojunction for High-Performance Photodetector. *Kharadi, M.A.*, +, *TED Jan. 2021 138-143*
- Staggered Pixel Layout to Reduce Area and Increase Full Well Capacity in CMOS Image Sensors. *Brunetti, A.M.*, +, *TED Feb. 2021 572-577*
- TCAD-Based Investigation of Double Gate Junctionless Transistor for UV Photodetector. *Kumari, V.*, +, *TED June 2021 2841-2847*
- Tunable Alloying Improved Wide Spectrum UV-Vis-NIR and Polarization-Sensitive Photodetector Based on Sb-S-Se Nanowires. *Yu, Y.*, +, *TED Aug. 2021 3887-3893*
- Ultrathin Flexible Inorganic Device for Long-Term Monitoring of Light and Temperature. *Wang, Z.*, +, *TED July 2021 3558-3561*
- Uniformly Broadband Far-Infrared Response From the Photocurrent Tunneling of Mesa Si:P Blocked-Impurity-Band Detector. *Chen, J.*, +, *TED Feb. 2021 560-564*
- UV Light Detection Using Resonance Frequency of Piezoelectric Quartz Crystal. *Das, S.*, +, *TED June 2021 2791-2795*
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- Photodiodes**
- Analysis of Charge Transfer Potential Barrier in Pinned Photodiode of CMOS Image Sensors. *Khan, U.*, +, *TED June 2021 2770-2777*
- CMOS Pixel Potentials Extraction Method From Test Structures Based on EKV Model. *Doyen, C.*, +, *TED June 2021 2835-2840*
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- Photoelectricity**
- Comparative Study of the Photoelectric and Thermal Performance Between Traditional and Chip-Scale Packaged White LED. *Chen, C.*, +, *TED April 2021 1710-1716*
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- Photoemission**
- Performance Improvement of MoS<sub>2</sub> Gas Sensor at Room Temperature. *Peng, X.*, +, *TED Sept. 2021 4644-4650*
- Uniformly Broadband Far-Infrared Response From the Photocurrent Tunneling of Mesa Si:P Blocked-Impurity-Band Detector. *Chen, J.*, +, *TED Feb. 2021 560-564*
- Photolithography**
- 16 × 4 Linear Solar-Blind UV Photoconductive Detector Array Based on β-Ga<sub>2</sub>O<sub>3</sub> Film. *Zhi, Y.*, +, *TED July 2021 3435-3438*
- A CRP-Space-Extended RRAM PUF With In-Cell Zero-Overhead Sali-cide-Blocked Contact. *Zhao, X.*, +, *TED July 2021 3702-3705*
- Flexible Printed Circuit Board as Novel Electrodes for Acoustofluidic Devices. *Sun, C.*, +, *TED Jan. 2021 393-398*
- Flexible Room Temperature Ammonia Gas Sensor Based on Low-Temperature Tuning of Functional Groups in Grapheme. *Sett, A.*, +, *TED July 2021 3181-3188*
- Ionic Liquid Channel Field Effect Transistor Fabricated Using Silicon Dioxide Trench. *Naorem, M.*, +, *TED Sept. 2021 4741-4747*
- Photoluminescence**
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- Enhanced Photoluminescence Intensity of Quantum Dot Films With the Sandwich Column Array Structure by Uniform Electrical Induction. *Yu, B.*, +, *TED Sept. 2021 4522-4528*
- Investigation of a Highly Sensitive Au Nanoparticle-Modified ZnO Nanorod Humidity Sensor. *Young, S.*, +, *TED Feb. 2021 775-779*
- Performance Improvement for Spray-Coated ZnO TFT by F Doping With Spray-Coated Zr-Al-O Gate Insulator. *Saha, J.K.*, +, *TED March 2021 1063-1069*
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- Thermal-Assisted UV-Photon Irradiation to Improve Crystallization and Luminescence Efficiency of ZnO. *Liu, W.*, +, *TED July 2021 3283-3289*
- Photomicrography**
- Effective Modulation of GaN-on-Si LED via Indigenous MOSFET Engineering. *Piao, J.*, +, *TED Nov. 2021 5640-5644*
- Photon counting**
- A Monolithic Amorphous-Selenium/CMOS Single-Photon-Counting X-Ray Detector. *El-Falou, A.*, +, *TED April 2021 1746-1752*
- Random Telegraph Signal in n<sup>+</sup>/p-Well CMOS Single-Photon Avalanche Diodes. *Jiang, W.*, +, *TED June 2021 2764-2769*
- Photonic band gap**
- Electrical, Optical, and Reliability Analysis of QD-Embedded Kesterite Solar Cell. *Sahoo, G.S.*, +, *TED Nov. 2021 5518-5524*
- Exploiting High-Density Earth-Abundant Kesterite Quantum Wells for Next-Generation PV Technology. *Chandrasekar, P.*, +, *TED Nov. 2021 5511-5517*



- First-Principles-Based Quantum Transport Simulations of Interfacial Point Defect Effects on InAs Nanowire Tunnel FETs. *Lee, H., +, TED Nov. 2021 5901-5907*
- Highly Reliable Electrocaloric Behaviors of Antiferroelectric Al:ZrO<sub>2</sub> Thin Films for Solid-State Cooling in Integrated Circuits. *Liu, Y., +, TED Dec. 2021 6352-6358*
- Performance Investigation of p-FETs Based on Highly Air-Stable Monolayer Pentagonal PdSe<sub>2</sub>. *Nandan, K., +, TED Dec. 2021 6551-6557*
- Selective Edge-Hydrogenated Zigzag Boron Nitride Nanoribbons for Giant Magnetoresistance and Rectifying Behavior. *Kharwar, S., +, TED Nov. 2021 5894-5900*
- Photonic crystals**
- Intelligent Forward-Wave Amplifier Design With Deep Learning and Genetic Algorithm. *Liu, K., +, TED July 2021 3568-3575*
- Photonic Crystal as a Section of Modulation and Interaction With a Virtual Cathode in Two-Section Vircator. *Badarin, A.A., +, TED Jan. 2021 336-341*
- Photonics**
- Effect of Transition Mechanism of Photon-Induced Carriers on Time Jitter of GaAs Photoconductive Semiconductor Switches. *Zhang, L., +, TED Dec. 2021 6262-6265*
- Nonlinear Carrier Dynamics in a Single Photon Avalanche Diode: Stability, Bifurcation, and Quenching Condition. *Inoue, A., +, TED Dec. 2021 6222-6227*
- Photothyristors**
- Low-Voltage Thyristor Heterostructure for High-Current Pulse Generation at High Repetition Rate. *Slipchenko, S.O., +, TED June 2021 2855-2860*
- Phototransistors**
- Low-Voltage and High-Gain Ultraviolet Detector Based on 4H-SiC n-p-n Bipolar Phototransistor. *Guo, S., +, TED May 2021 2342-2346*
- Photovoltaic cells**
- Bifacial Heterojunction Back Contact Solar Cell: 29-mW/cm<sup>2</sup> Output Power Density in Standard Albedo Condition. *Sugiura, T., +, TED Nov. 2021 5645-5651*
- Electrical, Optical, and Reliability Analysis of QD-Embedded Kesterite Solar Cell. *Sahoo, G.S., +, TED Nov. 2021 5518-5524*
- Explicit Two-Piece Quadratic Current–Voltage Characteristic Model for Solar Cells. *Correa, H.P., +, TED Dec. 2021 6273-6278*
- Exploiting High-Density Earth-Abundant Kesterite Quantum Wells for Next-Generation PV Technology. *Chandrasekar, P., +, TED Nov. 2021 5511-5517*
- Modeling of Photovoltaic Solar Cell Based on CuSbS<sub>2</sub> Absorber for the Enhancement of Performance. *Sadanand, ., +, TED March 2021 1121-1128*
- The Maximum Efficiency and Parametric Optimum Selection of a Solar-Driven Thermionic-Photovoltaic Integrated Device. *Xiao, J., +, TED Feb. 2021 632-637*
- Photovoltaic effects**
- Understanding the Correlation Between Temperature Dependent Performance and Trap Distribution for Nickel Oxide Based Inverted Perovskite Solar Cells. *Rana, A., +, TED Aug. 2021 3907-3913*
- Physics**
- Design and Analysis of an Overmoded Circuit for Two-Beam Sub-THz Extended Interaction Oscillator. *Bi, L., +, TED Nov. 2021 5807-5813*
- TCAD-Augmented Machine Learning With and Without Domain Expertise. *Dhillon, H., +, TED Nov. 2021 5498-5503*
- Piezoelectric actuators**
- Flexible Printed Circuit Board as Novel Electrodes for Acoustofluidic Devices. *Sun, C., +, TED Jan. 2021 393-398*
- Piezoelectric materials**
- UV Light Detection Using Resonance Frequency of Piezoelectric Quartz Crystal. *Das, S., +, TED June 2021 2791-2795*
- Piezoelectric semiconductors**
- Fabrication and Characterization of Flexible AlGaIn/GaN HEMTs on Kapton Tape. *Hsu, K., +, TED July 2021 3320-3324*
- Piezoelectric transducers**
- Design and Performance of ScAlN/AlN Trapezoidal Cantilever-Based MEMS Piezoelectric Energy Harvesters. *Liu, Y., +, TED June 2021 2971-2976*
- Piezoelectricity**
- Size-Dependent Magnetization Switching in Magnetoelectric Heterostructures for Self-Biased MRAM Applications. *Pathak, P., +, TED Sept. 2021 4418-4424*
- Piezoresistance**
- Piezoresistive Characteristics of MOSFET Channels Determined With Indentation. *Schlipf, S., +, TED April 2021 1483-1488*
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- Piezoresistive devices**
- Piezoresistive Electronic-Skin Sensors Produced With Self-Channeling Laser Microstructured Silicon Molds. *Su, Y., +, TED Feb. 2021 786-792*
- Pins**
- Investigation and Suppression of Holding Voltage Deterioration in Multifinger SCR for Robust High-Voltage ESD Engineering. *Du, F., +, TED Dec. 2021 6338-6343*
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- An Easy-to-Fabricate Circular TE<sub>21</sub>/TE<sub>01</sub> Mode Generator. *Ren, J., +, TED Dec. 2021 6532-6537*
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- Ferroelectric Hafnium Zirconium Oxide Compatible With Back-End-of-Line Process. *Hur, J., +, TED July 2021 3176-3180*
- Implementation of RTCVD-SiN<sub>x</sub> Gate Dielectric Into Enhancement-Mode GaN MIS-HEMTs Fabricated on Ultrathin-Barrier AlGaIn/GaN-on-Si Platform. *Shi, W., +, TED Sept. 2021 4274-4277*
- Low-Temperature Self-Aligned-Silicide-Capable Transistor Process Using Solid-Phase-Epitaxy and Lift-Off for Hybrid Substrates. *Tarighat, R.S., +, TED Jan. 2021 244-250*
- Plasma CVD coatings**
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- Plasma density**
- Experiment for Evaluating a K-Band Space TWT Electron Beam. *Wei, Y., +, TED July 2021 3596-3603*
- Plasma deposition**
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Ultrashort Pulse Detection and Response Time Analysis Using Plasma-Wave Terahertz Field-Effect Transistors. *Zhang, Y.*, +, *TED Feb. 2021 903-910*

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- Thin Film Magnetic Core Microinductor With Stacked Windings. *Feeney, C.*, +, *TED Sept. 2021 4237-4241*
- Power integrated circuits**
- A  $\square T$  Reduced Power Module With Inbuilt Phase Change Material for Reliability Enhancement. *Jiang, H.*, +, *TED Sept. 2021 4557-4564*
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- Enhanced Color Quality of Phosphor-Converted White Laser Diodes Through Bicolor Phosphor-in-Glass. *Wang, H.*, +, *TED Nov. 2021 5652-5655*
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- A Novel 3-D Equivalent Circuit Model of Thermoelectric MEMS Microwave Power Sensors. *Wang, D.*, +, *TED June 2021 2931-2937*
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Influence of High-Pressure Annealing Conditions on Ferroelectric and Interfacial Properties of Zr-Rich Hf<sub>x</sub>Zr<sub>1-x</sub>O<sub>2</sub> Capacitors. *Das, D.*, +, *TED April 2021 1996-2002*

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Improved Correlated Multiple Sampling by Using Interleaved Pixel Source Follower for High-Resolution and High-Framerate CMOS Image Sensor. *Tomioka, K.*, +, *TED May 2021 2326-2334*

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Noise-Resilient DNN: Tolerating Noise in PCM-Based AI Accelerators via Noise-Aware Training. *Kariyappa, S.*, +, *TED Sept. 2021 4356-4362*

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- Impact of Nonuniform Ozone Anneal Treatment on the Resistance Levels in an IGZO-ReRAM Fabricated on ITO-Coated Glass Substrate. *Kishore, R.*, +, *TED Dec. 2021 6087-6093*
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- 3-D Vertical via Nitrogen-Doped Aluminum Oxide Resistive Random-Access Memory. *Lien, Y.*, +, *TED June 2021 2712-2716*
- A 4T2R RRAM Bit Cell for Highly Parallel Ternary Content Addressable Memory. *Wang, X.*, +, *TED Oct. 2021 4933-4937*
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- A Seamless, Reconfigurable, and Highly Parallel In-Memory Stochastic Computing Approach With Resistive Random Access Memory Array. *Shen, W.*, +, *TED Jan. 2021 103-108*
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Development of Laser-Induced Graphene-Based Automated Electro Microfluidic Viscometer for Biochemical Sensing Applications. *Wagh, M.D.*, +, *TED Oct. 2021 5184-5191*

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Compact Relativistic Magnetron With Omnidirectional Radiation Through a Slotted Waveguide Array Antenna. *He, C.*, +, *TED April 2021 1912-1917*

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Characteristics of Stacked Gate-All-Around Si Nanosheet MOSFETs With Metal Sidewall Source/Drain and Their Impacts on CMOS Circuit Properties. *Sung, W.*, +, *TED June 2021 3124-3128*

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Fabrication of an Electrostatic Actuated Dielectric Mirror With Free-Standing Layers of Polymer. *Vergara, P.*, +, *TED Dec. 2021 6240-6248*

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Improved Model for Beam-Wave Interaction With Ohmic Losses and Reflections of Sheet Beam Traveling Wave Tubes. *Tian, H.*, +, *TED June 2021 2977-2983*

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A Novel Coplanar Slow-Wave Structure for Millimeter-Wave BWO Applications. *Zhao, C.*, +, *TED April 2021 1924-1929*

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- Experimental Validation of Process-Induced Variability Aware SPICE Simulation Platform for Sub-20 nm FinFET Technologies. *Rawat, A.*, +, *TED March 2021 976-980*
- Exploiting Fringing Fields Created by High- $\kappa$  Gate Insulators to Enhance the Performance of Ultrascaled 2-D-Material-Based Transistors. *Bennett, R.K.A.*, +, *TED Sept. 2021 4618-4624*
- Extraction of Compact Static Thermal Model Parameters for SiGe HBTs. *Huszka, Z.*, +, *TED Feb. 2021 491-496*
- Finger Gate Vacuum Channel Field Emission Transistors: Performance and Sensitivity Analysis. *Khoskbijari, F.K.*, +, *TED Oct. 2021 5250-5256*
- Flexible High-Temperature Polycrystalline Silicon Thin Film Transistor on Metal Foil With S/D Doped by Diffusion. *Yu, B.*, +, *TED Aug. 2021 3857-3862*
- Gate Current Partitioning Model for Schottky Gate GaN HEMTs. *Debnath, A.*, +, *TED Jan. 2021 425-429*
- Gate Oxide Damage of SiC MOSFETs Induced by Heavy-Ion Strike. *Zhou, X.*, +, *TED Aug. 2021 4010-4015*
- Gate Voltage-Dependence of Junction Capacitance in MOSFETs. *Kuk, J.*, +, *TED Oct. 2021 5315-5318*
- High Band-to-Band Tunneling Current in InAs/GaSb Heterojunction Esaki Diodes by the Enhancement of Electric Fields Close to the Mesa Sidewalls. *Hou, W.*, +, *TED Aug. 2021 3748-3754*
- Hybrid Design Using Metal–Oxide–Semiconductor Field-Effect Transistors and Negative-Capacitance Field-Effect Transistors for Analog Circuit Applications. *Han, K.*, +, *TED Feb. 2021 846-852*
- Hybrid Electrothermal Simulations of GaN HEMT Devices Based on Self-Heating Free Virtual Electrical Characteristics. *Valletta, A.*, +, *TED Aug. 2021 3740-3747*
- Identification of Electrically Stressed Regions in AlGaIn/GaN-on-Si Schottky Barrier Diode Using EBIC Technique. *Priesol, J.*, +, *TED Jan. 2021 216-221*
- Impact of Charge Trapping and Depolarization on Data Retention Using Simultaneous  $P-V$  and  $I-V$  in HfO<sub>2</sub>-Based Ferroelectric FET. *Higashi, Y.*, +, *TED Sept. 2021 4391-4396*
- Impact of Self-Heating on Negative-Capacitance FinFET: Device-Circuit Interaction. *Prakash, O.*, +, *TED April 2021 1420-1424*
- Impedance and Effective Resistance of Capacitors With Resistive Top and Bottom Plates. *Xia, K.*, +, *TED Oct. 2021 4834-4841*
- Implementing a Ternary Inverter Using Dual-Pocket Tunnel Field-Effect Transistors. *Gupta, A.*, +, *TED Oct. 2021 5305-5310*
- Improved Compact Modeling of SiGe HBT Linearity With MEXTRAM. *Zhang, H.*, +, *TED June 2021 2597-2603*
- Improved Mobility Extraction Methodology for Reconfigurable Transistors Considering Resistive Components and Effective Drain Bias. *Mane, S.*, +, *TED Sept. 2021 4797-4800*
- Improved Model on Buried-Oxide Damage Induced by Total-Ionizing-Dose Effect for HV SOI LDMOS. *Yuan, Z.*, +, *TED April 2021 2064-2070*
- Improved Retention Characteristics of Z<sup>2</sup>-FET Employing Half Back-Gate Control. *Kwon, S.*, +, *TED March 2021 1041-1044*
- Improvement of Breakdown Voltage and ON-Resistance in Normally-OFF AlGaIn/GaN HEMTs Using Etching-Free p-GaN Stripe Array Gate. *Wei, X.*, +, *TED Oct. 2021 5041-5047*
- Improvement of the Self-Heating Performance of an Advanced SiGe HBT Transistor Through the Peltier Effect. *Boulgheb, A.*, +, *TED Feb. 2021 479-484*

- InAlN/GaN HEMT on Si With  $f_{\max} = 270$  GHz. Cui, P., +, *TED March 2021 994-999*
- Influence of Carbon on pBTI Degradation in GaN-on-Si E-Mode MOS-HEMT. Viey, A.G., +, *TED April 2021 2017-2024*
- Influence of Process Variations on the Electrical Performance of SiC Power MOSFETs. Muting, J., +, *TED Jan. 2021 230-235*
- Influence of Within-Die Transistor Characteristics Variation on FINFET Circuit Delay. Pidin, S., *TED July 2021 3276-3282*
- Input-Referred Low-Frequency Noise Analysis for Single-Layer Graphene FETs. Mavredakis, N., +, *TED Sept. 2021 4762-4765*
- Interface States Characterization of UTB SOI MOSFETs From the Sub-threshold Current. Vermeer, M.L., +, *TED Feb. 2021 497-502*
- Internal Thermoelectric Cooling in Nanosheet Gate-All-Around FETs Using Schottky Drain Contacts. Kang, M.J., +, *TED Aug. 2021 4156-4160*
- Interplay Between Surface and Buffer Traps in Governing Breakdown Characteristics of AlGaIn/GaN HEMTs—Part II. Joshi, V., +, *TED Jan. 2021 80-87*
- Intrinsic Mechanism of Mobility Collapse in Short MOSFETs. Cristoloveanu, S., +, *TED Oct. 2021 5090-5094*
- Investigation of the Impact of Hot-Carrier-Induced Interface State Generation on Carrier Mobility in nMOSFET. Wu, Z., +, *TED July 2021 3246-3253*
- Investigation of Trap-Induced Performance Degradation and Restriction on Higher Ferroelectric Thickness in Negative Capacitance FDSOI FET. Garg, C., +, *TED Oct. 2021 5298-5304*
- Investigation on Single Pulse Avalanche Failure of 1200-V SiC MOSFETs via Optimized Thermoelectric Simulation. Bai, Z., +, *TED March 2021 1168-1175*
- Investigations on the Negative Shift of the Threshold Voltage of Polycrystalline Silicon Thin-Film Transistors Under Positive Gate Bias Stress. Liang, N., +, *TED Feb. 2021 550-555*
- Junctionless Multiple-Gate (JLMG) MOSFETs: A Unified Subthreshold Current Model to Assess Noise Margin of Subthreshold Logic Gate. Chiang, T., *TED Oct. 2021 5330-5334*
- L-Shaped Tunnel Field-Effect Transistor-Based 1T DRAM With Improved Read Current Ratio, Retention Time, and Sense Margin. Kamal, N., +, *TED June 2021 2705-2711*
- Layout-Induced Strain Study for RF Performance Improvement of 22-nm UTBB FDSOI PFET. Sloyan, K., +, *TED July 2021 3230-3237*
- LCE and PAMDLE Effects From Diamond Layout for MOSFETs at High-Temperature Ranges. Salerno Galembeck, E.H., +, *TED Aug. 2021 3914-3922*
- Localizing Hot-Carrier Degradation in Silicon Trench MOSFETs. Ruch, B., +, *TED April 2021 1804-1809*
- Low ON-Resistance ( $2.5 \text{ m}\Omega \cdot \text{cm}^2$ ) Vertical-Type 2-D Hole Gas Diamond MOSFETs With Trench Gate Structure. Tsunoda, J., +, *TED July 2021 3490-3496*
- Low Switching Loss and EMI Noise IGBT With Self-Adaptive Hole-Extracting Path. Wei, J., +, *TED May 2021 2572-2576*
- Mobility Degradation and Series Resistance in Graphene Field-Effect Transistors. Jeppson, K., +, *TED June 2021 3091-3095*
- Model of Electron Population and Energy Band Diagram of Multiple-Channel GaN Heterostructures. Chen, X., +, *TED April 2021 1557-1562*
- Modeling and Analysis of 3-D Core-Shell Superjunction Structures. Saxena, T., +, *TED Feb. 2021 658-665*
- Modeling and Analysis of High- $Q$  Resonant-Fin Transistors. Hager, E., +, *TED Sept. 2021 4780-4786*
- Modeling of Bias-Dependent Effective Velocity and Its Impact on Saturation Transconductance in AlGaIn/GaN HEMTs. Pampori, A.U.H., +, *TED July 2021 3302-3307*
- Modeling of Repeated FET Hot-Carrier Stress and Anneal Cycles Using Si-H Bond Dissociation/Passivation Energy Distributions. Vandemaele, M., +, *TED April 2021 1454-1460*
- Modeling of Semiconductor Substrates for RF Applications: Part I—Static and Dynamic Physics of Carriers and Traps. Rack, M., +, *TED Sept. 2021 4598-4605*
- Modeling of Semiconductor Substrates for RF Applications: Part II—Parameter Impact on Harmonic Distortion. Rack, M., +, *TED Sept. 2021 4606-4613*
- Modeling Peak Temperature in SOI-FinFET-Like Structures Considering 2-D Heat Flow. Nidhin, K., +, *TED March 2021 981-986*
- Negative-Capacitance FET With a Cold Source. Guo, S., +, *TED Feb. 2021 911-918*
- Nonlinear Thermal Analysis of AlGaIn/GaN HEMTs With Temperature-Dependent Parameters. Tang, M., +, *TED Sept. 2021 4565-4570*
- Novel Physics-Based Small-Signal Modeling and Characterization for Advanced RF Bulk FinFETs. Zhang, W., +, *TED May 2021 2160-2166*
- Novel SOI LDMOS Without RESURF Effect by Flexible Substrate for Flexible Electronic Systems. Duan, B., +, *TED Aug. 2021 4150-4155*
- Novel Vertical Power MOSFET With Step Hk Insulator Close to Super Junction Limit Relationship Between Breakdown Voltage and Specific ON-Resistance by Improving Electric Field Modulation. Duan, B., +, *TED Oct. 2021 5048-5054*
- Numerical Study of Novel GaN HEMTs With Integrated SBDs for Ultrahigh Reverse Conduction Capability. Li, S., +, *TED Feb. 2021 931-933*
- On the Explicit Saturation Drain Current in the Generalized EKV Compact MOSFET Model. Garcia-Sanchez, F.J., +, *TED Oct. 2021 4813-4818*
- On the Operation Modes of Dual-Gate Reconfigurable Nanowire Transistors. Sun, B., +, *TED July 2021 3684-3689*
- On the Physical Meaning of Single-Value Activation Energies for BTI in Si and SiC MOSFET Devices. Feil, M.W., +, *TED Jan. 2021 236-243*
- Optimization of 1700-V 4H-SiC Superjunction Schottky Rectifiers With Implanted P-Pillars for Practical Realization. Baker, G.W.C., +, *TED July 2021 3497-3504*
- Parasitic Capacitance Modeling of Si-Bulk FinFET-Based pMOS. Jing, Y., +, *TED Oct. 2021 4819-4825*
- Partial Recovery of Dynamic  $R_{\text{ON}}$  Versus OFF-State Stress Voltage in p-GaN Gate AlGaIn/GaN Power HEMTs. Cioni, M., +, *TED Oct. 2021 4862-4868*
- Performance Enhancement of 2.3 kV 4H-SiC Planar-Gate MOSFETs Using Reduced Gate Oxide Thickness. Agarwal, A., +, *TED Oct. 2021 5029-5033*
- Performance Optimization of Monolayer 1T/1T'-2H MoX<sub>2</sub> Lateral Heterojunction Transistors. Yin, D., +, *TED July 2021 3649-3657*
- Physical Modeling of Charge Trapping in 4H-SiC DMOSFET Technologies. Schleich, C., +, *TED Aug. 2021 4016-4021*
- Quasisaturation Effect and Optimization for 4H-SiC Trench MOSFET With P+ Shielding Region. Fu, H., +, *TED Sept. 2021 4550-4556*
- Recessed Anode AlGaIn/GaN Schottky Barrier Diode for Temperature Sensor Application. Pu, T., +, *TED Oct. 2021 5162-5166*
- Recovery Behavior of Interface Traps After Negative Bias Temperature Instability Stress in p-FinFETs Featuring Fast Trap Characterization Technique. Zhou, L., +, *TED Sept. 2021 4251-4258*
- Room-Temperature Negative Differential Resistance in Amorphous Carbon: The Role of Electron Trapping Defects at Device Interfaces. Le, P.Y., +, *TED Feb. 2021 720-725*
- S-Curve Engineering for ON-State Performance Using Anti-Ferroelectric/Ferroelectric Stack Negative-Capacitance FinFET. Huang, S., +, *TED Sept. 2021 4787-4792*
- Self-Consistent Modeling of B or N Substitution Doped Bottom Gated Graphene FET With Nonzero Bandgap. Chandrasekar, L., +, *TED July 2021 3658-3664*
- Sensitivity Analysis of a Novel Negative Capacitance FinFET for Label-Free Biosensing. Dixit, A., +, *TED Oct. 2021 5204-5210*
- Simulation Study of a High Gate-to-Source ESD Robustness Power p-GaN HEMT With Self-Triggered Discharging Channel. Xin, Y., +, *TED Sept. 2021 4536-4542*
- Simulation Study of Novel Trench Gate U-Shaped Channel SOI Lateral IGBTs With Suppressed Gate Voltage Overshoot and Reduced  $di/dt$ . Ma, J., +, *TED Aug. 2021 3930-3935*
- Simulation Study of Single-Event Burnout in 1.5-kV 4H-SiC JTE Termination. Yu, C., +, *TED July 2021 3711-3715*
- Simulation Study of the Instability Induced by the Variation of Grain Boundary Width and Trap Density in Gate-All-Around Polysilicon Transistor. Lin, P., +, *TED April 2021 1969-1974*

- Simulation Study on Single-Event Burnout in Rated 1.2-kV 4H-SiC Super-Junction VDMOS. *Yu, C.*, +, *TED Oct. 2021 5034-5040*
- Single-Mask Implantation-Free Technique Based on Aperture Density Modulation for Termination in High-Voltage SiC Thyristors. *Long, H.*, +, *TED March 2021 1181-1184*
- Stackable InGaAs-on-Insulator HEMTs for Monolithic 3-D Integration. *Jeong, J.*, +, *TED May 2021 2205-2211*
- Study on the Roles of Charge Trapping and Fixed Charge on Subthreshold Characteristics of FeFETs. *Jin, C.*, +, *TED March 2021 1304-1312*
- Substrate Bias Enhanced Trap Effects on Time-Dependent Dielectric Breakdown of GaN MIS-HEMTs. *Yang, W.*, +, *TED May 2021 2233-2239*
- Super Single Pulse Charge Pumping Technique for Profiling Interfacial Defects. *Chen, Y.*, +, *TED Feb. 2021 726-732*
- Surface-Potential-Based Analytical Model of Low-Frequency Noise for Planar-Type Tunnel Field-Effect Transistors. *Park, Y.*, +, *TED Aug. 2021 4051-4056*
- Switching Performance Analysis of 3.5 kV Ga<sub>2</sub>O<sub>3</sub> Power FinFETs. *Jian, Z.A.*, +, *TED Feb. 2021 672-678*
- Switching Stability Analysis of Paralleled RC-IGBTs With Snapback Effect. *Diaz Reigosa, P.*, +, *TED July 2021 3429-3434*
- TCAD-Based Investigation of Double Gate Junctionless Transistor for UV Photodetector. *Kumari, V.*, +, *TED June 2021 2841-2847*
- Temperature-Dependent Low-Frequency Noise Analysis of ZnO Nanowire Field-Effect Transistors. *Xue, H.*, +, *TED July 2021 3532-3536*
- The Critical Role of Charge Balance on the Memory Characteristics of Ferroelectric Field-Effect Transistors. *Si, M.*, +, *TED Oct. 2021 5108-5113*
- Theoretical Study of Negative Capacitance FinFET With Quasi-Antiferroelectric Material. *Zhang, F.*, +, *TED June 2021 3074-3079*
- Thermal Design Rules of AlGaIn/GaN-Based Microwave Transistors on Diamond. *Gerrer, T.*, +, *TED April 2021 1530-1536*
- Thickness-Dependent Study of High-Performance WS<sub>2</sub>-FETs With Ultrascaled Channel Lengths. *Pang, C.*, +, *TED April 2021 2123-2129*
- Time-Dependent Random Threshold Voltage Variation Due to Random Telegraph Noise. *Wirth, G.*, *TED Jan. 2021 17-23*
- Toward Automated Defect Extraction From Bias Temperature Instability Measurements. *Waldhoer, D.*, +, *TED Aug. 2021 4057-4063*
- Transistor Compact Model Based on Multigradient Neural Network and Its Application in SPICE Circuit Simulations for Gate-All-Around Si Cold Source FETs. *Yang, Q.*, +, *TED Sept. 2021 4181-4188*
- Transistor Subthreshold Swing Lowered by 2-D Heterostructures. *Wu, F.*, +, *TED Jan. 2021 411-414*
- Tri-Gate GaN Junction HEMTs: Physics and Performance Space. *Ma, Y.*, +, *TED Oct. 2021 4854-4861*
- Tunneling Junction as Cold Source: Toward Steep-Slope Field-Effect Transistors Based on Monolayer MoS<sub>2</sub>. *Wang, Q.*, +, *TED Sept. 2021 4758-4761*
- Ultrashort Pulse Detection and Response Time Analysis Using Plasma-Wave Terahertz Field-Effect Transistors. *Zhang, Y.*, +, *TED Feb. 2021 903-910*
- Unipolar Quantum Well InGaAs/AlGaAs Heterostructures With Impact Ionization for Efficient Low-Voltage Light-Emitting Devices. *Slipchenko, S.O.*, +, *TED June 2021 2823-2828*
- Using Anisotropic Insulators to Engineer the Electrostatics of Conventional and Tunnel Field-Effect Transistors. *Bennett, R.K.A.*, +, *TED Feb. 2021 865-872*
- Vertical Electric Field-Induced Abnormal Capacitance-Voltage Electrical Characteristics in a-InGaZnO TFTs. *Kuo, C.*, +, *TED Sept. 2021 4431-4436*
- Vertical Sandwich GAA FETs With Self-Aligned High-*k* Metal Gate Made by Quasi Atomic Layer Etching Process. *Zhang, Y.*, +, *TED June 2021 2604-2610*
- Semiconductor device noise**
- A Compact Current- and Voltage-Mode Model of Antenna-Coupled FET Terahertz Detectors. *Perenzoni, M.*, +, *TED Feb. 2021 471-478*
- A Comprehensive Gate and Drain Trapping/De trapping Noise Model and its Implications for Thin-Dielectric MOSFETs. *Asanovski, R.*, +, *TED Oct. 2021 4826-4833*
- A New Method to Measure the Parasitic Parameter Model of IGBT on Bias Voltage. *Wang, J.*, +, *TED May 2021 2387-2394*
- Analog Figures of Merit of Vertically Stacked Silicon Nanosheets nMOS-FETs With Two Different Metal Gates for the Sub-7 nm Technology Node Operating at High Temperatures. *Silva, V.C.P.*, +, *TED July 2021 3630-3635*
- Carrier Stored Layer Density Effect Analysis of Radiated Noise at Turn-On Switching via Gabor Wavelet Transform. *Tadakuma, T.*, +, *TED April 2021 1827-1834*
- Degradation Behavior and Defect Analysis for SiC Power MOSFETs Based on Low-Frequency Noise Under Repetitive Power-Cycling Stress. *Yang, X.*, +, *TED Feb. 2021 666-671*
- Degradation Behavior and Trap Analysis Based on Low-Frequency Noise of AlGaIn/GaN HEMTs Subjected to Radio Frequency Overdrive Stress. *Chen, Q.*, +, *TED Jan. 2021 66-71*
- Dielectric-Modulated Bulk-Planar Junctionless Field-Effect Transistor for Biosensing Applications. *Singh, D.*, +, *TED July 2021 3545-3551*
- Direct White Noise Characterization of Short-Channel MOSFETs. *Ohmori, K.*, +, *TED April 2021 1478-1482*
- Finger Gate Vacuum Channel Field Emission Transistors: Performance and Sensitivity Analysis. *Khoshkijari, F.K.*, +, *TED Oct. 2021 5250-5256*
- Identification of Channel Hot Carrier Stress-Induced Oxide Traps Leading to Random Telegraph Signals in pMOSFETs. *Ahmed, T.*, +, *TED Feb. 2021 713-719*
- Input-Referred Low-Frequency Noise Analysis for Single-Layer Graphene FETs. *Mavredakis, N.*, +, *TED Sept. 2021 4762-4765*
- Interfacial Properties of nMOSFETs With Different Al<sub>2</sub>O<sub>3</sub> Capping Layer Thickness and TiN Gate Stacks. *Wang, D.*, +, *TED March 2021 948-953*
- Junctionless Multiple-Gate (JLMG) MOSFETs: A Unified Subthreshold Current Model to Assess Noise Margin of Subthreshold Logic Gate. *Chiang, T.*, *TED Oct. 2021 5330-5334*
- Low Switching Loss and EMI Noise IGBT With Self-Adaptive Hole-Extracting Path. *Wei, J.*, +, *TED May 2021 2572-2576*
- Noise Analysis of the Leakage Current in Time-Dependent Dielectric Breakdown in a GaN SLCFET. *Dalcanale, S.*, +, *TED May 2021 2220-2225*
- On Noise Performance of Dual-Gated Silicon FET Biosensors With Schottky Contacts. *Gao, W.*, +, *TED June 2021 2965-2970*
- Quadruple Gate-Recessed AlGaIn/GaN Fin-Nanochannel Array Metal-Oxide-Semiconductor High-Electron Mobility Transistors. *Lee, H.*, +, *TED Jan. 2021 42-48*
- Random Telegraph Signal in n<sup>+</sup>/p-Well CMOS Single-Photon Avalanche Diodes. *Jiang, W.*, +, *TED June 2021 2764-2769*
- Surface-Potential-Based Analytical Model of Low-Frequency Noise for Planar-Type Tunnel Field-Effect Transistors. *Park, Y.*, +, *TED Aug. 2021 4051-4056*
- Temperature-Dependent Low-Frequency Noise Analysis of ZnO Nanowire Field-Effect Transistors. *Xue, H.*, +, *TED July 2021 3532-3536*
- Thermal Design Rules of AlGaIn/GaN-Based Microwave Transistors on Diamond. *Gerrer, T.*, +, *TED April 2021 1530-1536*
- Time-Dependent Hot Carrier Degradation in Polysilicon Emitter Bipolar Transistors Under High Current and Radiation Combined Stress. *Zhang, P.*, +, *TED Sept. 2021 4208-4213*
- Time-Dependent Random Threshold Voltage Variation Due to Random Telegraph Noise. *Wirth, G.*, *TED Jan. 2021 17-23*
- Semiconductor device packaging**
- Partial Recovery of Dynamic R<sub>ON</sub> Versus OFF-State Stress Voltage in p-GaN Gate AlGaIn/GaN Power HEMTs. *Cioni, M.*, +, *TED Oct. 2021 4862-4868*
- Semiconductor device reliability**
- In-Situ* Investigation of the Gate Bias Instability of Tungsten-Doped Indium Zinc Oxide Thin Film Transistor by Simultaneous Ultraviolet and Thermal Treatment. *Kim, M.J.*, +, *TED Aug. 2021 3851-3856*
- A High-Efficiency IGBT Health Status Assessment Method Based on Data Driven. *Zhang, Z.*, +, *TED Jan. 2021 168-174*
- A Novel 4H-SiC Trench MOSFET Integrated With Mesa-Sidewall SBD. *Han, Z.*, +, *TED Jan. 2021 192-196*

- A Physical Model for Bulk Gate Insulator Trap Generation During Bias-Temperature Stress in Differently Processed p-Channel FETs. *Samadder, T.*, +, *TED Feb. 2021 485-490*
- A Physically Based Compact Model for IGZO Transistors. *Rios, R.*, +, *TED April 2021 1664-1669*
- A Review of Low Temperature Process Modules Leading Up to the First ( $\leq 500$  °C) Planar FDSOI CMOS Devices for 3-D Sequential Integration. *Fenouillet-Beranger, C.*, +, *TED July 2021 3142-3148*
- A Study of the Gate-Stack Small-Signal Model and Determination of Interface Traps in GaN-Based MIS-HEMTs. *Huang, Z.*, +, *TED April 2021 1507-1512*
- A Unified Degradation Model of Elevated-Metal Metal Oxide (EMMO) TFTs Under Positive Gate Bias With or Without an Illumination. *Zhang, Y.*, +, *TED March 2021 1081-1087*
- Analytical Model and Optimization for SiC Floating Island Structure. *Wang, C.*, +, *TED Jan. 2021 222-229*
- Anomalous Behavior of Gate Current and TDDDB Lifetime by Constant Voltage Stress in NO-Annealed SiC-MOSFETs. *Murakami, E.*, +, *TED March 2021 1207-1213*
- Carrier Stored Layer Density Effect Analysis of Radiated Noise at Turn-On Switching via Gabor Wavelet Transform. *Tadakuma, T.*, +, *TED April 2021 1827-1834*
- Characterization and Analysis on Performance and Avalanche Reliability of SiC MOSFETs With Varied JFET Region Width. *Zhu, Z.*, +, *TED Aug. 2021 3982-3990*
- CMOS Pixel Potentials Extraction Method From Test Structures Based on EKV Model. *Doyen, C.*, +, *TED June 2021 2835-2840*
- Compact Reliability Model of Analog RRAM for Computation-in-Memory Device-to-System Codesign and Benchmark. *Liu, Y.*, +, *TED June 2021 2686-2692*
- Degradation and Failure of Flexible Low-Temperature Poly-Si TFTs Under Dynamic Stretch Stress. *Yin, X.*, +, *TED Sept. 2021 4455-4461*
- Degradation Behavior of Etch-Stopper-Layer Structured a-InGaZnO Thin-Film Transistors Under Hot-Carrier Stress and Illumination. *Lin, D.*, +, *TED Feb. 2021 556-559*
- Design of a Fan-Out Panel-Level SiC MOSFET Power Module Using Ant Colony Optimization-Back Propagation Neural Network. *Qian, Y.*, +, *TED July 2021 3460-3467*
- Effect of Bandgap Widening on Negative-Bias Illumination Stress Stability of Oxide Thin-Film Transistors. *Deng, C.*, +, *TED Sept. 2021 4450-4454*
- Effect of Threshold Voltage Hysteresis on Switching Characteristics of Silicon Carbide MOSFETs. *Cai, Y.*, +, *TED Oct. 2021 5014-5021*
- Effects of Back-Gate Bias on the Mobility and Reliability of Junction-Less FDSOI Transistors for 3-D Sequential Integration. *Wu, Z.*, +, *TED Feb. 2021 464-470*
- Electric-Field-Dependence Mechanism for Cosmic Ray Failure in Power Semiconductor Devices. *Oda, T.*, +, *TED July 2021 3505-3512*
- Electrical Degradation of *In Situ* SiN/AlGaIn/GaN MIS-HEMTs Caused by Dehydrogenation and Trap Effect Under Hot Carrier Stress. *Niu, X.*, +, *TED Sept. 2021 4283-4288*
- Energy Band Adjustment in a Reliable Novel Charge Plasma SiGe Source TFET to Intensify the BTBT Rate. *Anvarifard, M.K.*, +, *TED Oct. 2021 5284-5290*
- ESD Breakdown of Parylene OFETs With Varying Contact Overlap Capacitance. *Behrman, K.*, +, *TED Sept. 2021 4630-4636*
- Gate Oxide Damage of SiC MOSFETs Induced by Heavy-Ion Strike. *Zhou, X.*, +, *TED Aug. 2021 4010-4015*
- Gate-Induced Threshold Voltage Instabilities in p-Gate GaN HEMTs. *Oeder, T.*, +, *TED Sept. 2021 4322-4328*
- High-Stability Quantum Dot-Converted 3-in-1 Full-Color Mini-Light-Emitting Diodes Passivated With Low-Temperature Atomic Layer Deposition. *Huang, Y.*, +, *TED Feb. 2021 597-601*
- Identification of Channel Hot Carrier Stress-Induced Oxide Traps Leading to Random Telegraph Signals in pMOSFETs. *Ahmed, T.*, +, *TED Feb. 2021 713-719*
- Improved Model on Buried-Oxide Damage Induced by Total-Ionizing-Dose Effect for HV SOI LDMOS. *Yuan, Z.*, +, *TED April 2021 2064-2070*
- Influence of Carbon on pBTI Degradation in GaN-on-Si E-Mode MOSc-HEMT. *Viey, A.G.*, +, *TED April 2021 2017-2024*
- Internal Thermoelectric Cooling in Nanosheet Gate-All-Around FETs Using Schottky Drain Contacts. *Kang, M.J.*, +, *TED Aug. 2021 4156-4160*
- Interplay Between Surface and Buffer Traps in Governing Breakdown Characteristics of AlGaIn/GaN HEMTs—Part II. *Joshi, V.*, +, *TED Jan. 2021 80-87*
- Investigation of Gate-Length Scaling of Ferroelectric FET. *Jindal, S.*, +, *TED March 2021 1364-1368*
- Investigation of Trap-Induced Performance Degradation and Restriction on Higher Ferroelectric Thickness in Negative Capacitance FDSOI FET. *Garg, C.*, +, *TED Oct. 2021 5298-5304*
- Investigation on Short-Circuit Characterization and Optimization of 3.3-kV SiC MOSFETs. *Chen, X.*, +, *TED Jan. 2021 184-191*
- Investigation on Single Pulse Avalanche Failure of 1200-V SiC MOSFETs via Optimized Thermoelectric Simulation. *Bai, Z.*, +, *TED March 2021 1168-1175*
- Localizing Hot-Carrier Degradation in Silicon Trench MOSFETs. *Ruch, B.*, +, *TED April 2021 1804-1809*
- Low Subthreshold Swing and High Performance of Ultrathin PEALD InGaZnO Thin-Film Transistors. *Jeong, S.*, +, *TED April 2021 1670-1675*
- Low-Frequency Noise Analysis of the Optimized Post High-k Deposition Annealing in FinFET Technology. *Deng, W.*, +, *TED March 2021 1202-1206*
- Mechanisms Underlying the Bidirectional  $V_T$  Shift After Negative-Bias Temperature Instability Stress in Carbon-Doped Fully Recessed AlGaIn/GaN MIS-HEMTs. *Zagni, N.*, +, *TED May 2021 2564-2567*
- New Failure Mechanism Induced by Current Limit for Superjunction MOSFET Under Single-Pulse UIS Stress. *Tong, X.*, +, *TED July 2021 3483-3489*
- NiSi/p<sup>+</sup>-Si(n<sup>+</sup>-Si)/n-Si(p-Si) Diodes With Dopant Segregation (DS): p-n or Schottky Junctions?. *Zhang, D.*, +, *TED June 2021 2886-2891*
- On the Channel Hot-Electron's Interaction With C-Doped GaN Buffer and Resultant Gate Degradation in AlGaIn/GaN HEMTs. *Chaudhuri, R.R.*, +, *TED Oct. 2021 4869-4876*
- On the Optimization of Performance and Reliability in a-InGaZnO Thin-Film Transistors by Versatile Light Shielding Design. *Kuo, C.*, +, *TED April 2021 1654-1658*
- On the Physical Meaning of Single-Value Activation Energies for BTI in Si and SiC MOSFET Devices. *Feil, M.W.*, +, *TED Jan. 2021 236-243*
- Online Monitoring for Threshold Voltage of SiC MOSFET Considering the Coupling Impact on BTI and Junction Temperature. *Xin, J.*, +, *TED April 2021 1772-1777*
- Performance Boosts in n-Type Lateral Double-Diffused MOSFET With Process-Induced Strain Using Contact Etch Stop Layer Stressor. *Wu, W.*, +, *TED Jan. 2021 421-424*
- Performance Enhancement of 2.3 kV 4H-SiC Planar-Gate MOSFETs Using Reduced Gate Oxide Thickness. *Agarwal, A.*, +, *TED Oct. 2021 5029-5033*
- Radiation Resistance of High-Voltage Silicon and 4H-SiC Power p-i-n Diodes. *Hazdra, P.*, +, *TED Jan. 2021 202-207*
- Reliability of p-GaN Gate HEMTs in Reverse Conduction. *Cingu, D.*, +, *TED Feb. 2021 645-652*
- Reliability of p-Type Pi-Gate Poly-Si Nanowire Channel Junctionless Accumulation-Mode FETs. *Hsieh, D.*, +, *TED June 2021 2647-2652*
- Roles of Gate Voltage and Stress Power in Self-Heating Degradation of a-InGaZnO Thin-Film Transistors. *Du, M.*, +, *TED April 2021 1644-1648*
- Simulation Study of a High Gate-to-Source ESD Robustness Power p-GaN HEMT With Self-Triggered Discharging Channel. *Xin, Y.*, +, *TED Sept. 2021 4536-4542*
- Single-Event Damage-Induced Gate-Leakage Mechanisms in AlGaIn/GaN High-Electron-Mobility Transistors. *Yue, S.*, +, *TED June 2021 2667-2672*
- Substrate Bias Enhanced Trap Effects on Time-Dependent Dielectric Breakdown of GaN MIS-HEMTs. *Yang, W.*, +, *TED May 2021 2233-2239*
- The Relationship Between Resistive Protective Oxide (RPO) and Hot Carrier Stress (HCS) Degradation in n-Channel LD SOI MOSFET. *Lin, Y.*, +, *TED March 2021 962-967*

- Thermal Design Rules of AlGaIn/GaN-Based Microwave Transistors on Diamond. *Gerrer, T.*, +, *TED April 2021 1530-1536*
- Time Evolution of DIBL in Gate-All-Around Nanowire MOSFETs During Hot-Carrier Stress. *Gupta, A.*, +, *TED June 2021 2641-2646*
- Time-Dependent Hot Carrier Degradation in Polysilicon Emitter Bipolar Transistors Under High Current and Radiation Combined Stress. *Zhang, P.*, +, *TED Sept. 2021 4208-4213*
- Time-Dependent Threshold Voltage Instability Mechanisms of p-GaN Gate AlGaIn/GaN HEMTs Under High Reverse Bias Conditions. *Li, S.*, +, *TED Jan. 2021 443-446*
- Toward Automated Defect Extraction From Bias Temperature Instability Measurements. *Waldhoer, D.*, +, *TED Aug. 2021 4057-4063*

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- 1.2-kV Vertical GaN Fin-JFETs: High-Temperature Characteristics and Avalanche Capability. *Liu, J.*, +, *TED April 2021 2025-2032*
- A High-Efficiency IGBT Health Status Assessment Method Based on Data Driven. *Zhang, Z.*, +, *TED Jan. 2021 168-174*
- A New Method to Measure the Parasitic Parameter Model of IGBT on Bias Voltage. *Wang, J.*, +, *TED May 2021 2387-2394*
- Analysis of Current Capability of SiC Power MOSFETs Under Avalanche Conditions. *Nida, S.*, +, *TED Sept. 2021 4587-4592*
- Characterization and Analysis on Performance and Avalanche Reliability of SiC MOSFETs With Varied JFET Region Width. *Zhu, Z.*, +, *TED Aug. 2021 3982-3990*
- Drain Field Plate Impact on the Hard-Switching Performance of AlGaIn/GaN HEMTs. *Minetto, A.*, +, *TED Oct. 2021 5003-5008*
- Fabrication and Characterization of High-Voltage NiO/ $\beta$ -Ga<sub>2</sub>O<sub>3</sub> Heterojunction Power Diodes. *Luo, H.*, +, *TED Aug. 2021 3991-3996*
- Investigation of the Impact of Hot-Carrier-Induced Interface State Generation on Carrier Mobility in nMOSFET. *Wu, Z.*, +, *TED July 2021 3246-3253*
- Investigation on Single Pulse Avalanche Failure of 1200-V SiC MOSFETs via Optimized Thermoelectric Simulation. *Bai, Z.*, +, *TED March 2021 1168-1175*
- Ionic Liquid Channel Field Effect Transistor Fabricated Using Silicon Dioxide Trench. *Naorem, M.*, +, *TED Sept. 2021 4741-4747*
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- New Failure Mechanism Induced by Current Limit for Superjunction MOSFET Under Single-Pulse UIS Stress. *Tong, X.*, +, *TED July 2021 3483-3489*
- Noise Analysis of the Leakage Current in Time-Dependent Dielectric Breakdown in a GaN SLCFET. *Dalcanale, S.*, +, *TED May 2021 2220-2225*

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- Acceleration of Semiconductor Device Simulation With Approximate Solutions Predicted by Trained Neural Networks. *Han, S.*, +, *TED Nov. 2021 5483-5489*
- Foreword Special Issue on “New Simulation Methodologies for Next-Generation TCAD Tools”. *Jungemann, C.*, +, *TED Nov. 2021 5346-5349*

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- A Multi-epi Superjunction MOSFET With a Lightly Doped MOS-Channel Diode for Improving Reverse Recovery. *Huang, M.*, +, *TED May 2021 2401-2407*
- Avalanche Delay and Dynamic Triggering in GaAs-Based S-Diodes Doped With Deep Level Impurity. *Prudaev, I.A.*, +, *TED Jan. 2021 57-65*
- Comparison of Impact Ionization Models for 4H-SiC Along the  $\langle 0001 \rangle$  Direction, Through Breakdown Voltage Simulations at Room Temperature. *Stefanakis, D.*, +, *TED May 2021 2582-2586*
- HfZrO<sub>2</sub>-Based Switchable Diode for Logic-in-Memory Applications. *Kao, R.*, +, *TED Feb. 2021 545-549*
- Low-Temperature Electrical Performance of PureB Photodiodes Revealing Al-Metallization-Related Degradation of Dark Currents. *Knezevic, T.*, +, *TED June 2021 2810-2817*
- Online Monitoring for Threshold Voltage of SiC MOSFET Considering the Coupling Impact on BTI and Junction Temperature. *Xin, J.*, +, *TED April 2021 1772-1777*

- Recessed AlGaIn/GaN Schottky Barrier Diodes With TiN and NiN Dual Anodes. *Wang, T.*, +, *TED June 2021 2867-2871*

- Stable and Printable Direct X-Ray Detectors Based on Micropyramid  $\omega$ -Bi<sub>2</sub>O<sub>3</sub> With Low Detection Limit. *Mao, L.*, +, *TED July 2021 3411-3416*

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- “Hole Redistribution” Model Explaining the Thermally Activated  $R_{ON}$  Stress/Recovery Transients in Carbon-Doped AlGaIn/GaN Power MIS-HEMTs. *Zagni, N.*, +, *TED Feb. 2021 697-703*
- 3-D Full-Band Monte Carlo Simulation of Hot-Electron Energy Distributions in Gate-All-Around Si Nanowire MOSFETs. *Reaz, M.*, +, *TED May 2021 2556-2563*
- A High  $Q$  Value ScAlN/AlN-Based SAW Resonator for Load Sensing. *Lin, B.*, +, *TED Oct. 2021 5192-5197*
- A Lateral Power p-Channel Trench MOSFET Improved by Variation Vertical Doping. *Cheng, J.*, +, *TED April 2021 2138-2141*
- A Surface Potential Model for Field-Effect Transistors With Bound-Charge Engineering. *Prentki, R.J.*, *TED Sept. 2021 4625-4629*
- Accumulation-Mode Lateral Double-Diffused MOSFET Breaking Silicon Limit by Eliminating Dependence of Specific ON-Resistance on Doping Concentration. *Wang, Y.*, +, *TED May 2021 2414-2419*
- An Asymmetrically Doped Vertical Si Biristor With Sub-1-V Operation. *Das, B.*, +, *TED Aug. 2021 3728-3733*
- Analysis and Modeling of Vertical Current Conduction and Breakdown Mechanisms in Semi-Insulating GaN Grown on GaN: Role of Deep Levels. *Stoklas, R.*, +, *TED May 2021 2365-2371*
- Analytical Study on a 700 V Triple RESURF LDMOS With a Variable High- $K$  Dielectric Trench. *Cao, Z.*, +, *TED June 2021 2872-2878*
- Compact Modeling of Multidomain Ferroelectric FETs: Charge Trapping, Channel Percolation, and Nucleation-Growth Domain Dynamics. *Xiang, Y.*, +, *TED April 2021 2107-2115*
- Contact Doping as a Design Strategy for Compact TFT-Based Temperature Sensing. *Bestelink, E.*, +, *TED Oct. 2021 4962-4965*
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- Doping Profile Engineered Triple Heterojunction TFETs With 12-nm Body Thickness. *Chen, C.*, +, *TED June 2021 3104-3111*
- Effect of the Si Doping Content in HfO<sub>2</sub> Film on the Key Performance Metrics of Ferroelectric FETs. *Mulaosmanovic, H.*, +, *TED Sept. 2021 4773-4779*
- Electrical and Thermal Performance of Ga<sub>2</sub>O<sub>3</sub>-Al<sub>2</sub>O<sub>3</sub>-Diamond Super-Junction Schottky Barrier Diodes. *Mishra, A.*, +, *TED Oct. 2021 5055-5061*
- Electrical Characteristics of Vertical GaN Nanowire Vacuum Field Emitter Devices. *Doundoulakis, G.*, +, *TED June 2021 3034-3039*
- Electrothermal Analysis of the Charge-Discharge Related Energy Loss of the Output Capacitance in OFF-State Superjunction MOSFETs. *Lin, Z.*, +, *TED Sept. 2021 4582-4586*
- Enhancement-Mode Atomic-Layer-Deposited In<sub>2</sub>O<sub>3</sub> Transistors With Maximum Drain Current of 2.2 A/mm at Drain Voltage of 0.7 V by Low-Temperature Annealing and Stability in Hydrogen Environment. *Si, M.*, +, *TED March 2021 1075-1080*
- Fabricating In-Plane MoTe<sub>2</sub> p-n Homojunction Photodetector Using Laser-Induced p-Type Doping. *Chen, J.*, +, *TED Sept. 2021 4485-4490*
- Flexible High-Temperature Polycrystalline Silicon Thin Film Transistor on Metal Foil With S/D Doped by Diffusion. *Yu, B.*, +, *TED Aug. 2021 3857-3862*
- Formation of F-Doped Offset Region for Spray Pyrolyzed Self-Aligned Coplanar Amorphous Zinc-Tin-Oxide Thin-Film Transistor by NF<sub>3</sub> Plasma Treatment. *Kim, Y.G.*, +, *TED March 2021 1057-1062*
- Gate-First Negative Capacitance Field-Effect Transistor With Self-Aligned Nickel-Silicide Source and Drain. *Kim, S.*, +, *TED Sept. 2021 4754-4757*
- Guidelines for Ferroelectric-Semiconductor Tunnel Junction Optimization by Band Structure Engineering. *Chang, P.*, +, *TED July 2021 3526-3531*
- High Band-to-Band Tunneling Current in InAs/GaSb Heterojunction Esaki Diodes by the Enhancement of Electric Fields Close to the Mesa Sidewalls. *Hou, W.*, +, *TED Aug. 2021 3748-3754*

- High-Performance Pentacene/ZnO UV-Visible Photodetector Using Solution Method. *Srivastava, A.*, +, *TED July 2021 3439-3445*
- Hydrogenation of Mg-Doped InGaZnO Thin-Film Transistors for Enhanced Electrical Performance and Stability. *Abliz, A.*, *TED July 2021 3379-3383*
- Impact of the Nonlinear Dielectric Hysteresis Properties of a Charge Trap Layer in a Novel Hybrid High-Speed and Low-Power Ferroelectric or Antiferroelectric HSO/HZO Boosted Charge Trap Memory. *Ali, T.*, +, *TED April 2021 2098-2106*
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- Reconfigurable MoTe<sub>2</sub> Field-Effect Transistors and its Application in Compact CMOS Circuits. *Chen, J.*, +, *TED Sept. 2021 4748-4753*
- Self-Consistent Modeling of B or N Substitution Doped Bottom Gated Graphene FET With Nonzero Bandgap. *Chandrasekar, L.*, +, *TED July 2021 3658-3664*
- Sensitivity Analysis and Design of Negative-Capacitance Junctionless Transistor for High-Performance Applications. *Gupta, M.*, +, *TED Aug. 2021 4136-4143*
- Small- and Large-Signal Dynamic Output Capacitance and Energy Loss in GaN-on-Si Power HEMTs. *Zhuang, J.*, +, *TED April 2021 1819-1826*
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- NiSi/p<sup>+</sup>-Si(n<sup>+</sup>-Si)/n-Si(p-Si) Diodes With Dopant Segregation (DS): p-n or Schottky Junctions?. *Zhang, D.*, +, *TED June 2021 2886-2891*
- Sub-mA/cm<sup>2</sup> Dark Current Density, Buffer-Less Germanium (Ge) Photodiodes on a 200-mm Ge-on-Insulator Substrate. *Lin, Y.*, +, *TED April 2021 1730-1737*
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- Exceptional Responsivity ( $>6$  kA/W) and Dark Current ( $<70$  fA) Tradeoff of n-Ga<sub>2</sub>O<sub>3</sub>/p-CuO Quasi-Heterojunction-Based Deep UV Photodetector. *Kumar, A.*, +, *TED Jan. 2021* 144-151
- Fabrication of Binder-Free TiO<sub>2</sub> Nanofiber Electrodes via Electrophoretic Deposition for Low-Power Electronic Applications. *Rani, S.*, +, *TED Jan. 2021* 251-256
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- Sub-mA/cm<sup>2</sup> Dark Current Density, Buffer-Less Germanium (Ge) Photodiodes on a 200-nm Ge-on-Insulator Substrate. *Lin, Y.*, +, *TED April 2021* 1730-1737
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- Epitaxial Al-InAs Heterostructures as Platform for Josephson Junction Field-Effect Transistor Logic Devices. *Wen, F.*, +, *TED April 2021* 1524-1529
- Formation of Graphene-Silicon Junction by Room Temperature Reduction With Simultaneous Defects Removal. *Yi, H.*, +, *TED Feb. 2021* 873-878
- High Band-to-Band Tunneling Current in InAs/GaSb Heterojunction Esaki Diodes by the Enhancement of Electric Fields Close to the Mesa Sidewalls. *Hou, W.*, +, *TED Aug. 2021* 3748-3754
- Interface Charge Effects on 2-D Electron Gas in Vertical-Scaled Ultrathin-Barrier AlGaIn/GaN Heterostructure. *Huang, S.*, +, *TED Jan. 2021* 36-41
- Millimeter-Wave Donor-Acceptor-Doped DpHEMT. *Pashkovskii, A.B.*, +, *TED Jan. 2021* 53-56
- Model of Electron Population and Energy Band Diagram of Multiple-Channel GaN Heterostructures. *Chen, X.*, +, *TED April 2021* 1557-1562
- Monolithic Integrated Normally OFF GaN Power Device With Antiparallel Lateral Schottky Barrier Controlled Schottky Rectifier. *Bi, L.*, +, *TED April 2021* 1778-1783
- Numerical Study of SiC MOSFET With Integrated n/n-Type Poly-Si/SiC Heterojunction Freewheeling Diode. *Yu, H.*, +, *TED Sept. 2021* 4571-4576
- Self-Powered Multicolor Broadband Photodetector Based on GaSe/WSe<sub>2</sub>//WSe<sub>2</sub>/BP Van Der Waals Heterostructure. *Chen, J.*, +, *TED Aug. 2021* 3881-3886
- Silicene/MoS<sub>2</sub> Heterojunction for High-Performance Photodetector. *Kharadi, M.A.*, +, *TED Jan. 2021* 138-143
- Single-Event Damage-Induced Gate-Leakage Mechanisms in AlGaIn/GaN High-Electron-Mobility Transistors. *Yue, S.*, +, *TED June 2021* 2667-2672
- Temporal Electron-Spin Splitter Based on a Semiconductor Microstructure Constructed on Surface of InAs/Al<sub>x</sub>In<sub>1-x</sub>As Heterostructure by Patterning a Ferromagnetic Stripe and a Schottky-Metal Stripe. *Lu, M.*, +, *TED Feb. 2021* 860-864
- Theoretical Study of Charge Carrier Lifetime and Recombination on the Performance of Eco-Friendly Perovskite Solar Cell. *Shukla, R.*, +, *TED July 2021* 3446-3452
- Transistor Subthreshold Swing Lowered by 2-D Heterostructures. *Wu, F.*, +, *TED Jan. 2021* 411-414
- Understanding High-Energy 75-MeV Sulfur-Ion Irradiation-Induced Degradation in GaN-Based Heterostructures: The Role of the GaN Channel Layer. *Challa, S.R.*, +, *TED Jan. 2021* 24-28
- Semiconductor junctions**
- A Multi-epi Superjunction MOSFET With a Lightly Doped MOS-Channel Diode for Improving Reverse Recovery. *Huang, M.*, +, *TED May 2021* 2401-2407
- Analytical Design and Experimental Verification of Lateral Superjunction Based on Global Region Normalization Method. *Zhang, W.*, +, *TED May 2021* 2372-2377
- Electrical and Thermal Performance of Ga<sub>2</sub>O<sub>3</sub>-Al<sub>2</sub>O<sub>3</sub>-Diamond Super-Junction Schottky Barrier Diodes. *Mishra, A.*, +, *TED Oct. 2021* 5055-5061
- Energy Band Adjustment in a Reliable Novel Charge Plasma SiGe Source TFET to Intensify the BTBT Rate. *Anvarifard, M.K.*, +, *TED Oct. 2021* 5284-5290
- Extraction of Compact Static Thermal Model Parameters for SiGe HBTs. *Huszka, Z.*, +, *TED Feb. 2021* 491-496

- New Failure Mechanism Induced by Current Limit for Superjunction MOSFET Under Single-Pulse UIS Stress. *Tong, X.*, +, *TED July 2021 3483-3489*
- Novel Vertical Power MOSFET With Step Hk Insulator Close to Super Junction Limit Relationship Between Breakdown Voltage and Specific ON-Resistance by Improving Electric Field Modulation. *Duan, B.*, +, *TED Oct. 2021 5048-5054*
- Optimum Aspect Ratio of Superjunction Pillars Considering Charge Imbalance. *Akshay, K.*, +, *TED April 2021 1798-1803*
- Simulation Study of Single-Event Burnout in 1.5-kV 4H-SiC JTE Termination. *Yu, C.*, +, *TED July 2021 3711-3715*
- Simulation Study on Single-Event Burnout in Rated 1.2-kV 4H-SiC Super-Junction VDMOS. *Yu, C.*, +, *TED Oct. 2021 5034-5040*
- Semiconductor laser arrays**
- Analysis of Thermal Properties of 940-nm Vertical Cavity Surface Emitting Laser Arrays. *Xun, M.*, +, *TED Jan. 2021 158-163*
- Semiconductor lasers**
- Avalanche Delay and Dynamic Triggering in GaAs-Based S-Diodes Doped With Deep Level Impurity. *Prudae, I.A.*, +, *TED Jan. 2021 57-65*
- Enhanced Color Quality of Phosphor-Converted White Laser Diodes Through Bicolor Phosphor-in-Glass. *Wang, H.*, +, *TED Nov. 2021 5652-5655*
- Investigation of an Opposed-Contact GaAs Photoconductive Semiconductor Switch at 1-kHz Excitation. *Xu, M.*, +, *TED May 2021 2355-2359*
- Low-Voltage Thyristor Heterostructure for High-Current Pulse Generation at High Repetition Rate. *Slipchenko, S.O.*, +, *TED June 2021 2855-2860*
- Performance Enhancement of Terahertz Laser Diode via Resonant Cavities. *Liu, Y.*, +, *TED Dec. 2021 6465-6469*
- Semiconductor materials**
- Effect of Insertion of Dielectric Layer on the Performance of Hafnia Ferroelectric Devices. *Hwang, J.*, +, *TED Feb. 2021 841-845*
- Enhanced Performance of SnO<sub>2</sub>-Noble Metal Composites on Electrical Energy Generation and Storage Devices. *Amuthameena, S.*, +, *TED Oct. 2021 5291-5297*
- Fabricating In-Plane MoTe<sub>2</sub> p-n Homojunction Photodetector Using Laser-Induced p-Type Doping. *Chen, J.*, +, *TED Sept. 2021 4485-4490*
- Fabrication of Binder-Free TiO<sub>2</sub> Nanofiber Electrodes via Electrophoretic Deposition for Low-Power Electronic Applications. *Rani, S.*, +, *TED Jan. 2021 251-256*
- Operation of Current Mirrors in SiGe BiCMOS Technology at Cryogenic Temperatures. *Ying, H.*, +, *TED April 2021 1439-1445*
- Origin of Ambipolar Behavior in p-Type Tin Monoxide Semiconductors: Impact of Oxygen Vacancy Defects. *Kim, T.*, +, *TED Sept. 2021 4467-4472*
- PbSnS<sub>2</sub>-Based Gas Sensor to Detect SF<sub>6</sub> Decompositions: DFT and NEGF Calculations. *Guo, H.*, +, *TED Oct. 2021 5322-5325*
- Reconfigurable MoTe<sub>2</sub> Field-Effect Transistors and its Application in Compact CMOS Circuits. *Chen, J.*, +, *TED Sept. 2021 4748-4753*
- Solution-Driven HfLaO<sub>x</sub>-Based Gate Dielectrics for Thin Film Transistors and Unipolar Inverters. *Wang, W.*, +, *TED Sept. 2021 4437-4443*
- Tunable Alloying Improved Wide Spectrum UV-Vis-NIR and Polarization-Sensitive Photodetector Based on Sb-S-Se Nanowires. *Yu, Y.*, +, *TED Aug. 2021 3887-3893*
- Semiconductor process modeling**
- A Multiscale Simulation Framework for Steep-Slope Si Nanowire Cold Source FET. *Gan, W.*, +, *TED Nov. 2021 5455-5461*
- Bridging TCAD and AI: Its Application to Semiconductor Design. *Jeong, C.*, +, *TED Nov. 2021 5364-5371*
- Design and Analysis of P-GaN/N-Ga<sub>2</sub>O<sub>3</sub> Based Junction Barrier Schottky Diodes. *Nandi, A.*, +, *TED Dec. 2021 6052-6058*
- Effect of Random Dopant Fluctuation on Data Retention Time Distribution in DRAM. *Kim, K.Y.*, +, *TED Nov. 2021 5572-5577*
- Fundamental Aspects of Semiconductor Device Modeling Associated With Discrete Impurities: Monte Carlo Simulation Scheme. *Sano, N.*, +, *TED Nov. 2021 5394-5399*
- Industrial TCAD: Modeling Atoms to Chips. *Stettler, M.A.*, +, *TED Nov. 2021 5350-5357*
- Machine Learning Regression-Based Single-Event Transient Modeling Method for Circuit-Level Simulation. *Xu, C.*, +, *TED Nov. 2021 5758-5764*
- Multigate Ferroelectric Transistor Design Toward 3-nm Technology Node. *Choe, G.*, +, *TED Nov. 2021 5908-5911*
- Stress in Silicon-Germanium Nanowires: Layout Dependence and Imperfect Source/Drain Epitaxial Stressors. *Eneman, G.*, +, *TED Nov. 2021 5380-5385*
- Semiconductor quantum dots**
- A Sandwich Structure Light-Trapping Fluorescence Antenna With Large Field of View for Visible Light Communication. *Yu, B.*, +, *TED Feb. 2021 565-571*
- Eliminating the Residual Ultraviolet Excitation Light and Increasing Quantum Dot Emission Intensity in LED Display Devices. *Yan, C.*, +, *TED Feb. 2021 584-591*
- High-Stability Quantum Dot-Converted 3-in-1 Full-Color Mini-Light-Emitting Diodes Passivated With Low-Temperature Atomic Layer Deposition. *Huang, Y.*, +, *TED Feb. 2021 597-601*
- Quantum Dot With a Diamond-Shaped Channel MOSFET on a Bulk Si Substrate. *Gu, J.*, +, *TED Jan. 2021 405-410*
- Semiconductor quantum wells**
- Capacitance Scaling in In<sub>0.71</sub>Ga<sub>0.29</sub>As/InP MOSFETs With Self-Aligned a:Si Spacers. *Garigapati, N.S.*, +, *TED Aug. 2021 3762-3767*
- Doping Profile Engineered Triple Heterojunction TFETs With 12-nm Body Thickness. *Chen, C.*, +, *TED June 2021 3104-3111*
- Epitaxial Al-InAs Heterostructures as Platform for Josephson Junction Field-Effect Transistor Logic Devices. *Wen, F.*, +, *TED April 2021 1524-1529*
- High Band-to-Band Tunneling Current in InAs/GaSb Heterojunction Esaki Diodes by the Enhancement of Electric Fields Close to the Mesa Sidewalls. *Hou, W.*, +, *TED Aug. 2021 3748-3754*
- Hole Transport in Ultraviolet Light-Emitting Diode via p-Type Injection Channel. *Mondal, R.K.*, +, *TED May 2021 2320-2325*
- Millimeter-Wave Donor-Acceptor-Doped DpHEMT. *Pashkovskii, A.B.*, +, *TED Jan. 2021 53-56*
- Unipolar Quantum Well InGaAs/AlGaAs Heterostructures With Impact Ionization for Efficient Low-Voltage Light-Emitting Devices. *Slipchenko, S.O.*, +, *TED June 2021 2823-2828*
- Semiconductor quantum wires**
- Electrical Characteristics of Vertical GaN Nanowire Vacuum Field Emitter Devices. *Doundoulakis, G.*, +, *TED June 2021 3034-3039*
- Semiconductor storage**
- Controlled Majority-Inverter Graph Logic With Highly Nonlinear, Self-Rectifying Memristor. *Ni, R.*, +, *TED Oct. 2021 4897-4902*
- Semiconductor superlattices**
- AlN/GaN Superlattice Channel HEMTs on Silicon Substrate. *Liu, S.*, +, *TED July 2021 3296-3301*
- Noise Analysis of the Leakage Current in Time-Dependent Dielectric Breakdown in a GaN SLCFET. *Dalcanale, S.*, +, *TED May 2021 2220-2225*
- Semiconductor switches**
- Avalanche Delay and Dynamic Triggering in GaAs-Based S-Diodes Doped With Deep Level Impurity. *Prudae, I.A.*, +, *TED Jan. 2021 57-65*
- Investigation of an Opposed-Contact GaAs Photoconductive Semiconductor Switch at 1-kHz Excitation. *Xu, M.*, +, *TED May 2021 2355-2359*
- Investigations of the Effects of the Orientation of AlN-Based Complementary Resistive Switches. *Hung, P.*, +, *TED Aug. 2021 3826-3831*
- Semiconductor thin films**
- 16 × 4 Linear Solar-Blind UV Photoconductive Detector Array Based on β-Ga<sub>2</sub>O<sub>3</sub> Film. *Zhi, Y.*, +, *TED July 2021 3435-3438*
- Carrier Velocity in Amorphous Metal-Oxide-Semiconductor Transistors. *Wang, X.*, +, *TED Jan. 2021 125-131*
- Dramatic Improvement in the Rectifying Properties of Pd Schottky Contacts on β-Ga<sub>2</sub>O<sub>3</sub> During Their High-Temperature Operation. *Hou, C.*, +, *TED April 2021 1791-1797*
- Effect of Femtosecond Laser Postannealing on a-IGZO Thin-Film Transistors. *Lee, J.*, +, *TED July 2021 3371-3378*
- Effect of Insertion of Dielectric Layer on the Performance of Hafnia Ferroelectric Devices. *Hwang, J.*, +, *TED Feb. 2021 841-845*
- Enhanced Photodetection Performance in Graphene-Assisted Tunneling Photodetector. *You, C.*, +, *TED April 2021 1702-1709*



- Enhanced Thermal Stability of Elevated-Metal Metal-Oxide Thin-Film Transistors via Low-Temperature Nitrogen Post-Annealing. *Wei, Y.*, +, *TED April 2021 1649-1653*
- Enhancement-Mode Atomic-Layer-Deposited In<sub>2</sub>O<sub>3</sub> Transistors With Maximum Drain Current of 2.2 A/mm at Drain Voltage of 0.7 V by Low-Temperature Annealing and Stability in Hydrogen Environment. *Si, M.*, +, *TED March 2021 1075-1080*
- Flexible Complementary Oxide Thin-Film Transistor-Based Inverter With High Gain. *Hsu, S.*, +, *TED March 2021 1070-1074*
- Formation of F-Doped Offset Region for Spray Pyrolyzed Self-Aligned Coplanar Amorphous Zinc-Tin-Oxide Thin-Film Transistor by NF<sub>3</sub> Plasma Treatment. *Kim, Y.G.*, +, *TED March 2021 1057-1062*
- High Field Temperature-Independent Field-Effect Mobility of Amorphous Indium-Gallium-Zinc Oxide Thin-Film Transistors: Understanding the Importance of Equivalent-Oxide-Thickness Downscaling. *Han, K.*, +, *TED Jan. 2021 118-124*
- High-Mobility, Low-Voltage Programmable/Erasable Ferroelectric Polymer Transistor Nonvolatile Memory Based on a P(VDF-TrFE)/PMMA Bilayer Gate Insulator. *Xu, M.*, +, *TED July 2021 3359-3364*
- High-Performance Pentacene/ZnO UV-Visible Photodetector Using Solution Method. *Srivastava, A.*, +, *TED July 2021 3439-3445*
- High-Performance Thin-Film IGZO Schottky Diodes With Sputtered PdO<sub>x</sub> Anode. *Yan, S.*, +, *TED Sept. 2021 4444-4449*
- Impact of the Nonlinear Dielectric Hysteresis Properties of a Charge Trap Layer in a Novel Hybrid High-Speed and Low-Power Ferroelectric or Antiferroelectric HSO/HZO Boosted Charge Trap Memory. *Ali, T.*, +, *TED April 2021 2098-2106*
- Improving the Cu<sub>2</sub>ZnSn(S,Se)<sub>4</sub>-Based Photovoltaic Conversion Efficiency by Back-Contact Modification. *Sengar, B.S.*, +, *TED June 2021 2748-2752*
- Influence of Cu Doping in Si-Te-Based Chalcogenide Glasses and Thin Films: Electrical Switching, Morphological and Raman Studies. *Roy, D.*, +, *TED March 2021 1196-1201*
- Investigation of Electrical and Optical Properties of AlGaInP Red Vertical Micro-Light-Emitting Diodes With Cu/Invar/Cu Metal Substrates. *Sinha, S.*, +, *TED June 2021 2818-2822*
- Low Subthreshold Swing and High Performance of Ultrathin PEALD InGaZnO Thin-Film Transistors. *Jeong, S.*, +, *TED April 2021 1670-1675*
- Modeling of Photovoltaic Solar Cell Based on CuSbS<sub>2</sub> Absorber for the Enhancement of Performance. *Sadanand, .*, +, *TED March 2021 1121-1128*
- Performance Improvement for Spray-Coated ZnO TFT by F Doping With Spray-Coated Zr-Al-O Gate Insulator. *Saha, J.K.*, +, *TED March 2021 1063-1069*
- Structural and Electrical Characteristics of ALD-TiO<sub>2</sub>/SiON/n-Si Gate-Stack for Advanced CMOS Device Applications. *Gupta, R.*, +, *TED June 2021 2625-2632*
- Tunable Negative Differential Resistance and Resistive Switching Properties of Amorphous WO<sub>x</sub> Devices. *Zhang, K.*, +, *TED Aug. 2021 3807-3812*
- Ultrathin Mg<sub>0.05</sub>Sn<sub>0.95</sub>O<sub>x</sub>-Based Thin-Film Transistor by Mist Chemical Vapor Deposition. *Liu, H.*, +, *TED July 2021 3390-3395*
- Vertical Sandwich GAA FETs With Self-Aligned High-*k* Metal Gate Made by Quasi Atomic Layer Etching Process. *Zhang, Y.*, +, *TED June 2021 2604-2610*
- Yb/InSe/SiO<sub>2</sub>/Au Straddling-Type Tunneling Devices Designed As Photosensors, MOS Capacitors, and Gigahertz Bandstop Filters. *Alfhaid, L.H.K.*, +, *TED March 2021 1093-1100*
- Semiconductor-insulator boundaries**
- Applicability of Shockley-Read-Hall Theory for Interface States. *Ruch, B.*, +, *TED April 2021 2092-2097*
- Semiconductor-insulator-semiconductor devices**
- A Cascade Electron Source Based on Series Horizontal Tunneling Junctions. *Li, Z.*, +, *TED Feb. 2021 818-821*
- Semiconductor-metal boundaries**
- Cladded Surface-Plasmon-Enhanced BP Photodetector Based on the Damage-Free Metal-Semiconductor Interface. *Yang, Z.*, +, *TED Jan. 2021 164-167*
- Experimental Investigation of As Preamorphization Implant on Electrical Property of Ti-Based Silicide Contacts. *Mao, S.*, +, *TED April 2021 1835-1840*
- Improvement of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> MIS-SBD Interface Using Al-Reacted Interfacial Layer. *He, M.*, +, *TED July 2021 3314-3319*
- Yb/InSe/SiO<sub>2</sub>/Au Straddling-Type Tunneling Devices Designed As Photosensors, MOS Capacitors, and Gigahertz Bandstop Filters. *Alfhaid, L.H.K.*, +, *TED March 2021 1093-1100*
- Sensitivity analysis**
- Compact Modeling of pH-Sensitive FETs Based on 2-D Semiconductors. *Groug, T.E.*, +, *TED Nov. 2021 5916-5919*
- Dielectric-Modulated Bulk-Planar Junctionless Field-Effect Transistor for Biosensing Applications. *Singh, D.*, +, *TED July 2021 3545-3551*
- Enhancing the Sensitivity of GaN High Electron-Mobility Transistors-Based pH Sensor by Dual Function of Monolithic Integrated Planar Multi-Channel and Ultraviolet Light. *Yang, X.*, +, *TED Dec. 2021 6437-6443*
- Finger Gate Vacuum Channel Field Emission Transistors: Performance and Sensitivity Analysis. *Khoshkijari, F.K.*, +, *TED Oct. 2021 5250-5256*
- Operation of Diamond Solution-Gated Field-Effect Transistor in the Frequency Domain. *Chang, X.*, +, *TED Dec. 2021 6400-6406*
- Portable Thermal Management Platform for Synthesis of ZnO Nanoparticle in a Microfluidic Device: Validated for Electrochemical Sensing and Glucose Fuel Cell Applications. *Kulkarni, M.B.*, +, *TED Aug. 2021 4070-4076*
- Study of a 0.34-THz Ladder-Type Extended Interaction Klystron With Narrow Coupling Cavities. *Guo, N.*, +, *TED Nov. 2021 5851-5857*
- Sensor arrays**
- Differential Signal Acquisition Using TFT Light-Sensing Pixel Array. *Tai, Y.*, +, *TED July 2021 3403-3410*
- Sensor phenomena and characterization**
- Yb/MoO<sub>3</sub>/In<sub>2</sub>Se<sub>3</sub>/Ag Sensors Designed as Tunneling Diodes, MOSFETs, Microwave Resonators, Laser Sensors, and VLC Receivers Suitable for 4G/5G and VLC Technologies. *Qasrawi, A.F.*, +, *TED Dec. 2021 6444-6450*
- Sensors**
- A Wearable Ultrathin Flexible Sensor Inserted Into Nasal Cavity for Precise Sleep Respiratory Monitoring. *Zhang, H.*, +, *TED Aug. 2021 4090-4097*
- Design and Investigation of Dielectrically Modulated Dual-Material Gate-Oxide-Stack Double-Gate TFET for Label-Free Detection of Biomolecules. *Singh, K.S.*, +, *TED Nov. 2021 5784-5791*
- High-Mechanical-Resolution Pressure Sensor Based on Melt-Blown Fibers in Integrated Wearable Mask for Respiratory Monitoring. *Gao, L.*, +, *TED Nov. 2021 5765-5772*
- Oxide TFT Frontend Amplifiers for Flexible Sensing Systems. *Xu, Y.*, +, *TED Dec. 2021 6190-6196*
- SAPIENS: A 64-kb RRAM-Based Non-Volatile Associative Memory for One-Shot Learning and Inference at the Edge. *Li, H.*, +, *TED Dec. 2021 6637-6643*
- Study of a Highly Sensitive Formaldehyde Sensor Prepared With a Tungsten Trioxide Thin Film and Gold Nanoparticles. *Niu, J.*, +, *TED Dec. 2021 6422-6429*
- Yb/MoO<sub>3</sub>/In<sub>2</sub>Se<sub>3</sub>/Ag Sensors Designed as Tunneling Diodes, MOSFETs, Microwave Resonators, Laser Sensors, and VLC Receivers Suitable for 4G/5G and VLC Technologies. *Qasrawi, A.F.*, +, *TED Dec. 2021 6444-6450*
- Series (mathematics)**
- Device Parameter-Based Analytical Modeling of Power Supply Induced Jitter in CMOS Inverters. *Arora, P.*, +, *TED July 2021 3268-3275*
- SF<sub>6</sub> insulation**
- Gas Sensor Based on Semihydrogenated and Semifluorinated h-BN for SF<sub>6</sub> Decomposition Components Detection. *Peng, Z.*, +, *TED April 2021 1878-1885*
- Shift registers**
- High Performance Dual Gate Blue Laser Annealed Poly-Si Thin-Film Transistor for High-Resolution Displays. *Jeong, D.Y.*, +, *TED Aug. 2021 3863-3869*
- ReRAM-Based Pseudo-True Random Number Generator With High Throughput and Unpredictability Characteristics. *Tseng, P.*, +, *TED April 2021 1593-1597*

**Short-circuit currents**

- Demonstration of Constant-Gate-Charge Scaling to Increase the Robustness of Silicon Carbide Power MOSFETs. *Cooper, J.A.*, +, *TED Sept. 2021 4577-4581*
- Device Engineering Approach Toward Stable, Efficient, and Eco-Friendly Perovskite Solar Cell. *Pandey, S.K.*, +, *TED March 2021 1142-1148*
- Efficiency Enhancement of the CdS/CdTe Solar Nanostructured Cell Using Electron-Reflecting Layer. *Sharma, D.K.*, +, *TED March 2021 1129-1134*
- Enhanced Charge Extraction in Metal-Perovskite-Metal Back-Contact Solar Cell Structure Through Electrostatic Doping: A Numerical Study. *Pandey, R.*, +, *TED April 2021 1757-1763*
- Improving Photovoltaic Performance of Dye-Sensitized Solar Cell by Modification of Photoanode With  $g\text{-C}_3\text{N}_4/\text{TiO}_2$  Nanofibers. *Nien, Y.*, +, *TED Oct. 2021 4982-4988*
- Investigation on Short-Circuit Characterization and Optimization of 3.3-kV SiC MOSFETs. *Chen, X.*, +, *TED Jan. 2021 184-191*
- Optimization of Organic Meso-Superstructured Solar Cells for Underwater  $\text{IOT}^2$  Self-Powered Sensors. *Hatem, T.*, +, *TED Oct. 2021 5319-5321*
- Spectral Response Enhancement of the CdS/CdTe Solar Nano-Structured Cell Using ZnO Window Layer. *Kumar, D.*, +, *TED Sept. 2021 4504-4508*

**Shot noise**

- Direct White Noise Characterization of Short-Channel MOSFETs. *Ohmori, K.*, +, *TED April 2021 1478-1482*
- Suppression of Shot Noise During the Soft Reset by Cascaded Transitions on a Potential Ladder With Single-Carrier Charging Steps. *Hirose, Y.*, *TED April 2021 1723-1729*

**Signal detection**

- Differential Signal Acquisition Using TFT Light-Sensing Pixel Array. *Tai, Y.*, +, *TED July 2021 3403-3410*
- Theoretical Prediction of High-Performance Room-Temperature InGaAs/Si Single-Photon Avalanche Diode Fabricated by Semiconductor Interlayer Bonding. *Ke, S.*, +, *TED April 2021 1694-1701*

**Signal generators**

- Monolithic Comparator and Sawtooth Generator of AlGaIn/GaN MIS-HEMTs With Threshold Voltage Modulation for High-Temperature Applications. *Li, A.*, +, *TED June 2021 2673-2679*

**Silicides**

- Impact of the Si Content on the Electrical Properties of  $\text{NiSi}_x\text{Ge}_{1-x}$  Source/Drain Contact Metal for Ge pMOSFETs. *Zeng, S.*, +, *TED Nov. 2021 5742-5746*

**Silicon**

- 100- $\mu\text{m}$ -Scale High-Detectivity Infrared Detector With Thermopile/Absorber Double-Deck Structure Formed in (111) Silicon. *Xue, D.*, +, *TED Dec. 2021 6233-6239*
- 1300 V Normally-OFF p-GaN Gate HEMTs on Si With High ON-State Drain Current. *Jiang, H.*, +, *TED Feb. 2021 653-657*
- 3-D Full-Band Monte Carlo Simulation of Hot-Electron Energy Distributions in Gate-All-Around Si Nanowire MOSFETs. *Reaz, M.*, +, *TED May 2021 2556-2563*
- A Cascade Electron Source Based on Series Horizontal Tunneling Junctions. *Li, Z.*, +, *TED Feb. 2021 818-821*
- A CMOS Photodetector for Direct Color Imaging. *Audet, Y.*, +, *TED March 2021 1107-1114*
- A Comparison of Analog Performance, Linearity, and Distortion Characteristics Between Symmetric InGaAs and Asymmetric InGaAs/InP MOSFETs. *Datta, E.*, +, *TED April 2021 1570-1576*
- A CRP-Space-Extended RRAM PUF With In-Cell Zero-Overhead Salicide-Blocked Contact. *Zhao, X.*, +, *TED July 2021 3702-3705*
- A Global Shutter Wide Dynamic Range Soft X-Ray CMOS Image Sensor With Backside-Illuminated Pinned Photodiode, Two-Stage Lateral Overflow Integration Capacitor, and Voltage Domain Memory Bank. *Shike, H.*, +, *TED April 2021 2056-2063*
- A Godunov-Type Stabilization Scheme for Large-Signal Simulations of a THz Nanowire Transistor Based on the Boltzmann Equation. *Noei, M.*, +, *TED Nov. 2021 5407-5413*
- A High-Efficiency Double-Side Silicon-Embedded Inductor for Integrated DC-DC Converter Applications. *Lv, G.*, +, *TED Sept. 2021 4801-4804*

- A Highly Scalable Junctionless FET Leaky Integrate-and-Fire Neuron for Spiking Neural Networks. *Kamal, N.*, +, *TED April 2021 1633-1638*
- A Highly Sensitive and Robust GaN Ultraviolet Photodetector Fabricated on 150-mm Si (111) Wafer. *Pokharia, R.S.*, +, *TED June 2021 2796-2803*
- A Multiscale Simulation Framework for Steep-Slope Si Nanowire Cold Source FET. *Gan, W.*, +, *TED Nov. 2021 5455-5461*
- A Surface Potential Model for Field-Effect Transistors With Bound-Charge Engineering. *Prentki, R.J.*, *TED Sept. 2021 4625-4629*
- An Asymmetrically Doped Vertical Si Bristor With Sub-1-V Operation. *Das, B.*, +, *TED Aug. 2021 3728-3733*
- Analog Figures of Merit of Vertically Stacked Silicon Nanosheets nMOS-FETs With Two Different Metal Gates for the Sub-7 nm Technology Node Operating at High Temperatures. *Silva, V.C.P.*, +, *TED July 2021 3630-3635*
- Analytical Study on a 700 V Triple RESURF LDMOS With a Variable High-K Dielectric Trench. *Cao, Z.*, +, *TED June 2021 2872-2878*
- Applicability of Shockley-Read-Hall Theory for Interface States. *Ruch, B.*, +, *TED April 2021 2092-2097*
- Benchmarking Silicon FinFET With the Carbon Nanotube and 2D-FETs for Advanced Node CMOS Logic Application. *Das, U.K.*, +, *TED July 2021 3643-3648*
- Capacitance Scaling in  $\text{In}_{0.71}\text{Ga}_{0.29}\text{As}/\text{InP}$  MOSFETs With Self-Aligned a:Si Spacers. *Garigapati, N.S.*, +, *TED Aug. 2021 3762-3767*
- Characteristics of Stacked Gate-All-Around Si Nanosheet MOSFETs With Metal Sidewall Source/Drain and Their Impacts on CMOS Circuit Properties. *Sung, W.*, +, *TED June 2021 3124-3128*
- CMOS-Compatible Ti/TiN/Al Refractory Ohmic Contact for GaAs Heterojunction Bipolar Transistors Grown on Ge/Si Substrate. *Wang, Y.*, +, *TED Dec. 2021 6065-6068*
- Compact DC and Quasi-Static Capacitances Modeling of a-Si:H TFTs, Including Parasitic Capacitances. *Lime, F.*, +, *TED July 2021 3384-3389*
- Compact Modeling of Multidomain Ferroelectric FETs: Charge Trapping, Channel Percolation, and Nucleation-Growth Domain Dynamics. *Xiang, Y.*, +, *TED April 2021 2107-2115*
- Compact Modeling of Temperature Effects in FDSOI and FinFET Devices Down to Cryogenic Temperatures. *Pahwa, G.*, +, *TED Sept. 2021 4223-4230*
- Compact Reliability Model of Analog RRAM for Computation-in-Memory Device-to-System Codesign and Benchmark. *Liu, Y.*, +, *TED June 2021 2686-2692*
- Compact Unipolar XNOR/XOR Circuit Using Multimodal Thin-Film Transistors. *Bestelink, E.*, +, *TED Oct. 2021 4951-4955*
- Corrections to "Optimized Si-Based Blocked Impurity Band Detector Under Alternative Operational Mode" [Sep 19 3891-3895]. *Zhu, H.*, +, *TED Jan. 2021 447*
- Coupled ZnO-SnO<sub>2</sub> Nanocomposite for Efficiency Enhancement of ZnO-SnO<sub>2</sub>/p-Si Heterojunction Solar Cell. *Narzary, R.*, +, *TED Feb. 2021 610-617*
- Defects and Passivation Mechanism of the Suboxide Layers at SiO<sub>2</sub>/4H-SiC (0001) Interface: A First-Principles Calculation. *Wang, Z.*, +, *TED Jan. 2021 288-293*
- Degradation and Failure of Flexible Low-Temperature Poly-Si TFTs Under Dynamic Stretch Stress. *Yin, X.*, +, *TED Sept. 2021 4455-4461*
- Demonstration of High-Performance 4H-SiC MISIM Ultraviolet Photodetector With Operation Temperature of 550 °C and High Responsivity. *Du, F.*, +, *TED Nov. 2021 5662-5665*
- Design of a Fan-Out Panel-Level SiC MOSFET Power Module Using Ant Colony Optimization-Back Propagation Neural Network. *Qian, Y.*, +, *TED July 2021 3460-3467*
- Design of a Low-Power Short-Channel Electrostatically Doped Silicene Nanoribbon FET. *Gooran-Shoorakchaly, A.*, +, *TED April 2021 1956-1961*
- Effect of Fixed Charges at Interface Between InP and Bonding Layer on Heterogeneous Integration of InP HEMTs. *Chen, Y.*, +, *TED May 2021 2226-2232*
- Effect of Kr/O<sub>2</sub>-Plasma Reactive Sputtering on Ferroelectric Nondoped HfO<sub>2</sub> Formation for MFSFET With Pt Gate Electrode. *Ohmi, S.*, +, *TED May 2021 2427-2433*

- Effect of the Si Doping Content in HfO<sub>2</sub> Film on the Key Performance Metrics of Ferroelectric FETs. *Mulaosmanovic, H.*, +, *TED Sept. 2021 4773-4779*
- Effective Modulation of GaN-on-Si LED via Indigenous MOSFET Engineering. *Piao, J.*, +, *TED Nov. 2021 5640-5644*
- Electrical Characteristics and Reliability of Wafer-on-Wafer (WOW) Bumpless Through-Silicon Via. *Tsai, Y.*, +, *TED July 2021 3520-3525*
- Energy-Saving Logic Gates Utilizing Coupling Phenomenon Between MIS(p) Tunneling Diodes. *Chen, J.H.*, +, *TED Dec. 2021 6558-6562*
- Epi-Gd<sub>2</sub>O<sub>3</sub>-MOSHEMT: A Potential Solution Toward Leveraging the Application of AlGaIn/GaN/Si HEMT With Improved I<sub>ON</sub>/I<sub>OFF</sub> Operating at 473 K. *Sarkar, R.*, +, *TED June 2021 2653-2660*
- Experimental Investigation of As Preamorphization Implant on Electrical Property of Ti-Based Silicide Contacts. *Mao, S.*, +, *TED April 2021 1835-1840*
- Exploiting Carbon Nanotube FET and Magnetic Tunneling Junction for Near-Memory-Computing Paradigm. *Yang, N.*, +, *TED April 2021 1975-1979*
- Fabrication and Characterization of Flexible AlGaIn/GaN HEMTs on Kapton Tape. *Hsu, K.*, +, *TED July 2021 3320-3324*
- Flexible Dual-Gate MoS<sub>2</sub> Neuromorphic Transistors on Freestanding Proton-Conducting Chitosan Membranes. *Chen, C.*, +, *TED June 2021 3119-3123*
- Flexible High-Temperature Polycrystalline Silicon Thin Film Transistor on Metal Foil With S/D Doped by Diffusion. *Yu, B.*, +, *TED Aug. 2021 3857-3862*
- Formation of Graphene-Silicon Junction by Room Temperature Reduction With Simultaneous Defects Removal. *Yi, H.*, +, *TED Feb. 2021 873-878*
- Frequency Response of Metal-Semiconductor Structures With Thin-Films Sapphire Interlayer by ALD Technique. *Tan, S.O.*, +, *TED Oct. 2021 5085-5089*
- Heterogeneous Integration of III-V Materials by Direct Wafer Bonding for High-Performance Electronics and Optoelectronics. *Caimi, D.*, +, *TED July 2021 3149-3156*
- High Performance Dual Gate Blue Laser Annealed Poly-Si Thin-Film Transistor for High-Resolution Displays. *Jeong, D.Y.*, +, *TED Aug. 2021 3863-3869*
- Highly Stacked GeSi Nanosheets and Nanowires by Low-Temperature Epitaxy and Wet Etching. *Liu, Y.*, +, *TED Dec. 2021 6599-6604*
- Identification of Channel Hot Carrier Stress-Induced Oxide Traps Leading to Random Telegraph Signals in pMOSFETs. *Ahmed, T.*, +, *TED Feb. 2021 713-719*
- Identification of Electrically Stressed Regions in AlGaIn/GaN-on-Si Schottky Barrier Diode Using EBIC Technique. *Priesol, J.*, +, *TED Jan. 2021 216-221*
- Impact of Channel Length on the Operation of Junctionless Transistors With Substrate Biasing. *Jeon, D.*, +, *TED June 2021 3070-3073*
- Impact of Charge Trapping and Depolarization on Data Retention Using Simultaneous P-V and I-V in HfO<sub>2</sub>-Based Ferroelectric FET. *Higashi, Y.*, +, *TED Sept. 2021 4391-4396*
- Impact of Interlayer and Ferroelectric Materials on Charge Trapping During Endurance Fatigue of FeFET With TiN/Hf<sub>x</sub>Zr<sub>1-x</sub>O<sub>2</sub>/Interlayer/Si (MFIS) Gate Structure. *Tian, F.*, +, *TED Nov. 2021 5872-5878*
- Impact of the Nonlinear Dielectric Hysteresis Properties of a Charge Trap Layer in a Novel Hybrid High-Speed and Low-Power Ferroelectric or Antiferroelectric HSO/HZO Boosted Charge Trap Memory. *Ali, T.*, +, *TED April 2021 2098-2106*
- Impact of the Si Content on the Electrical Properties of NiSi<sub>x</sub>Ge<sub>1-x</sub> Source/Drain Contact Metal for Ge pMOSFETs. *Zeng, S.*, +, *TED Nov. 2021 5742-5746*
- Impacts of Independent Dual-Gate Operation on Reliability of Nanosheet Junctionless Thin-Film Transistor. *Ma, W.C.*, +, *TED Dec. 2021 6171-6176*
- Improved Retention Characteristics of Z<sup>2</sup>-FET Employing Half Back-Gate Control. *Kwon, S.*, +, *TED March 2021 1041-1044*
- Improvement of Resistive Switching Characteristics of Titanium Oxide Based Nanowedge RRAM Through Nickel Silicidation. *Lee, D.K.*, +, *TED Jan. 2021 438-442*
- InAlN/GaN HEMT on Si With f<sub>max</sub> = 270 GHz. *Cui, P.*, +, *TED March 2021 994-999*
- Influence of Carbon on pBTI Degradation in GaN-on-Si E-Mode MOSC-HEMT. *Viey, A.G.*, +, *TED April 2021 2017-2024*
- Influence of Reduction in Effective Channel Length on Device Operations of In-Ga-Zn-O Thin-Film Transistors With Variations in Channel Compositions. *Bae, S.*, +, *TED Dec. 2021 6159-6165*
- Influence of Si-Substrate Concentration on Electrical Properties of Back-and-Top-Gate MoS<sub>2</sub> Transistors. *Zhao, X.*, +, *TED June 2021 3087-3090*
- Inherent Dipole Layer Formation Driven by Surface Energy at Nonplanar Dielectric Interface. *Fang, Y.*, +, *TED Jan. 2021 294-298*
- Investigation of V<sub>t</sub> Distribution Tails of Ground-Select-Line Cells and Edge Dummy Cells in a 3-D NAND Flash Memory. *Chou, Y.*, +, *TED May 2021 2260-2264*
- Investigation of CsSn<sub>0.5</sub>Ge<sub>0.5</sub>I<sub>3</sub>-on-Si Tandem Solar Device Utilizing SCAPS Simulation. *Islam, M.T.*, +, *TED Feb. 2021 618-625*
- Investigations on the Negative Shift of the Threshold Voltage of Polycrystalline Silicon Thin-Film Transistors Under Positive Gate Bias Stress. *Liang, N.*, +, *TED Feb. 2021 550-555*
- Leakage-Prevention Mechanism to Maintain Driving Capability of Compensation Pixel Circuit for Low Frame Rate AMOLED Displays. *Lin, C.*, +, *TED May 2021 2313-2319*
- Localizing Hot-Carrier Degradation in Silicon Trench MOSFETs. *Ruch, B.*, +, *TED April 2021 1804-1809*
- Low-Frequency Noise Analysis of the Optimized Post High-k Deposition Annealing in FinFET Technology. *Deng, W.*, +, *TED March 2021 1202-1206*
- Low-Temperature Electrical Performance of PureB Photodiodes Revealing Al-Metallization-Related Degradation of Dark Currents. *Knezevic, T.*, +, *TED June 2021 2810-2817*
- Low-Temperature Processing of Electronic Materials Using Uniform Microwave Fields. *Hubbard, R.L.*, *TED July 2021 3170-3175*
- Low-Temperature Self-Aligned-Silicide-Capable Transistor Process Using Solid-Phase-Epitaxy and Lift-Off for Hybrid Substrates. *Tarighat, R.S.*, +, *TED Jan. 2021 244-250*
- Low-Voltage, High-Brightness Silicon Micro-LEDs for CMOS Photonics. *Xue, J.*, +, *TED Aug. 2021 3870-3875*
- Machine Learning Aided Device Simulation of Work Function Fluctuation for Multichannel Gate-All-Around Silicon Nanosheet MOSFETs. *Akbar, C.*, +, *TED Nov. 2021 5490-5497*
- Material- and Process-Tolerant High-Efficiency Solar Cells With Dynamic Recovery of Performance. *Chatterji, N.*, +, *TED April 2021 1676-1681*
- Modeling of Nonlinear Dynamics and Temperature Stability of Doped Silicon Microresonators. *Rajai, P.*, +, *TED June 2021 2957-2964*
- Modeling of Repeated FET Hot-Carrier Stress and Anneal Cycles Using Si-H Bond Dissociation/Passivation Energy Distributions. *Vandemaele, M.*, +, *TED April 2021 1454-1460*
- Modeling of the Gate Tunneling Current in MFIS NCFETs. *Tyagi, K.*, +, *TED Nov. 2021 5886-5893*
- Monolithic Integrated Normally OFF GaN Power Device With Antiparallel Lateral Schottky Barrier Controlled Schottky Rectifier. *Bi, L.*, +, *TED April 2021 1778-1783*
- New Concerns on Heavy Ion Irradiation Induced Variation Degradation in Nanoscale CMOS Devices. *Ren, Z.*, +, *TED April 2021 2142-2146*
- NiSi/p<sup>+</sup>-Si(n<sup>+</sup>-Si)/n-Si(p-Si) Diodes With Dopant Segregation (DS): p-n or Schottky Junctions?. *Zhang, D.*, +, *TED June 2021 2886-2891*
- Nitrogen-Implanted Guard Rings for 600-V Quasi-Vertical GaN-on-Si Schottky Barrier Diodes With a BFOM of 0.26 GW/cm<sup>2</sup>. *Guo, X.*, +, *TED Nov. 2021 5682-5686*
- Novel LDMOS With Integrated Triple Direction High-k Gate and Field Dielectrics. *Yao, J.*, +, *TED Aug. 2021 3997-4003*
- Novel Snapback-Free SOI LIGHT With Shorted Anode and Trench Barriers. *Sun, L.*, +, *TED May 2021 2408-2413*
- On Noise Performance of Dual-Gated Silicon FET Biosensors With Schottky Contacts. *Gao, W.*, +, *TED June 2021 2965-2970*
- On the Operation Modes of Dual-Gate Reconfigurable Nanowire Transistors. *Sun, B.*, +, *TED July 2021 3684-3689*

- On the Physical Meaning of Single-Value Activation Energies for BTI in Si and SiC MOSFET Devices. *Feil, M.W.*, +, *TED Jan. 2021 236-243*
- On-Wafer Electron Beam Detectors by Floating-Gate FinFET Technologies. *Wang, S.J.*, +, *TED Sept. 2021 4651-4655*
- Optimum Aspect Ratio of Superjunction Pillars Considering Charge Imbalance. *Akshay, K.*, +, *TED April 2021 1798-1803*
- Parallel Velocity Extension for Level-Set-Based Material Flow on Hierarchical Meshes in Process TCAD. *Quell, M.*, +, *TED Nov. 2021 5430-5437*
- Performance Projection of 2-D Material-Based CMOS Inverters for Sub-10-nm Channel Length. *Rawat, A.*, +, *TED July 2021 3622-3629*
- Permittivity Characterization of Dielectric Surfaces Using Nanofabricated In-Plane Capacitors. *Mousavi Karimi, Z.*, +, *TED Aug. 2021 4033-4038*
- Piezoresistive Electronic-Skin Sensors Produced With Self-Channeling Laser Microstructured Silicon Molds. *Su, Y.*, +, *TED Feb. 2021 786-792*
- Quantum Dot With a Diamond-Shaped Channel MOSFET on a Bulk Si Substrate. *Gu, J.*, +, *TED Jan. 2021 405-410*
- Radiation Resistance of High-Voltage Silicon and 4H-SiC Power p-i-n Diodes. *Hazdra, P.*, +, *TED Jan. 2021 202-207*
- Reconfigurable MoTe<sub>2</sub> Field-Effect Transistors and its Application in Compact CMOS Circuits. *Chen, J.*, +, *TED Sept. 2021 4748-4753*
- Recovery Behavior of Interface Traps After Negative Bias Temperature Instability Stress in p-FinFETs Featuring Fast Trap Characterization Technique. *Zhou, L.*, +, *TED Sept. 2021 4251-4258*
- Reducing Power Consumption of Active-Matrix Mini-LED Backlit LCDs by Driving Circuit. *Deng, M.*, +, *TED May 2021 2347-2354*
- Reliability of p-Type Pi-Gate Poly-Si Nanowire Channel Junctionless Accumulation-Mode FETs. *Hsieh, D.*, +, *TED June 2021 2647-2652*
- Response Comparison of Resistor- and Si FET-Type Gas Sensors on the Same Substrate. *Jung, G.*, +, *TED July 2021 3552-3557*
- RF Performance of Stacked Si Nanosheet nFETs. *Lin, H.*, +, *TED Oct. 2021 5277-5283*
- Schottky-Embedded Silicon-Controlled Rectifier With High Holding Voltage Realized in a 0.18- $\mu\text{m}$  Low-Voltage CMOS Process. *Chang, R.*, +, *TED April 2021 1764-1771*
- Silicene-Based Spin Filter With High Spin-Polarization. *Kharadi, M.A.*, +, *TED Oct. 2021 5095-5100*
- Silicon Field Emission Electron Source With Individually Controllable Single Emitters. *Lawrowski, R.*, +, *TED Aug. 2021 4116-4122*
- Silicon-on-Insulator Lateral DMOS With Potential Modulation Plates and Multiple Deep-Oxide Trenches. *Ma, J.*, +, *TED Oct. 2021 5073-5077*
- Simulation Study of the Instability Induced by the Variation of Grain Boundary Width and Trap Density in Gate-All-Around Polysilicon Transistor. *Lin, P.*, +, *TED April 2021 1969-1974*
- Single-Crystal Islands (SCI) for Monolithic 3-D and Back-End-of-Line FinFET Circuits. *Liu, Y.*, +, *TED Oct. 2021 5257-5262*
- Small- and Large-Signal Dynamic Output Capacitance and Energy Loss in GaN-on-Si Power HEMTs. *Zhuang, J.*, +, *TED April 2021 1819-1826*
- Spreading Resistance Modeling for Contact Resistivity Extraction in Ohmic Multilayer Structures With Circular Electrodes. *Turkay, D.*, +, *TED Dec. 2021 6344-6351*
- Stackable InGaAs-on-Insulator HEMTs for Monolithic 3-D Integration. *Jeong, J.*, +, *TED May 2021 2205-2211*
- Strained Silicon-on-Insulator Platform for Cointegration of Logic and RF—Part I: Implant-Induced Strain Relaxation. *Sun, C.*, +, *TED April 2021 1425-1431*
- Stretchable Carbon Nanotube Thin-Film Transistor Arrays Realized by a Universal Transferable-Band-Aid Method. *Fan, L.*, +, *TED Nov. 2021 5879-5885*
- Structural and Electrical Characteristics of ALD-TiO<sub>2</sub>/SiON/n-Si Gate-Stack for Advanced CMOS Device Applications. *Gupta, R.*, +, *TED June 2021 2625-2632*
- Sub-mA/cm<sup>2</sup> Dark Current Density, Buffer-Less Germanium (Ge) Photodiodes on a 200-nm Ge-on-Insulator Substrate. *Lin, Y.*, +, *TED April 2021 1730-1737*
- Surround Gate Transistor With Epitaxially Grown Si Pillar and Simulation Study on Soft Error and Rowhammer Tolerance for DRAM. *Han, J.*, +, *TED Feb. 2021 529-534*
- TCAD-Based Assessment of the Lateral GAA Nanosheet Transistor for Future CMOS. *Huang, Y.*, +, *TED Dec. 2021 6586-6591*
- The Effect of Interface Traps at the Si/SiO<sub>2</sub> Interface on the Transient Negative Capacitance of Ferroelectric FETs. *Sun, X.*, +, *TED Sept. 2021 4735-4740*
- Theoretical Prediction of High-Performance Room-Temperature InGaAs/Si Single-Photon Avalanche Diode Fabricated by Semiconductor Interlayer Bonding. *Ke, S.*, +, *TED April 2021 1694-1701*
- Transient Current Enhancement in MIS Tunnel Diodes With Lateral Electric Field Induced by Designed High-Low Oxide Layers. *Huang, S.*, +, *TED Dec. 2021 6580-6585*
- Transistor Compact Model Based on Multigradient Neural Network and Its Application in SPICE Circuit Simulations for Gate-All-Around Si Cold Source FETs. *Yang, Q.*, +, *TED Sept. 2021 4181-4188*
- Tunable Electronic Trap Energy in Sol-Gel Processed Dielectrics. *Mondal, S.*, +, *TED March 2021 1190-1195*
- Understanding High-Energy 75-MeV Sulfur-Ion Irradiation-Induced Degradation in GaN-Based Heterostructures: The Role of the GaN Channel Layer. *Challa, S.R.*, +, *TED Jan. 2021 24-28*
- Uniformly Broadband Far-Infrared Response From the Photocarrier Tunneling of Mesa Si:P Blocked-Impurity-Band Detector. *Chen, J.*, +, *TED Feb. 2021 560-564*
- Vertical Sandwich GAA FETs With Self-Aligned High-*k* Metal Gate Made by Quasi Atomic Layer Etching Process. *Zhang, Y.*, +, *TED June 2021 2604-2610*
- Silicon carbide**
- A Compact Spice Model for SiC Gate Turn-Off Thyristors With Complete Parameter Extraction Procedure. *Ma, H.*, +, *TED Dec. 2021 6296-6304*
- A Study on the Isolation Ability of Local Oxidation of SiC (LOCOSiC) for 4H-SiC CMOS Process. *Tsui, B.*, +, *TED Dec. 2021 6644-6647*
- Comparative Study of Hall Effect Mobility in Inversion Layer of 4H-SiC MOSFETs With Nitrided and Phosphorus-Doped Gate Oxides. *Noguchi, M.*, +, *TED Dec. 2021 6321-6329*
- Demonstration of High-Performance 4H-SiC MISIM Ultraviolet Photodetector With Operation Temperature of 550 °C and High Responsivity. *Du, F.*, +, *TED Nov. 2021 5662-5665*
- Design and Analysis of P-GaN/N-Ga<sub>2</sub>O<sub>3</sub> Based Junction Barrier Schottky Diodes. *Nandi, A.*, +, *TED Dec. 2021 6052-6058*
- Design and Fabrication of 1.92 kV 4H-SiC Super-Junction SBD With Wide-Trench Termination. *Wang, B.*, +, *TED Nov. 2021 5674-5681*
- Investigation and Modeling of the Avalanche Failure Mechanism of 1.2-kV 4H-SiC J MOS. *Zhang, Y.*, +, *TED Dec. 2021 6313-6320*
- Plasma Spreading Layers: An Effective Method for Improving Surge and Avalanche Robustness of SiC Devices. *Ren, N.*, +, *TED Nov. 2021 5687-5694*
- Visible-Blind Photodetector Based on p-i-n Junction 4H-SiC Vertical Nanocone Array. *Guo, S.*, +, *TED Dec. 2021 6208-6215*
- Silicon compounds**
- 1.2-kV Vertical GaN Fin-JFETs: High-Temperature Characteristics and Avalanche Capability. *Liu, J.*, +, *TED April 2021 2025-2032*
- 100- $\mu\text{m}$ -Scale High-Detectivity Infrared Detector With Thermopile/Absorber Double-Deck Structure Formed in (111) Silicon. *Xue, D.*, +, *TED Dec. 2021 6233-6239*
- 1100 V, 22.9 m $\Omega\text{cm}^2$  4H-SiC RESURF Lateral Double-Implanted MOSFET With Trench Isolation. *Hu, J.*, +, *TED Oct. 2021 5009-5013*
- 650-V 4H-SiC Planar Inversion-Channel Power JBSFETs With 55-nm Gate Oxide: Relative Performance of Three Cell Types. *Agarwal, A.*, +, *TED May 2021 2395-2400*
- A Cascade Electron Source Based on Series Horizontal Tunneling Junctions. *Li, Z.*, +, *TED Feb. 2021 818-821*
- A Compact Trench-Assisted Space-Modulated JTE Design for High-Voltage 4H-SiC Devices. *Dai, T.*, +, *TED March 2021 1162-1167*
- A High-Performance 4H-SiC JFET With Reverse Recovery Capability and Low Switching Loss. *Kong, M.*, +, *TED Oct. 2021 5022-5028*
- A Highly Efficient Annealing Process With Supercritical N<sub>2</sub>O at 120 °C for SiO<sub>2</sub>/4H-SiC Interface. *Wang, M.*, +, *TED April 2021 1841-1846*
- A Novel 4H-SiC Trench MOSFET Integrated With Mesa-Sidewall SBD. *Han, Z.*, +, *TED Jan. 2021 192-196*

- A Novel Approach to Inactivate the Body p-i-n Diode of SiC MOSFET by Using the Normally-OFF JFET. *Li, P.*, +, *TED April 2021 1784-1790*
- Analysis of Current Capability of SiC Power MOSFETs Under Avalanche Conditions. *Nida, S.*, +, *TED Sept. 2021 4587-4592*
- Analysis of Mobility for 4H-SiC N/P-Channel MOSFETs Up To 300 °C. *Yang, L.*, +, *TED Aug. 2021 3936-3941*
- Analytical Model and Optimization for SiC Floating Island Structure. *Wang, C.*, +, *TED Jan. 2021 222-229*
- Anomalous Behavior of Gate Current and TDDDB Lifetime by Constant Voltage Stress in NO-Annealed SiC-MOSFETs. *Murakami, E.*, +, *TED March 2021 1207-1213*
- Applicability of Shockley-Read-Hall Theory for Interface States. *Ruch, B.*, +, *TED April 2021 2092-2097*
- Breakdown Voltage Enhancement in ScAlN/GaN High-Electron-Mobility Transistors by High-*k* Bismuth Zinc Niobate Oxide. *Cheng, J.*, +, *TED July 2021 3333-3338*
- Channel Properties of Ga<sub>2</sub>O<sub>3</sub>-on-SiC MOSFETs. *Wang, Y.*, +, *TED March 2021 1185-1189*
- Characterization and Analysis on Performance and Avalanche Reliability of SiC MOSFETs With Varied JFET Region Width. *Zhu, Z.*, +, *TED Aug. 2021 3982-3990*
- Characterization of Al<sub>2</sub>O<sub>3</sub>/LaAlO<sub>3</sub>/SiO<sub>2</sub> Gate Stack on 4H-SiC After Post-Deposition Annealing. *Huang, L.*, +, *TED April 2021 2133-2137*
- Comparison of Impact Ionization Models for 4H-SiC Along the <0001> Direction, Through Breakdown Voltage Simulations at Room Temperature. *Stefanakis, D.*, +, *TED May 2021 2582-2586*
- Defects and Passivation Mechanism of the Suboxide Layers at SiO<sub>2</sub>/4H-SiC (0001) Interface: A First-Principles Calculation. *Wang, Z.*, +, *TED Jan. 2021 288-293*
- Degradation Behavior and Defect Analysis for SiC Power MOSFETs Based on Low-Frequency Noise Under Repetitive Power-Cycling Stress. *Yang, X.*, +, *TED Feb. 2021 666-671*
- Demonstration of CMOS-Compatible Multi-Level Graphene Interconnects With Metal Vias. *Agashiwala, K.*, +, *TED April 2021 2083-2091*
- Demonstration of Constant-Gate-Charge Scaling to Increase the Robustness of Silicon Carbide Power MOSFETs. *Cooper, J.A.*, +, *TED Sept. 2021 4577-4581*
- Design of a Fan-Out Panel-Level SiC MOSFET Power Module Using Ant Colony Optimization-Back Propagation Neural Network. *Qian, Y.*, +, *TED July 2021 3460-3467*
- Dramatic Improvement in the Rectifying Properties of Pd Schottky Contacts on  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> During Their High-Temperature Operation. *Hou, C.*, +, *TED April 2021 1791-1797*
- Effect of Fixed Charges at Interface Between InP and Bonding Layer on Heterogeneous Integration of InP HEMTs. *Chen, Y.*, +, *TED May 2021 2226-2232*
- Effect of Threshold Voltage Hysteresis on Switching Characteristics of Silicon Carbide MOSFETs. *Cai, Y.*, +, *TED Oct. 2021 5014-5021*
- Electrical and Thermal Performance of Ga<sub>2</sub>O<sub>3</sub>-Al<sub>2</sub>O<sub>3</sub>-Diamond Super-Junction Schottky Barrier Diodes. *Mishra, A.*, +, *TED Oct. 2021 5055-5061*
- Electrical Degradation of *In Situ* SiN/AlGaN/GaN MIS-HEMTs Caused by Dehydrogenation and Trap Effect Under Hot Carrier Stress. *Niu, X.*, +, *TED Sept. 2021 4283-4288*
- Enhanced High-Frequency Performance of Top-Gated Graphene FETs Due to Substrate-Induced Improvements in Charge Carrier Saturation Velocity. *Asad, M.*, +, *TED Feb. 2021 899-902*
- Extraction of the Trench Sidewall Capacitances in an n-Type 4H-SiC Trench Metal-Oxide-Semiconductor Structure. *Guo, Z.*, +, *TED June 2021 2879-2885*
- Formation of Graphene-Silicon Junction by Room Temperature Reduction With Simultaneous Defects Removal. *Yi, H.*, +, *TED Feb. 2021 873-878*
- Gate Oxide Damage of SiC MOSFETs Induced by Heavy-Ion Strike. *Zhou, X.*, +, *TED Aug. 2021 4010-4015*
- High Linear Power E-Band Traveling-Wave Tube for Communication Applications. *Liu, S.*, +, *TED June 2021 2984-2989*
- Identification of Channel Hot Carrier Stress-Induced Oxide Traps Leading to Random Telegraph Signals in pMOSFETs. *Ahmed, T.*, +, *TED Feb. 2021 713-719*
- Impact of Charge Trapping and Depolarization on Data Retention Using Simultaneous *P-V* and *I-V* in HfO<sub>2</sub>-Based Ferroelectric FET. *Higashi, Y.*, +, *TED Sept. 2021 4391-4396*
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#### Submillimeter wave detectors

A Compact Current- and Voltage-Mode Model of Antenna-Coupled FET Terahertz Detectors. *Perenzoni, M.*, +, *TED Feb. 2021 471-478*

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- Flexible Complementary Oxide Thin-Film Transistor-Based Inverter With High Gain. *Hsu, S.*, +, *TED March 2021 1070-1074*
- Formation of F-Doped Offset Region for Spray Pyrolyzed Self-Aligned Coplanar Amorphous Zinc–Tin–Oxide Thin-Film Transistor by NF<sub>3</sub> Plasma Treatment. *Kim, Y.G.*, +, *TED March 2021 1057-1062*
- Frequency Response of Metal–Semiconductor Structures With Thin-Films Sapphire Interlayer by ALD Technique. *Tan, S.O.*, +, *TED Oct. 2021 5085-5089*
- Gas Sensor Based on Semihydrogenated and Semifluorinated h-BN for SF<sub>6</sub> Decomposition Components Detection. *Peng, Z.*, +, *TED April 2021 1878-1885*
- Gate Current Partitioning Model for Schottky Gate GaN HEMTs. *Debnath, A.*, +, *TED Jan. 2021 425-429*
- Gate Oxide Damage of SiC MOSFETs Induced by Heavy-Ion Strike. *Zhou, X.*, +, *TED Aug. 2021 4010-4015*
- Gate-First Negative Capacitance Field-Effect Transistor With Self-Aligned Nickel-Silicide Source and Drain. *Kim, S.*, +, *TED Sept. 2021 4754-4757*
- Gate-Induced Threshold Voltage Instabilities in p-Gate GaN HEMTs. *Oeder, T.*, +, *TED Sept. 2021 4322-4328*
- High Breakdown Voltage and Low-Current Dispersion in AlGaIn/GaN HEMTs With High-Quality AlN Buffer Layer. *Kim, J.*, +, *TED April 2021 1513-1517*
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- High-Performance Thin-Film IGZO Schottky Diodes With Sputtered PdO<sub>x</sub> Anode. *Yan, S.*, +, *TED Sept. 2021 4444-4449*
- High-Temperature Sensitivity of a Depletion-Mode AlGaIn/GaN MIS-HEMT. *Mutsafi, Z.*, +, *TED Nov. 2021 5695-5700*
- Hole Transport in Ultraviolet Light-Emitting Diode via p-Type Injection Channel. *Mondal, R.K.*, +, *TED May 2021 2320-2325*
- Hybrid Electrothermal Simulations of GaN HEMT Devices Based on Self-Heating Free Virtual Electrical Characteristics. *Valletta, A.*, +, *TED Aug. 2021 3740-3747*
- Hydrogen Behavior in Top Gate Amorphous In–Ga–Zn–O Device Fabrication Process During Gate Insulator Deposition and Gate Insulator Etching. *Song, A.*, +, *TED June 2021 2723-2728*
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- Identifying the Properties of Traps in GaN High-Electron-Mobility Transistors via Amplitude Analysis Based on the Voltage-Transient Method. *Pan, S.*, +, *TED Nov. 2021 5541-5546*
- Implementation of RTCVD-Si<sub>x</sub> Gate Dielectric Into Enhancement-Mode GaN MIS-HEMTs Fabricated on Ultrathin-Barrier AlGaIn/GaN-on-Si Platform. *Shi, W.*, +, *TED Sept. 2021 4274-4277*
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- Improvement of β-Ga<sub>2</sub>O<sub>3</sub> MIS-SBD Interface Using Al-Reacted Interfacial Layer. *He, M.*, +, *TED July 2021 3314-3319*
- Improvement of Both n- and p-Channel Mobilities in 4H-SiC MOSFETs by High-Temperature N<sub>2</sub> Annealing. *Tachiki, K.*, +, *TED Feb. 2021 638-644*
- Improvement of Breakdown Voltage and ON-Resistance in Normally-OFF AlGaIn/GaN HEMTs Using Etching-Free p-GaN Stripe Array Gate. *Wei, X.*, +, *TED Oct. 2021 5041-5047*
- Improving the Cu<sub>2</sub>ZnSn(S,Se)<sub>4</sub>-Based Photovoltaic Conversion Efficiency by Back-Contact Modification. *Sengar, B.S.*, +, *TED June 2021 2748-2752*
- InAlN/GaN HEMT on Si With f<sub>max</sub> = 270 GHz. *Cui, P.*, +, *TED March 2021 994-999*
- Influence of Carbon on pBTI Degradation in GaN-on-Si E-Mode MOS-HEMT. *Viey, A.G.*, +, *TED April 2021 2017-2024*
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- Influence of Process Variations on the Electrical Performance of SiC Power MOSFETs. *Muting, J.*, +, *TED Jan. 2021 230-235*
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- Low Leakage and High Forward Current Density Quasi-Vertical GaN Schottky Barrier Diode With Post-Mesa Nitridation. *Kang, X.*, +, *TED March 2021 1369-1373*
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- Low Subthreshold Swing and High Performance of Ultrathin PEALD InGaZnO Thin-Film Transistors. *Jeong, S.*, +, *TED April 2021 1670-1675*
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- Low-Voltage, High-Brightness Silicon Micro-LEDs for CMOS Photonics. *Xue, J.*, +, *TED Aug. 2021 3870-3875*
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- On Noise Performance of Dual-Gated Silicon FET Biosensors With Schottky Contacts. *Gao, W.*, +, *TED June 2021 2965-2970*
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- Proposal and Experimental Demonstration of Ultrathin-Body (111) InAs-On-Insulator nMOSFETs With L Valley Conduction. *Sumita, K.*, +, *TED April 2021 2003-2009*
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- Substrate Bias Enhanced Trap Effects on Time-Dependent Dielectric Breakdown of GaN MIS-HEMTs. *Yang, W.*, +, *TED May 2021 2233-2239*
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- Time-Dependent Threshold Voltage Instability Mechanisms of p-GaN Gate AlGaN/GaN HEMTs Under High Reverse Bias Conditions. *Li, S.*, +, *TED Jan. 2021 443-446*
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- Flexible Organic Thin-Film Transistors With High Mechanical Stability on Polyimide Substrate by Chemically Plated Silver Electrodes. *Zou, J.*, +, *TED Oct. 2021 5120-5126*
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- Junctionless Multiple-Gate (JLMG) MOSFETs: A Unified Subthreshold Current Model to Assess Noise Margin of Subthreshold Logic Gate. *Chiang, T.*, *TED Oct. 2021 5330-5334*
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## Y

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